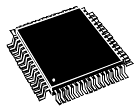
STM32L162VC STM32L162RC

Ultra-low-power 32-bit MCU ARM-based Cortex-M3, 256KB Flash, 32KB SRAM, 8KB EEPROM, LCD, USB, ADC, DAC, AES

Datasheet - production data

Features

- Ultra-low-power platform
  - 1.65 V to 3.6 V power supply
  - **-40°C to 85°C/105°C** Temperature range
  - 0.35 µA Standby mode (3 wake up pins)
  - **1.3 µA Standby mode + RTC**
  - 0.65 µA Stop mode (16 wakeup lines)
  - 1.5 µA Stop mode + RTC
  - 8.6 µA Low-power Run mode
  - 187 µA/MHz Run mode
  - 10 nA ultra-low I/O leakage
  - 8 µs wakeup time
- AES-128bit encryption hardware accelerator
- Core: ARM® Cortex™-M3 32-bit CPU
  - From 32 kHz up to 32 MHz max
  - 33.3 DMIPS peak (Dhrystone 2.1)
  - Memory protection unit
- Reset and supply management
  - Low power, ultrasafe BOR (brownout reset) with 5 selectable thresholds
  - Ultralow power POR/PDR
  - Programmable voltage detector (PVD)
- Clock sources
  - 1 to 24 MHz crystal oscillator
  - 32 kHz oscillator for RTC with calibration
  - High Speed Internal 16 MHz factory-trimmed RC (+/- 1%)
  - Internal low power 37 kHz RC
  - Internal multispeed low power 65 kHz to 4.2 MHz RC
  - PLL for CPU clock and USB (48 MHz)
- Pre-programmed bootloader
  - USB and USART supported
- Development support
  - Serial wire debug supported
  - JTAG and trace supported



LQFP100 (14 × 14 mm)
LQFP64 (10 × 10 mm)

- Up to 83 fast I/Os (70 I/Os 5V tolerant),all mappable on 16 external interrupt vectors
- Memories
  - 256 KB Flash with ECC
  - 32 KB RAM
  - 8 KB of true EEPROM with ECC
  - 128 Byte backup register
- LCD Driver for up to 8×40 segments
  - Support contrast adjustment
  - Support blinking mode
  - Step-up converter on board
- Rich Analog peripherals (down to 1.8V)
  - 2x operational amplifier
  - 12-bit ADC 1 Msps up to 25 channels
  - 12-bit DAC 2 ch with output buffers
  - 2x Ultra-low-power-comparators (window mode and wake up capability)
- DMA controller 12x channels
- 9x communication interfaces
  - 1x USB 2.0 (internal 48MHz PLL)
  - 3x USART
  - 3x SPI 16 Mbits/s (2x SPI with I2S)
  - 2x I2C (SMBus/PMBus)
- 11x timers: 1x 32-bit, 6x 16-bit with up to 4 IC/OC/PWM channels each, 2x 16-bit basic timer and 2x watchdog timers (independent and window)
- Up to 23 capacitive sensing channels
- CRC calculation unit, 96-bit unique ID

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1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the medium density plus STM32L162xC ultra-low-power ARM Cortex-M3 based microcontrollers product line. Medium density plus STM32L162xC devices are microcontrollers with a Flash memory density of 256 Kbytes.

The medium density plus ultra-low-power STM32L162xC family includes devices in 2 different package types: from 64 pins to 100 pins. Depending on the device chosen, different sets of peripherals are included, the description below gives an overview of the complete range of peripherals proposed in this family.

These features make the medium density plus ultra-low-power STM32L162xC microcontroller family suitable for a wide range of applications:

- Medical and handheld equipment
- Application control and user interface
- PC peripherals, gaming, GPS and sport equipment
- Alarm systems, wired and wireless sensors, Video intercom
- Utility metering

This STM32L162xC datasheet should be read in conjunction with the STM32L1xxxx reference manual (RM0038). The document "Getting started with STM32L1xxx hardware development" AN3216 gives a hardware implementation overview. Both documents are available from the STMicroelectronics website www.st.com.

For information on the ARM Cortex-M3 core please refer to the ARM Cortex-M3 Technical Reference Manual, available from the *www.arm.com* website at the following address: http://infocenter.arm.com/help/index.jsp?topic=/com.arm.doc.ddi0337g.

Figure 1 shows the general block diagram of the device family.

2 Description

The medium density plus ultra-low-power STM32L162xC incorporates the connectivity power of the universal serial bus (USB) with the high-performance ARM Cortex-M3 32-bit RISC core operating at a 32 MHz frequency, a memory protection unit (MPU), high-speed embedded memories (Flash memory up to 256 Kbytes and RAM up to 32 Kbytes) and an extensive range of enhanced I/Os and peripherals connected to two APB buses.

The STM32L162xC medium density plus devices offer two operational amplifiers, one 12-bit ADC, two DACs, two ultra-low-power comparators, AES, one general-purpose 32-bit timer, six general-purpose 16-bit timers and two basic timers, which can be used as time bases.

Moreover, the medium density plus STM32L162xC devices contain standard and advanced communication interfaces: up to two I2Cs, three SPIs, two I2S, three USARTs and a USB. The STM32L162xC devices offer up to 23 capacitive sensing channels to simply add touch sensing functionality to any application.

They also include a real-time clock and a set of backup registers that remain powered in Standby mode.

Finally, the integrated LCD controller has a built-in LCD voltage generator that allows you to drive up to 8 multiplexed LCDs with contrast independent of the supply voltage.

The ultra-low-power STM32L162xC operates from a 1.8 to 3.6 V power supply (down to 1.65 V at power down) with BOR and from a 1.65 to 3.6 V power supply without BOR option. It is available in the -40 to +85 °C temperature range, extended to 105°C in low power dissipation state. A comprehensive set of power-saving modes allows the design of low-power applications.

2.1 Device overview

Table 1. Ultralow power STM32L162xC device features and peripheral counts

Peripheral		STM32L162RC	STM32L162VC
Flash (Kbytes)		256	
Data EEPROM (Kbytes)		8	
RAM (Kbytes)		32	
AES		1	
Timers	**32 bit**	1	
	General-purpose	6	
	Basic	2	
Communication interfaces	**SPI/(I2S)**	3/(2)	
	I^2C	2	
	USART	3	
	USB	1	
GPIOs		51	83
Operation amplifiers		2	
12-bit synchronized ADC **Number of channels**		1 21	1 25
12-bit DAC **Number of channels**		2 2	
LCD **COM x SEG**		1 4x32 or 8x28	1 4x44 or 8x40
Comparators		2	
Capacitive sensing channels		23	23
Max. CPU frequency		32 MHz	
Operating voltage		1.8 V to 3.6 V (down to 1.65 V at power-down) with BOR option 1.65 V to 3.6 V without BOR option	
Operating temperatures		Ambient temperature: –40 to +85 °C Junction temperature: –40 to + 105 °C	
Packages		LQFP64	LQFP100

2.2 Ultra-low-power device continuum

The ultra-low-power STM32L15xxD, STM32L162xD, STM32L15xxC and STM32L162xC are fully pin-to-pin and software compatible. Besides the full compatibility within the family, the devices are part of STMicroelectronics microcontrollers ultra-low-power strategy which also includes STM8L101xx and STM8L15xx devices. The STM8L and STM32L families allow a continuum of performance, peripherals, system architecture and features.

They are all based on STMicroelectronics ultralow leakage process.

Note: The ultra-low-power STM32L and general-purpose STM32Fxxxx families are pin-to-pin compatible. The STM8L15xxx devices are pin-to-pin compatible with the STM8L101xx devices. Please refer to the STM32F and STM8L documentation for more information on these devices.

2.2.1 Performance

All families incorporate highly energy-efficient cores with both Harvard architecture and pipelined execution: advanced STM8 core for STM8L families and ARM Cortex-M3 core for STM32L family. In addition specific care for the design architecture has been taken to optimize the mA/DMIPS and mA/MHz ratios.

This allows the ultra-low-power performance to range from 5 up to 33.3 DMIPs.

2.2.2 Shared peripherals

STM8L15xxx, STM32L15xxx and STM32L162xx share identical peripherals which ensure a very easy migration from one family to another:

- Analog peripherals: ADC, DAC and comparators
- Digital peripherals: RTC and some communication interfaces

2.2.3 Common system strategy

To offer flexibility and optimize performance, the STM8L15xxx, STM32L15xxx and STM32L162xx families use a common architecture:

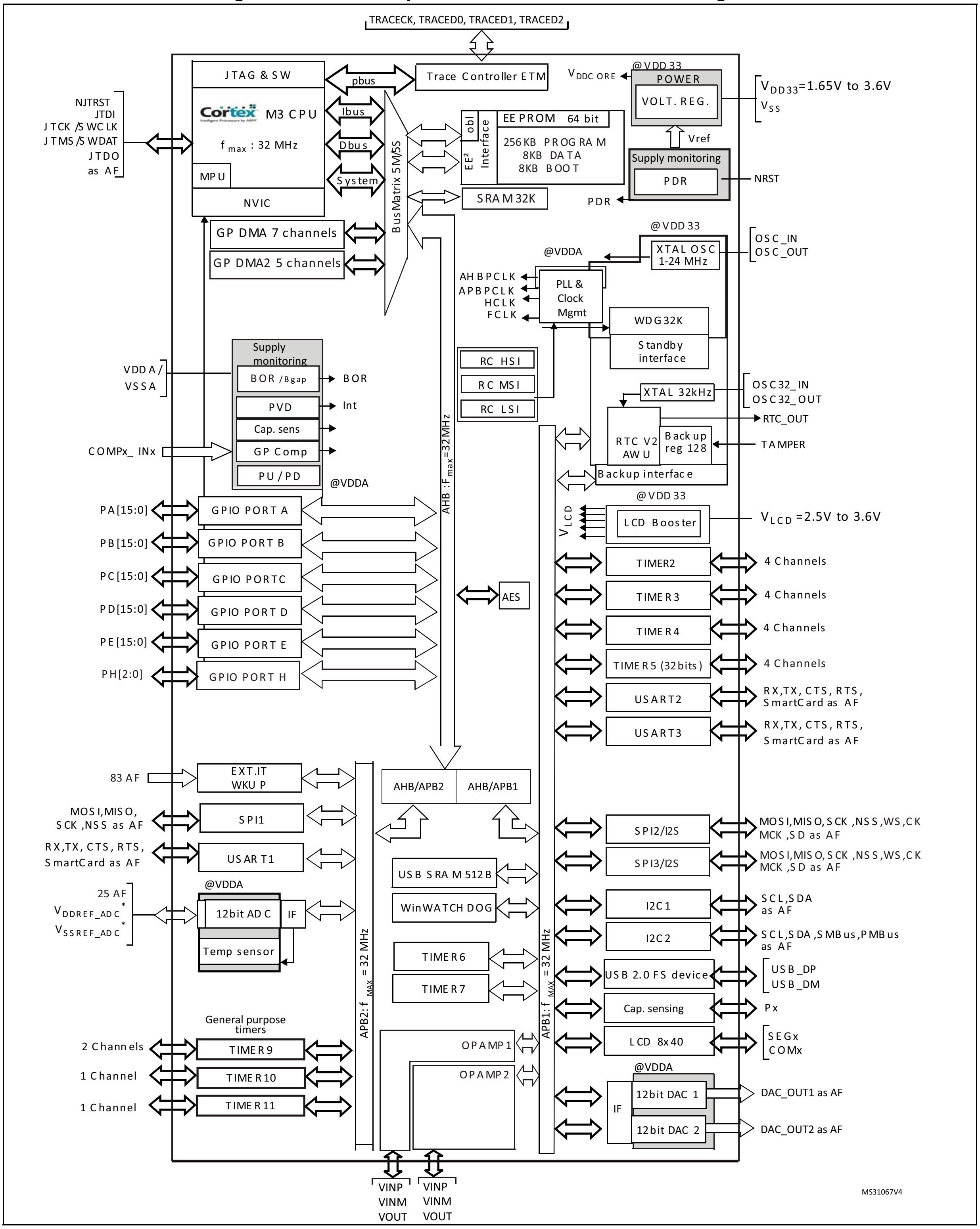
- Same power supply range from 1.65 V to 3.6 V
- Architecture optimized to reach ultralow consumption both in low power modes and Run mode
- Fast startup strategy from low power modes
- Flexible system clock
- Ultrasafe reset: same reset strategy including power-on reset, power-down reset, brownout reset and programmable voltage detector

2.2.4 Features

ST ultra-low-power continuum also lies in feature compatibility:

- More than 15 packages with pin count from 20 to 144 pins and size down to 3 x 3 mm
- Memory density ranging from 2 to 384 Kbytes

Figure 1. Ultra-low-power STM32L162xC block diagram



1. Legend: AF: alternate function ADC: analog-to-digital converter
AES: advanced encryption standard hardware accelerator
BOR: brown out reset DMA: direct memory access
DAC: digital-to-analog converter I²C: inter-integrated circuit multimaster interface

3 Functional overview

3.1 Low power modes

The ultra-low-power STM32L162xC supports dynamic voltage scaling to optimize its power consumption in run mode. The voltage from the internal low-drop regulator that supplies the logic can be adjusted according to the system’s maximum operating frequency and the external voltage supply.

There are three power consumption ranges:

- Range 1 (V_{DD} range limited to 2.0V-3.6V), with the CPU running at up to 32 MHz
- Range 2 (full V_{DD} range), with a maximum CPU frequency of 16 MHz
- Range 3 (full V_{DD} range), with a maximum CPU frequency limited to 4 MHz (generated only with the multispeed internal RC oscillator clock source)

Seven low power modes are provided to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

- **Sleep** mode

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs. Sleep mode power consumption at 16 MHz is about 1 mA with all peripherals off.
- **Low power run** mode

  This mode is achieved with the multispeed internal (MSI) RC oscillator set to the minimum clock (131 kHz), execution from SRAM or Flash memory, and internal regulator in low power mode to minimize the regulator's operating current. In Low power run mode, the clock frequency and the number of enabled peripherals are both limited.
- **Low power sleep** mode

  This mode is achieved by entering Sleep mode with the internal voltage regulator in Low power mode to minimize the regulator’s operating current. In Low power sleep mode, both the clock frequency and the number of enabled peripherals are limited; a typical example would be to have a timer running at 32 kHz.

  When wakeup is triggered by an event or an interrupt, the system reverts to the run mode with the regulator on.
- **Stop** mode with RTC

  Stop mode achieves the lowest power consumption while retaining the RAM and register contents and real time clock. All clocks in the V_{CORE} domain are stopped, the PLL, MSI RC, HSI RC and HSE crystal oscillators are disabled. The LSE or LSI is still running. The voltage regulator is in the low power mode.

  The device can be woken up from Stop mode by any of the EXTI line, in 8 µs. The EXTI line source can be one of the 16 external lines. It can be the PVD output, the Comparator 1 event or Comparator 2 event (if internal reference voltage is on), it can be the RTC alarm(s), the USB wakeup, the RTC tamper events, the RTC timestamp event or the RTC wakeup.

- **Stop** mode without RTC

  Stop mode achieves the lowest power consumption while retaining the RAM and register contents. All clocks are stopped, the PLL, MSI RC, HSI and LSI RC, LSE and HSE crystal oscillators are disabled. The voltage regulator is in the low power mode. The device can be woken up from Stop mode by any of the EXTI line, in 8 µs. The EXTI line source can be one of the 16 external lines. It can be the PVD output, the Comparator 1 event or Comparator 2 event (if internal reference voltage is on). It can also be wakened by the USB wakeup.
- **Standby** mode with RTC

  Standby mode is used to achieve the lowest power consumption and real time clock. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSI RC and HSE crystal oscillators are also switched off. The LSE or LSI is still running. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32K osc, RCC_CSR).

  The device exits Standby mode in 60 µs when an external reset (NRST pin), an IWDG reset, a rising edge on one of the three WKUP pins, RTC alarm (Alarm A or Alarm B), RTC tamper event, RTC timestamp event or RTC Wakeup event occurs.
- **Standby** mode without RTC

  Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are also switched off. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32K osc, RCC_CSR).

  The device exits Standby mode in 60 µs when an external reset (NRST pin) or a rising edge on one of the three WKUP pin occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped automatically by entering Stop or Standby mode.

Table 2. Functionalities depending on the operating power supply range

	Functionalities depending on the operating power supply range			
Operating power supply range	**DAC and ADC operation**	**USB**	**Dynamic voltage scaling range**	**I/O operation**
V_{DD} = 1.65 to 1.8 V	Not functional	Not functional	Range 2 or range 3	Degraded speed performance
V_{DD} = 1.8 to 2.0 V	Conversion time up to 500 Ksps	Not functional	Range 2 or range 3	Degraded speed performance
V_{DD} = 2.0 to 2.4 V	Conversion time up to 500 Ksps	Functional(1)	Range 1, range 2 or range 3	Full speed operation
V_{DD} = 2.4 to 3.6 V	Conversion time up to 1 Msps	Functional(1)	Range 1, range 2 or range 3	Full speed operation

1. To be USB compliant from the IO voltage standpoint, the minimum V_{DD} is 3.0 V.

Table 3. CPU frequency range depending on dynamic voltage scaling

CPU frequency range	Dynamic voltage scaling range
16 MHz to 32 MHz (1ws) 32 kHz to 16 MHz (0ws)	Range 1
8 MHz to 16 MHz (1ws) 32 kHz to 8 MHz (0ws)	Range 2
2.1MHz to 4.2 MHz (1ws) 32 kHz to 2.1 MHz (0ws)	Range 3

Table 4. Functionalities depending on the working mode (from Run/active down to standby)

Ips	Run/Active	Sleep	Low-power Run	Low-power Sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
CPU	Y	--	Y	--	--		--	
Flash	Y	Y	Y	N	--		--	
RAM	Y	Y	Y	Y	Y		--	
Backup Registers	Y	Y	Y	Y	Y		Y	
EEPROM	Y	--	Y	Y	Y		--	
Brown-out rest (BOR)	Y	Y	Y	Y	Y	Y	Y	
DMA	Y	Y	Y	Y	--		--	
Programable Voltage Detector (PVD)	Y	Y	Y	Y	Y	Y	Y	
Power On Reset (POR)	Y	Y	Y	Y	Y	Y	Y	
Power Down Rest (PDR)	Y	Y	Y	Y	Y		Y	
High Speed Internal (HSI)	Y	Y	--	--	--		--	
High Speed External (HSE)	Y	Y	--	--	--		--	
Low Speed Internal (LSI)	Y	Y	Y	Y	Y		--	
Low Speed External (LSE)	Y	Y	Y	Y	Y		--	
Multi-Speed Internal (MSI)	Y	Y	Y	Y	--		--	
Inter-Connect Controler	Y	Y	Y	Y	--		--	
RTC	Y	Y	Y	Y	Y	Y	Y	
RTC Tamper	Y	Y	Y	Y	Y	Y	Y	Y
Auto WakeUp (AWU)	Y	Y	Y	Y	Y	Y	Y	Y
LCD	Y	Y	Y	Y	Y		--	
USB	Y	Y	--	--	--	Y	--	
USART	Y	Y	Y	Y	Y	(1)	--	
SPI	Y	Y	Y	Y			--	
I2C	Y	Y	Y	Y		(1)	--	

Table 4. Functionalities depending on the working mode (from Run/active down to standby) (continued)

Ips	Run/Active	Sleep	Low-power Run	Low-power Sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
ADC	Y	Y	--	--	--		--	
DAC	Y	Y	Y	Y	Y		--	
Tempsensor	Y	Y	Y	Y	Y		--	
OP amp	Y	Y	Y	Y	Y		--	
Comparators	Y	Y	Y	Y	Y	Y	--	
16-bit and 32-bit Timers	Y	Y	Y	Y	--		--	
IWDG	Y	Y	Y	Y	Y	Y	Y	Y
WWDG	Y	Y	Y	Y	--		--	
Touch sensing	Y	Y	--	--	--		--	
Systic Timer	Y	Y	Y	Y			--	
GPIOs	Y	Y	Y	Y	Y	Y		3Pins
Wakeup time to Run mode	0 µs	0.36 µs	3 µs	32 µs	< 8 µs		50 µs	
Consumption V_{DD}=1.8V to 3.6V (Typ)	Down to 187 µA/MHz (from Flash)	Down to 40 µA/MHz (from Flash)	Down to 8.6 µA	Down to 4.4 µA	0.65 µA (No RTC) V_{DD}=1.8V		0.35 µA (No RTC) V_{DD}=1.8V	
					1.5 µA (with RTC) V_{DD}=1.8V		1 µA (with RTC) V_{DD}=1.8V	
					0.65µA (No RTC) V_{DD}=3.0V		0.35 µA (No RTC) V_{DD}=3.0V	
					1.7 µA (with RTC) V_{DD}=3.0V		1.3 µA (with RTC) V_{DD}=3.0V	

1. The startup on communication line wakes the CPU which was made possible by an EXTI, this induces a delay before entering run mode.

3.2 ARM Cortex-M3 core with MPU

The ARM Cortex-M3 processor is the industry leading processor for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM Cortex-M3 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

The memory protection unit (MPU) improves system reliability by defining the memory attributes (such as read/write access permissions) for different memory regions. It provides up to eight different regions and an optional predefined background region.

Owing to its embedded ARM core, the STM32L162xC is compatible with all ARM tools and software.

Nested vectored interrupt controller (NVIC)

The ultra-low-power STM32L162xC embeds a nested vectored interrupt controller able to handle up to 53 maskable interrupt channels (not including the 16 interrupt lines of ARM Cortex-M3) and 16 priority levels.

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of *late arriving*, higher-priority interrupts
- Support for tail-chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimal interrupt latency.

3.3 Reset and supply management

3.3.1 Power supply schemes

- V_{DD} = 1.65 to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} = 1.65 to 3.6 V: external analog power supplies for ADC, reset blocks, RCs and PLL (minimum voltage to be applied to V_{DDA} is 1.8 V when the ADC is used). V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS}, respectively.

3.3.2 Power supply supervisor

The device has an integrated ZEROPOWER power-on reset (POR)/power-down reset (PDR) that can be coupled with a brownout reset (BOR) circuitry.

The device exists in two versions:

- The version with BOR activated at power-on operates between 1.8 V and 3.6 V.
- The other version without BOR operates between 1.65 V and 3.6 V.

After the V_{DD} threshold is reached (1.65 V or 1.8 V depending on the BOR which is active or not at power-on), the option byte loading process starts, either to confirm or modify default thresholds, or to disable the BOR permanently: in this case, the V_{DD} min value becomes 1.65 V (whatever the version, BOR active or not, at power-on).

When BOR is active at power-on, it ensures proper operation starting from 1.8 V whatever the power ramp-up phase before it reaches 1.8 V. When BOR is not active at power-up, the power ramp-up should guarantee that 1.65 V is reached on V_{DD} at least 1 ms after it exits the POR area.

Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the internal reference voltage (V_{REFINT}) in Stop mode. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR}, without the need for any external reset circuit.

Note: The start-up time at power-on is typically 3.3 ms when BOR is active at power-up, the start-up time at power-on can be decreased down to 1 ms typically for devices with BOR inactive at power-up.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. This PVD offers 7 different levels between 1.85 V and 3.05 V, chosen by software, with a step around 200 mV. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.3.3 Voltage regulator

The regulator has three operation modes: main (MR), low power (LPR) and power down.

- MR is used in Run mode (nominal regulation)
- LPR is used in the Low power run, Low power sleep and Stop modes
- Power down is used in Standby mode. The regulator output is high impedance, the kernel circuitry is powered down, inducing zero consumption but the contents of the registers and RAM are lost except for the standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE crystal 32K osc, RCC_CSR).

3.3.4 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from Flash memory
- Boot from System memory
- Boot from embedded RAM

The boot from Flash usually boots at the beginning of the Flash (bank 1). An additional boot mechanism is available through user option byte, to allow booting from bank 2 when bank 2 contains valid code. This dual boot capability can be used to easily implement a secure field software update mechanism.

The boot loader is located in System memory. It is used to reprogram the Flash memory by using USART1 and USART2. See STM32™ microcontroller system memory boot mode AN2606 for details.

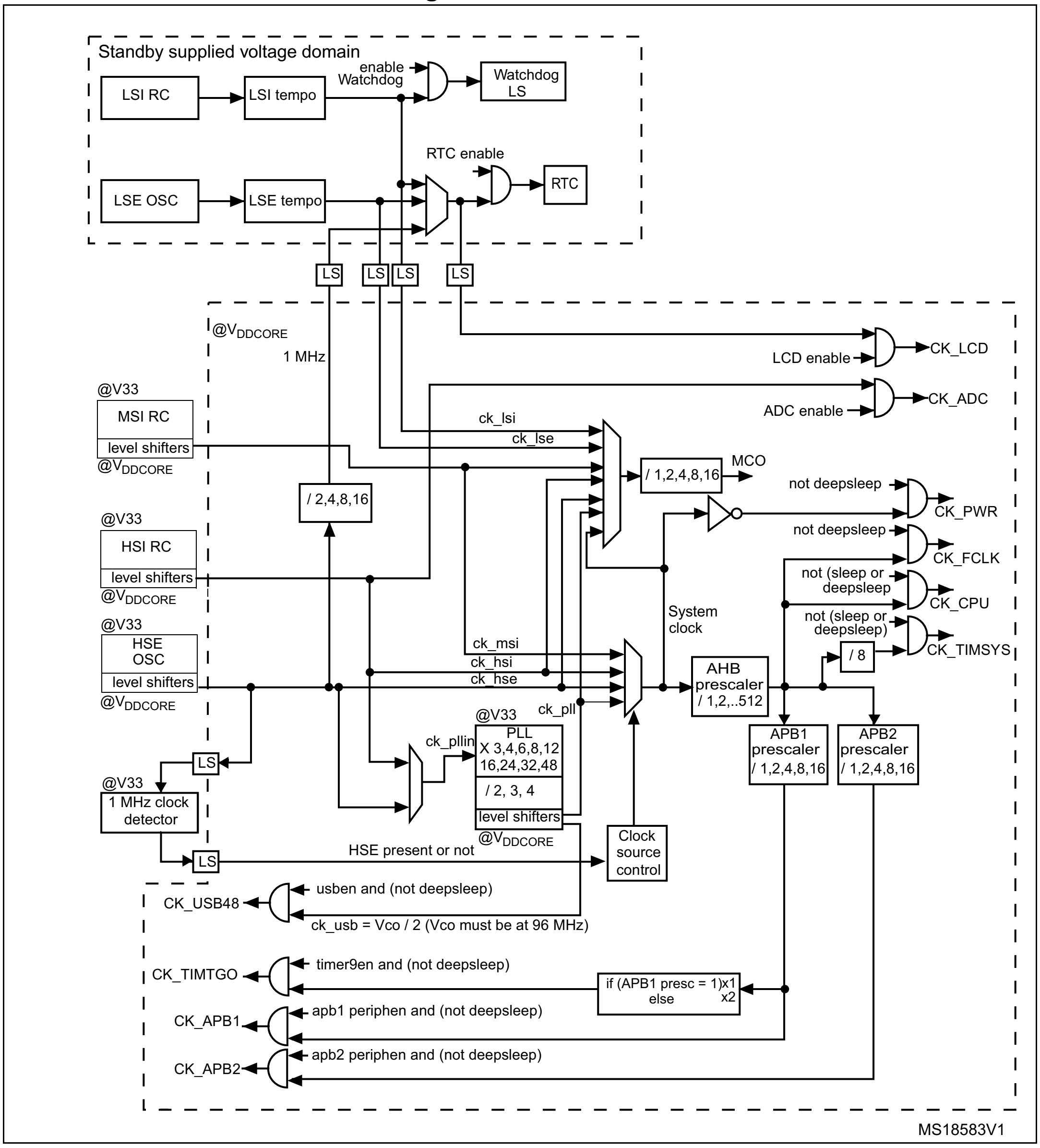
3.4 Clock management

The clock controller distributes the clocks coming from different oscillators to the core and the peripherals. It also manages clock gating for low power modes and ensures clock robustness. It features:

- **Clock prescaler**: to get the best trade-off between speed and current consumption, the clock frequency to the CPU and peripherals can be adjusted by a programmable prescaler.
- **Safe clock switching**: clock sources can be changed safely on the fly in run mode through a configuration register.
- **Clock management**: to reduce power consumption, the clock controller can stop the clock to the core, individual peripherals or memory.
- **System clock source**: three different clock sources can be used to drive the master clock SYSCLK:
  – 1-24 MHz high-speed external crystal (HSE), that can supply a PLL
  – 16 MHz high-speed internal RC oscillator (HSI), trimmable by software, that can supply a PLL
  – Multispeed internal RC oscillator (MSI), trimmable by software, able to generate 7 frequencies (65 kHz, 131 kHz, 262 kHz, 524 kHz, 1.05 MHz, 2.1 MHz, 4.2 MHz). When a 32.768 kHz clock source is available in the system (LSE), the MSI frequency can be trimmed by software down to a ±0.5% accuracy.
- **Auxiliary clock source**: two ultra-low-power clock sources that can be used to drive the LCD controller and the real-time clock:
  – 32.768 kHz low-speed external crystal (LSE)
  – 37 kHz low-speed internal RC (LSI), also used to drive the independent watchdog. The LSI clock can be measured using the high-speed internal RC oscillator for greater precision.
- **RTC and LCD clock sources:** the LSI, LSE or HSE sources can be chosen to clock the RTC and the LCD, whatever the system clock.
- **USB clock source:** the embedded PLL has a dedicated 48 MHz clock output to supply the USB interface.
- **Startup clock:** after reset, the microcontroller restarts by default with an internal 2 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.
- **Clock security system (CSS):** this feature can be enabled by software. If a HSE clock failure occurs, the master clock is automatically switched to HSI and a software interrupt is generated if enabled.
- **Clock-out capability (MCO: microcontroller clock output):** it outputs one of the internal clocks for external use by the application.

Several prescalers allow the configuration of the AHB frequency, each APB (APB1 and APB2) domains. The maximum frequency of the AHB and the APB domains is 32 MHz. See *Figure 2* for details on the clock tree.

Figure 2. Clock tree



1. For the USB function to be available, both HSE and PLL must be enabled, with the CPU running at either 24 MHz or 32 MHz.

3.5 Low power real-time clock and backup registers

The real-time clock (RTC) is an independent BCD timer/counter. Dedicated registers contain the sub-second, second, minute, hour (12/24 hour), week day, date, month, year, in BCD (binary-coded decimal) format. Correction for 28, 29 (leap year), 30, and 31 day of the month are made automatically. The RTC provides two programmable alarms and programmable periodic interrupts with wakeup from Stop and Standby modes.

The programmable wakeup time ranges from 120 µs to 36 hours.

The RTC can be calibrated with an external 512 Hz output, and a digital compensation circuit helps reduce drift due to crystal deviation.

The RTC can also be automatically corrected with a 50/60Hz stable powerline.

The RTC calendar can be updated on the fly down to sub second precision, which enables network system synchronisation.

A time stamp can record an external event occurrence, and generates an interrupt.

There are thirty-two 32-bit backup registers provided to store 128 bytes of user application data. They are cleared in case of tamper detection.

Three pins can be used to detect tamper events. A change on one of these pins can reset backup register and generate an interrupt. To prevent false tamper event, like ESD event, these three tamper inputs can be digitally filtered.

3.6 GPIOs (general-purpose inputs/outputs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated AFIO registers. All GPIOs are high current capable. The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to the AHB with a toggling speed of up to 16 MHz.

External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 24 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 83 GPIOs can be connected to the 16 external interrupt lines. The 8 other lines are connected to RTC, PVD, USB, comparator events or capacitive sensing acquisition.

3.7 Memories

The STM32L162xC devices have the following features:

- 32 Kbytes of embedded RAM accessed (read/write) at CPU clock speed with 0 wait states. With the enhanced bus matrix, operating the RAM does not lead to any performance penalty during accesses to the system bus (AHB and APB buses).
- The non-volatile memory is divided into three arrays:
  - 256 Kbytes of embedded Flash program memory
  - 8 Kbytes of data EEPROM
  - Options bytes

  The options bytes are used to write-protect the memory (with 4 KB granularity) and/or readout-protect the whole memory with the following options:
  - Level 0: no readout protection
  - Level 1: memory readout protection, the Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
  - Level 2: chip readout protection, debug features (ARM Cortex-M3 JTAG and serial wire) and boot in RAM selection disabled (JTAG fuse)

  The whole non-volatile memory embeds the error correction code (ECC) feature.

3.8 DMA (direct memory access)

The flexible 12-channel, general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA controller supports circular buffer management, avoiding the generation of interrupts when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with software trigger support for each channel. Configuration is done by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: AES, SPI, I^2C, USART, general-purpose timers, DAC and ADC.

3.9 LCD (liquid crystal display)

The LCD drives up to 8 common terminals and 44 segment terminals to drive up to 320 pixels.

- Internal step-up converter to guarantee functionality and contrast control irrespective of V_{DD}. This converter can be deactivated, in which case the V_{LCD} pin is used to provide the voltage to the LCD
- Supports static, 1/2, 1/3, 1/4 and 1/8 duty
- Supports static, 1/2, 1/3 and 1/4 bias
- Phase inversion to reduce power consumption and EMI
- Up to 8 pixels can be programmed to blink
- Unneeded segments and common pins can be used as general I/O pins
- LCD RAM can be updated at any time owing to a double-buffer
- The LCD controller can operate in Stop mode
- V_{LCD} rail decoupling capability

Table 5. V_{LCD} rail decoupling

	Bias			Pin	
	1/2	1/3	1/4		
V_{RAIL1}	1/2 V_{LCD}	2/3 V_{LCD}	1/2 V_{LCD}	PB2	
V_{RAIL2}	N/A	1/3 V_{LCD}	1/4 V_{LCD}	PB12	PE11
V_{RAIL3}	N/A	N/A	3/4 V_{LCD}	PB0	PE12

3.10 ADC (analog-to-digital converter)

A 12-bit analog-to-digital converters is embedded into STM32L162xC devices with up to 25 external channels, performing conversions in single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs with up to 24 external channels in a group.

The ADC can be served by the DMA controller.

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all scanned channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the general-purpose timers (TIMx) can be internally connected to the ADC start triggers, to allow the application to synchronize A/D conversions and timers. An injection mode allows high priority conversions to be done by interrupting a scan mode which runs in as a background task.

The ADC includes a specific low power mode. The converter is able to operate at maximum speed even if the CPU is operating at a very low frequency and has an auto-shutdown function. The ADC’s runtime and analog front-end current consumption are thus minimized whatever the MCU operating mode.

3.10.1 Temperature sensor

The temperature sensor (T_{SENSE}) generates a voltage V_{SENSE} that varies linearly with temperature.

The temperature sensor is internally connected to the ADC_IN16 input channel which is used to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode.

Table 6. Temperature sensor calibration values

Calibration value name	Description	Memory address
TSENSE_CAL1	TS ADC raw data acquired at temperature of 30 °C, V_{DDA}= 3 V	0x1FF8 00FA - 0x1FF8 00FB
TSENSE_CAL2	TS ADC raw data acquired at temperature of 110 °C V_{DDA}= 3 V	0x1FF8 00FE - 0x1FF8 00FF

3.10.2 Internal voltage reference (V_{REFINT})

The internal voltage reference (V_{REFINT}) provides a stable (bandgap) voltage output for the ADC and Comparators. V_{REFINT} is internally connected to the ADC_IN17 input channel. It enables accurate monitoring of the V_{DD} value (when no external voltage, VREF+, is available for ADC). The precise voltage of V_{REFINT} is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode.

Table 7. Internal voltage reference measured values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 30 °C V_{DDA}= 3 V	0x1FF8 00F8 - 0x1FF8 00F9

3.11 DAC (digital-to-analog converter)

The two 12-bit buffered DAC channels can be used to convert two digital signals into two analog voltage signal outputs. The chosen design structure is composed of integrated resistor strings and an amplifier in non-inverting configuration.

This dual digital Interface supports the following features:

- Two DAC converters: one for each output channel
- Up to 10-bit output
- Left or right data alignment in 12-bit mode
- Synchronized update capability
- Noise-wave generation
- Triangular-wave generation
- Dual DAC channels, independent or simultaneous conversions
- DMA capability for each channel (including the underrun interrupt)
- External triggers for conversion
- Input reference voltage V_{REF+}

Eight DAC trigger inputs are used in the STM32L162xC. The DAC channels are triggered through the timer update outputs that are also connected to different DMA channels.

3.12 Operational amplifier

The STM32L162xC embeds two operational amplifiers with external or internal follower routing capability (or even amplifier and filter capability with external components). When one operational amplifier is selected, one external ADC channel is used to enable output measurement.

The operational amplifiers feature:

- Low input bias current
- Low offset voltage
- Low power mode
- Rail-to-rail input

3.13 Ultra-low-power comparators and reference voltage

The STM32L162xC embeds two comparators sharing the same current bias and reference voltage. The reference voltage can be internal or external (coming from an I/O).

- One comparator with fixed threshold
- One comparator with rail-to-rail inputs, fast or slow mode. The threshold can be one of the following:
  - DAC output
  - External I/O
  - Internal reference voltage (V_{REFINT}) or a submultiple (1/4, 1/2, 3/4)

Both comparators can wake up from Stop mode, and be combined into a window comparator.

The internal reference voltage is available externally via a low power / low current output buffer (driving current capability of 1 µA typical).

3.14 System configuration controller and routing interface

The system configuration controller provides the capability to remap some alternate functions on different I/O ports.

The highly flexible routing interface allows the application firmware to control the routing of different I/Os to the TIM2, TIM3 and TIM4 timer input captures. It also controls the routing of internal analog signals to ADC1, COMP1 and COMP2 and the internal reference voltage V_{REFINT}.

3.15 Touch sensing

The STM32L162xC devices provide a simple solution for adding capacitive sensing functionality to any application. These devices offer up to 23 capacitive sensing channels distributed over 10 analog I/O groups. Both software and timer capacitive sensing acquisition modes are supported.

Capacitive sensing technology is able to detect the presence of a finger near a sensor which is protected from direct touch by a dielectric (glass, plastic, ...). The capacitive variation introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle. It consists of charging the sensor capacitance and then transferring a part of the accumulated charges into a sampling capacitor until the voltage across this capacitor has reached a specific threshold. The capacitive sensing acquisition only requires few external components to operate.

Reliable touch sensing functionality can be quickly and easily implemented using the free STM32L1xx STMTouch touch sensing firmware library.

3.16 AES

The AES Hardware Accelerator can be used to encrypt and decrypt data using the AES algorithm (compatible with FIPS PUB 197, 2001 Nov 26).

- Key scheduler
- Key derivation for decryption
- 128-bit data block processed
- 128-bit key length
- 213 clock cycles to encrypt/decrypt one 128-bit block
- Electronic codebook (ECB), cypher block chaining (CBC), and counter mode (CTR) supported by hardware.

AES data flow can be served by 2ch (D_{IN}/D_{OUT}) of the DMA2 controller

3.17 Timers and watchdogs

The ultra-low-power STM32L162xC devices include seven general-purpose timers, two basic timers, and two watchdog timers.

Table 8 compares the features of the general-purpose and basic timers.

Table 8. Timer feature comparison

Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
TIM2, TIM3, TIM4	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM5	32-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM9	16-bit	Up, down, up/down	Any integer between 1 and 65536	No	2	No
TIM10, TIM11	16-bit	Up	Any integer between 1 and 65536	No	1	No
TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

3.17.1 General-purpose timers (TIM2, TIM3, TIM4, TIM5, TIM9, TIM10 and TIM11)

There are seven synchronizable general-purpose timers embedded in the STM32L162xC devices (see *Table 8* for differences).

TIM2, TIM3, TIM4, TIM5

TIM2, TIM3, TIM4 are based on 16-bit auto-reload up/down counter. TIM5 is based on a 32-bit auto-reload up/down counter. They include a 16-bit prescaler. They feature four independent channels each for input capture/output compare, PWM or one-pulse mode output. This gives up to 16 input captures/output compares/PWMs on the largest packages.

TIM2, TIM3, TIM4, TIM5 general-purpose timers can work together or with the TIM10, TIM11 and TIM9 general-purpose timers via the Timer Link feature for synchronization or event chaining. Their counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs.

TIM2, TIM3, TIM4, TIM5 all have independent DMA request generation.

These timers are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

TIM10, TIM11 and TIM9

TIM10 and TIM11 are based on a 16-bit auto-reload upcounter. TIM9 is based on a 16-bit auto-reload up/down counter. They include a 16-bit prescaler. TIM10 and TIM11 feature one independent channel, whereas TIM9 has two independent channels for input capture/output compare, PWM or one-pulse mode output. They can be synchronized with the TIM2, TIM3, TIM4, TIM5 full-featured general-purpose timers.

They can also be used as simple time bases and be clocked by the LSE clock source (32.768 kHz) to provide time bases independent from the main CPU clock.

3.17.2 Basic timers (TIM6 and TIM7)

These timers are mainly used for DAC trigger generation. They can also be used as generic 16-bit time bases.

3.17.3 SysTick timer

This timer is dedicated to the OS, but could also be used as a standard downcounter. It is based on a 24-bit downcounter with autoreload capability and a programmable clock source. It features a maskable system interrupt generation when the counter reaches 0.

3.17.4 Independent watchdog (IWDG)

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 37 kHz internal RC and, as it operates independently of the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes. The counter can be frozen in debug mode.

3.17.5 Window watchdog (WWDG)

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

3.18 Communication interfaces

3.18.1 I²C bus

Up to two I²C bus interfaces can operate in multimaster and slave modes. They can support standard and fast modes.

They support dual slave addressing (7-bit only) and both 7- and 10-bit addressing in master mode. A hardware CRC generation/verification is embedded.

They can be served by DMA and they support SM Bus 2.0/PM Bus.

3.18.2 Universal synchronous/asynchronous receiver transmitter (USART)

The three USART interfaces are able to communicate at speeds of up to 4 Mbit/s. They support IrDA SIR ENDEC, are ISO 7816 compliant and have LIN Master/Slave capability. The three USARTs provide hardware management of the CTS and RTS signals.

All USART interfaces can be served by the DMA controller.

3.18.3 Serial peripheral interface (SPI)

Up to three SPIs are able to communicate at up to 16 Mbits/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

The SPIs can be served by the DMA controller.

3.18.4 Inter-integrated sound (I^2S)

Two standard I2S interfaces (multiplexed with SPI2 and SPI3) are available. They can operate in master or slave mode, and can be configured to operate with a 16-/32-bit resolution as input or output channels. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When either or both of the I2S interfaces is/are configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

The I2Ss can be served by the DMA controller.

3.18.5 Universal serial bus (USB)

The STM32L162xC embeds a USB device peripheral compatible with the USB full-speed 12 Mbit/s. The USB interface implements a full-speed (12 Mbit/s) function interface. It has software-configurable endpoint setting and supports suspend/resume. The dedicated 48 MHz clock is generated from the internal main PLL (the clock source must use a HSE crystal oscillator).

3.19 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

3.20 Development support

Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target. The JTAG JTMS and JTCK pins are shared with SWDAT and SWCLK, respectively, and a specific sequence on the JTMS pin is used to switch between JTAG-DP and SW-DP.

The JTAG port can be permanently disabled with a JTAG fuse.

Embedded Trace Macrocell™

The ARM® Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32L162xC through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using USB, Ethernet, or any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer running debugger software. TPA hardware is commercially available from common development tool vendors. It operates with third party debugger software tools.

4 Pin descriptions

Figure 3. STM32L162VC LQFP100 pinout

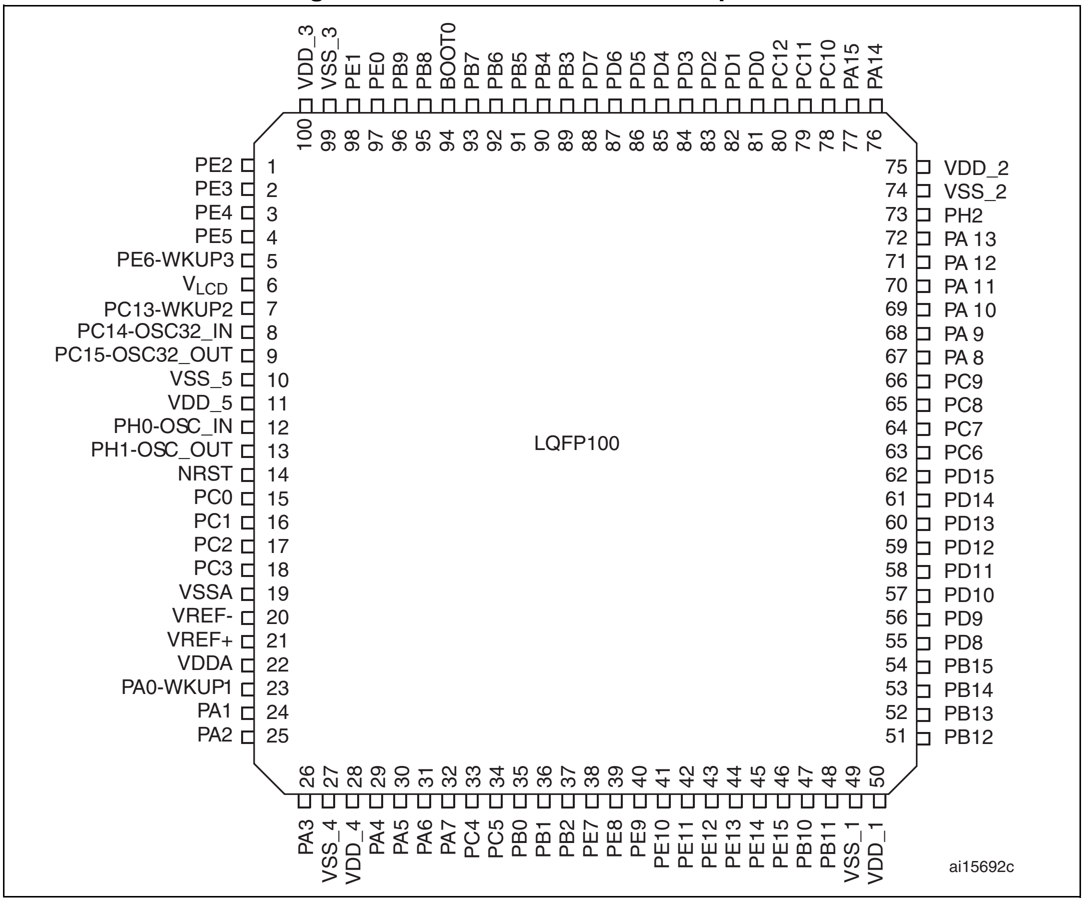


Figure 4. STM32L162RC LQFP64 pinout

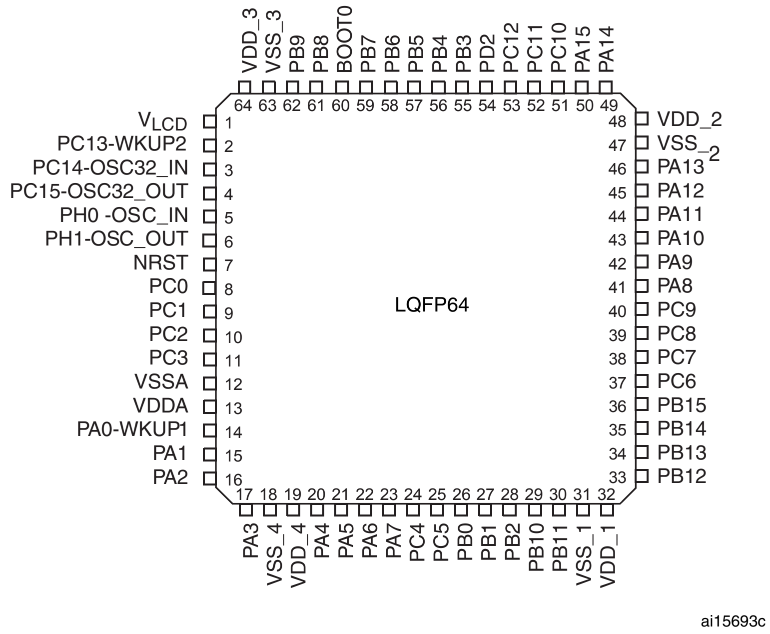


Table 9. STM32L162xC pin definitions

Pins		Pin name	Type[(1)]	I / O Level[(2)]	Main function[(3)] (after reset)	Alternate functions
LQFP100	LQFP64					
1	-	PE2	I/O	FT	PE2	TIM3_ETR/LCD_SEG38/TRACECLK
2	-	PE3	I/O	FT	PE3	TIM3_CH1/LCD_SEG39/TRACED0
3	-	PE4	I/O	FT	PE4	TIM3_CH2/TRACED1
4	-	PE5	I/O	FT	PE5	TIM9_CH1/TRACED2
5	-	PE6-WKUP3	I/O	FT	PE6	WKUP3/RTC_TAMP3/TIM9_CH2/TRACED3
6	1	V_{LCD}[(4)]	S		V_{LCD}	
7	2	PC13-WKUP2	I/O	FT	PC13	WKUP2/RTC_TAMP1/RTC_TS/RTC_OUT
8	3	PC14-OSC32_IN[(5)]	I/O		PC14	OSC32_IN
9	4	PC15-OSC32_OUT	I/O		PC15	OSC32_OUT
10	-	V_{SS_5}	S		V_{SS_5}	

Table 9. STM32L162xC pin definitions (continued)

Pins		Pin name	Type[(1)]	I / O Level[(2)]	Main function[(3)] (after reset)	Alternate functions
LQFP100	LQFP64					
11	-	V_{DD_5}	S		V_{DD_5}	
12	5	PH0-OSC_IN[(6)]	I/O		PH0	OSC_IN
13	6	PH1-OSC_OUT[(6)]	I/O		PH1	OSC_OUT
14	7	NRST	I/O		NRST	
15	8	PC0	I/O	FT	PC0	LCD_SEG18/ADC_IN10/COMP1_INP
16	9	PC1	I/O	FT	PC1	LCD_SEG19/ADC_IN11/COMP1_INP
17	10	PC2	I/O	FT	PC2	LCD_SEG20/ADC_IN12/COMP1_INP
18	11	PC3	I/O		PC3	LCD_SEG21/ADC_IN13/COMP1_INP
19	12	V_{SSA}	S		V_{SSA}	
20	-	V_{REF-}	S		V_{REF-}	
21	-	V_{REF+}	S		V_{REF+}	
22	13	V_{DDA}	S		V_{DDA}	
23	14	PA0-WKUP1	I/O	FT	PA0	WKUP1/RTC_TAMP2/TIM2_CH1_ETR/TIM5_CH1/ USART2_CTS/ADC_IN0/COMP1_INP
24	15	PA1	I/O	FT	PA1	TIM2_CH2/TIM5_CH2/ USART2_RTS/LCD_SEG0/ ADC_IN1/COMP1_INP/OPAMP1_VINP
25	16	PA2	I/O	FT	PA2	TIM2_CH3/TIM5_CH3/TIM9_CH1/USART2_TX/ LCD_SEG1/ADC_IN2/COMP1_INP/OPAMP1_VINM
26	17	PA3	I/O		PA3	TIM2_CH4/TIM5_CH4/TIM9_CH2/USART2_RX/ LCD_SEG2/ADC_IN3/COMP1_INP/ OPAMP1_VOUT
27	18	V_{SS_4}	S		V_{SS_4}	
28	19	V_{DD_4}	S		V_{DD_4}	
29	20	PA4	I/O		PA4	SPI1_NSS/SPI3_NSS/I2S3_WS/USART2_CK/ ADC_IN4/DAC_OUT1/COMP1_INP
30	21	PA5	I/O		PA5	TIM2_CH1_ETR/SPI1_SCK/ADC_IN5/DAC_OUT2/ COMP1_INP
31	22	PA6	I/O	FT	PA6	TIM3_CH1/TIM10_CH1/SPI1_MISO/LCD_SEG3/ ADC_IN6/COMP1_INP/OPAMP2_VINP
32	23	PA7	I/O	FT	PA7	TIM3_CH2/TIM11_CH1/SPI1_MOSI/LCD_SEG4/ ADC_IN7/COMP1_INP/OPAMP2_VINM

Table 9. STM32L162xC pin definitions (continued)

Pins		Pin name	Type[1]	I / O Level[2]	Main function[3] (after reset)	Alternate functions
LQFP100	LQFP64					
33	24	PC4	I/O	FT	PC4	LCD_SEG22/ADC_IN14/COMP1_INP
34	25	PC5	I/O	FT	PC5	LCD_SEG23/ADC_IN15/COMP1_INP
35	26	PB0	I/O		PB0	TIM3_CH3/LCD_SEG5/ADC_IN8/COMP1_INP/ VREF_OUT/OPAMP2_VOUT
36	27	PB1	I/O	FT	PB1	TIM3_CH4/LCD_SEG6/ADC_IN9/COMP1_INP/ VREF_OUT
37	28	PB2	I/O	FT	PB2/BOOT1	COMP1_INP
38	-	PE7	I/O		PE7	ADC_IN22/COMP1_INP
39	-	PE8	I/O		PE8	ADC_IN23/COMP1_INP
40	-	PE9	I/O		PE9	TIM2_CH1_ETR/ADC_IN24/TIM5_ETR/ COMP1_INP
41	-	PE10	I/O		PE10	TIM2_CH2/ADC_IN25/COMP1_INP
42	-	PE11	I/O	FT	PE11	TIM2_CH3
43	-	PE12	I/O	FT	PE12	TIM2_CH4/SPI1_NSS
44	-	PE13	I/O	FT	PE13	SPI1_SCK
45	-	PE14	I/O	FT	PE14	SPI1_MISO
46	-	PE15	I/O	FT	PE15	SPI1_MOSI
47	29	PB10	I/O	FT	PB10	TIM2_CH3/I2C2_SCL/USART3_TX/LCD_SEG10
48	30	PB11	I/O	FT	PB11	TIM2_CH4/I2C2_SDA/USART3_RX/LCD_SEG11
49	31	V_{SS_1}	S		V_{SS_1}	
50	32	V_{DD_1}	S		V_{DD_1}	
51	33	PB12	I/O	FT	PB12	TIM10_CH1/I2C2_SMBA/SPI2_NSS/I2S2_WS/ USART3_CK/LCD_SEG12/ADC_IN18/COMP1_INP
52	34	PB13	I/O	FT	PB13	TIM9_CH1/SPI2_SCK/ I2S2_CK/ USART3_CTS/ LCD_SEG13/ADC_IN19/COMP1_INP
53	35	PB14	I/O	FT	PB14	TIM9_CH2/SPI2_MISO/ USART3_RTS/LCD_SEG14/ ADC_IN20/COMP1_INP
54	36	PB15	I/O	FT	PB15	TIM11_CH1/SPI2_MOSI/I2S2_SD/LCD_SEG15/ ADC_IN21/COMP1_INP/RTC_REFIN
55	-	PD8	I/O	FT	PD8	USART3_TX/LCD_SEG28
56	-	PD9	I/O	FT	PD9	USART3_RX/LCD_SEG29

Table 9. STM32L162xC pin definitions (continued)

Pins LQFP100	Pins LQFP64	Pin name	Type(1)	I / O Level(2)	Main function(3) (after reset)	Alternate functions
57	-	PD10	I/O	FT	PD10	USART3_CK/LCD_SEG30
58	-	PD11	I/O	FT	PD11	USART3_CTS/LCD_SEG31
59	-	PD12	I/O	FT	PD12	TIM4_CH1/USART3_RTS/LCD_SEG32
60	-	PD13	I/O	FT	PD13	TIM4_CH2/LCD_SEG33
61	-	PD14	I/O	FT	PD14	TIM4_CH3/LCD_SEG34
62	-	PD15	I/O	FT	PD15	TIM4_CH4/LCD_SEG35
63	37	PC6	I/O	FT	PC6	TIM3_CH1/I2S2_MCK/LCD_SEG24
64	38	PC7	I/O	FT	PC7	TIM3_CH2/I2S3_MCK/LCD_SEG25
65	39	PC8	I/O	FT	PC8	TIM3_CH3/LCD_SEG26
66	40	PC9	I/O	FT	PC9	TIM3_CH4/LCD_SEG27
67	41	PA8	I/O	FT	PA8	USART1_CK/MCO/LCD_COM0
68	42	PA9	I/O	FT	PA9	USART1_TX/LCD_COM1
69	43	PA10	I/O	FT	PA10	USART1_RX/LCD_COM2
70	44	PA11	I/O	FT	PA11	USART1_CTS/USB_DM/SPI1_MISO
71	45	PA12	I/O	FT	PA12	USART1_RTS/USB_DP/SPI1_MOSI
72	46	PA13	I/O	FT	JTMS-SWDAT	
73	-	PH2	I/O	FT	PH2	
74	47	V_{SS_2}	S		V_{SS_2}	
75	48	V_{DD_2}	S		V_{DD_2}	
76	49	PA14	I/O	FT	JTCK-SWCLK	
77	50	PA15	I/O	FT	JTDI	TIM2_CH1_ETR/SPI1_NSS/SPI3_NSS/I2S3_WS/ LCD_SEG17
78	51	PC10	I/O	FT	PC10	SPI3_SCK/I2S3_CK/USART3_TX/LCD_SEG28/ LCD_SEG40/LCD_COM4
79	52	PC11	I/O	FT	PC11	SPI3_MISO/USART3_RX/LCD_SEG29/LCD_SEG4/ LCD_COM5/
80	53	PC12	I/O	FT	PC12	SPI3_MOSI/I2S3_SD/USART3_CK/LCD_SEG30/ LCD_SEG42/LCD_COM6
81	-	PD0	I/O	FT	PD0	TIM9_CH1/SPI2_NSS/I2S2_WS

Table 9. STM32L162xC pin definitions (continued)

Pins		Pin name	Type[1]	I / O Level[2]	Main function[3] (after reset)	Alternate functions
LQFP100	LQFP64					
82	-	PD1	I/O	FT	PD1	SPI2_SCK/I2S2_CK
83	54	PD2	I/O	FT	PD2	TIM3_ETR/LCD_SEG31/LCD_SEG43/LCD_COM7
84	-	PD3	I/O	FT	PD3	SPI2_MISO/USART2_CTS
85	-	PD4	I/O	FT	PD4	SPI2_MOSI/I2S2_SD/USART2_RTS
86	-	PD5	I/O	FT	PD5	USART2_TX
87	-	PD6	I/O	FT	PD6	USART2_RX
88	-	PD7	I/O	FT	PD7	TIM9_CH2/USART2_CK
89	55	PB3	I/O	FT	JTDO	TIM2_CH2/SPI1_SCK/SPI3_SCK/I2S3_CK/ LCD_SEG7/COMP2_INM
90	56	PB4	I/O	FT	NJTRST	TIM3_CH1/SPI1_MISO/SPI3_MISO/LCD_SEG8/ COMP2_INP
91	57	PB5	I/O	FT	PB5	TIM3_CH2/I2C1_SMBA/SPI1_MOSI/SPI3_MOSI/ I2S3_SD/LCD_SEG9/COMP2_INP
92	58	PB6	I/O	FT	PB6	TIM4_CH1/I2C1_SCL/USART1_TX/COMP2_INP
93	59	PB7	I/O	FT	PB7	TIM4_CH2/I2C1_SDA/USART1_RX/PVD_IN/ COMP2_INP
94	60	BOOT0	I		BOOT0	
95	61	PB8	I/O	FT	PB8	TIM4_CH3/TIM10_CH1/I2C1_SCL/LCD_SEG16
96	62	PB9	I/O	FT	PB9	TIM4_CH4/ TIM11_CH1/I2C1_SDA/LCD_COM3
97	-	PE0	I/O	FT	PE0	TIM4_ETR/TIM10_CH1/LCD_SEG36
98	-	PE1	I/O	FT	PE1	TIM11_CH1/LCD_SEG37
99	63	V_{SS_3}	S		V_{SS_3}	
100	64	V_{DD_3}	S		V_{DD_3}	

1. I = input, O = output, S = supply.
2. FT = 5 V tolerant.
3. Function availability depends on the chosen device.
4. Applicable to STM32L152xC devices only. In STM32L151xC devices, this pin should be connected to V_{DD}.
5. The PC14 and PC15 I/Os are only configured as OSC32_IN/OSC32_OUT when the LSE oscillator is ON (by setting the LSEON bit in the RCC_CSR register). The LSE oscillator pins OSC32_IN/OSC32_OUT can be used as general-purpose PH0/PH1 I/Os, respectively, when the LSE oscillator is off (after reset, the LSE oscillator is off). The LSE has priority over the GPIO function. For more details, refer to Using the OSC32_IN/OSC32_OUT pins as GPIO PC14/PC15 port pins section in the STM32L151xx, STM32L152xx and STM32L162xx reference manual (RM0038).

6. The PH0 and PH1 I/Os are only configured as OSC_IN/OSC_OUT when the HSE oscillator is ON (by setting the HSEON bit in the RCC_CR register). The HSE oscillator pins OSC_IN/OSC_OUT can be used as general-purpose PH0/PH1 I/Os, respectively, when the HSE oscillator is off (after reset, the HSE oscillator is off). The HSE has priority over the GPIO function.

Table 10. Alternate function input/output

Port name	Digital alternate function number													
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	. .	AFIO10	AFIO11	. .	AFIO14	AFIO15
	Alternate function													
	SYSTEM	TIM2	TIM3/4/5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/3		USB	LCD		CPRI	SYSTEM
BOOT0	BOOT0													EVENT OUT
NRST	NRST													
PA0-WKUP1	WKUP1/ TAMPER2	TIM2_CH1_ ETR	TIM5_CH1					USART2_CTS					COMP1_INP/ TIMx_IC1_0/ G1IO1	EVENT OUT
PA1		TIM2_CH2	TIM5_CH2					USART2_RTS			SEG0		COMP1_INP/ TIMx_IC2_0 G1IO2	EVENT OUT
PA2		TIM2_CH3	TIM5_CH3	TIM9_CH1				USART2_TX			SEG1		COMP1_INP/ TIMx_IC3_0/ G1IO3	EVENT OUT
PA3		TIM2_CH4	TIM5_CH4	TIM9_CH2				USART2_RX			SEG2		COMP1_INP/ TIMx_IC4_0/ G1IO4	EVENT OUT
PA4						SPI1_NSS	SPI3_NSS I2S3_WS	USART2_CK					COMP1_INP/ TIMx_IC1_1	EVENT OUT
PA5		TIM2_CH1_ETR*				SPI1_SCK							COMP1_INP/ TIMx_IC2_1	EVENT OUT
PA6			TIM3_CH1	TIM10_ CH1		SPI1_MISO					SEG3		COMP1_INP/ TIMx_IC3_1 G2IO1	EVENT OUT
PA7			TIM3_CH2	TIM11_ CH1		SPI1_MOSI					SEG4		COMP1_INP/ TIMx_IC4_1/ G2IO2	EVENT OUT
PA8	MCO							USART1_CK			COM0		TIMx_IC1_2/ G4IO1	EVENT OUT
PA9								USART1_TX			COM1		TIMx_IC2_2/ G4IO2	EVENT OUT
PA10								USART1_RX			COM2		TIMx_IC3_2/ G4IO3	EVENT OUT
PA11						SPI1_MISO		USART1_CTS		USB_DM			TIMx_IC4_2	EVENT OUT
PA12						SPI1_MOSI		USART1_RTS		USB_DP			TIMx_IC1_3/	EVENT OUT
PA13	JTMS-SWDIO												TIMx_IC2_3/ G5IO1	EVENT OUT
PA14	JTCK-SWCLK												TIMx_IC3_3/ G5IO2	EVEN TOUT
PA15	JTDI	TIM2_CH1_ETR				SPI1_NSS	SPI3_NSS I2S3_WS				SEG17		TIMx_IC4_3/ G5IO3	EVEN TOUT
PB0			TIM3_CH3								SEG5		COMP1_INP/ G3IO1	EVEN TOUT
PB1			TIM3_CH4								SEG6		COMP1_INP/ G3IO2	EVENT OUT

Table 10. Alternate function input/output (continued)

Port name	Digital alternate function number													
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	..	AFIO10	AFIO11	..	AFIO14	AFIO15
	Alternate function													
	SYSTEM	TIM2	TIM3/4/5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/3		USB	LCD		CPRI	SYSTEM
PB2	BOOT1												COMP1_INP/ G3IO3	EVENT OUT
PB3	JTDO	TIM2_CH2				SPI1_SCK	SPI3_SCK I2S3_CK				SEG7			EVENT OUT
PB4	JTRST		TIM3_CH1			SPI1_MISO	SPI3_MISO				SEG8		G6IO1	EVENT OUT
PB5			TIM3_CH2		I2C1_ SMBA	SPI1_MOSI	SPI3_MOSI I2S3_SD				SEG9		G6IO2	EVENT OUT
PB6			TIM4_CH1		I2C1_SCL			USART1_TX					G6IO3	EVENT OUT
PB7			TIM4_CH2		I2C1_SDA			USART1_RX					G6IO4	EVENT OUT
PB8			TIM4_CH3	TIM10_ CH1	I2C1_SCL						SEG16			EVENT OUT
PB9			TIM4_CH4	TIM11_ CH1	I2C1_SDA						COM3			EVENT OUT
PB10		TIM2_CH3			I2C2_SCL			USART3_TX			SEG10			EVENT OUT
PB11		TIM2_CH4			I2C2_SDA			USART3_RX			SEG11			EVENT OUT
PB12				TIM10_ CH1	I2C2_SMBA	SPI2_NSS I2S2_WS		USART3_CK			SEG12		COMP1_INP/ G7IO1	EVENT OUT
PB13				TIM9_ CH1		SPI2_SCK I2S2_CK		USART3_CTS			SEG13		COMP1_INP/ G7IO2	EVENT OUT
PB14				TIM9_ CH2		SPI2_MISO		USART3_RTS			SEG14		COMP1_INP/ G7IO3	EVENT OUT
PB15	RTC_REFIN			TIM11_ CH1		SPI2_MOSI I2S2_SD					SEG15		COMP1_INP/ G7IO4	EVENT OUT
PC0											SEG18		COMP1_INP/ TIMx_IC1_4/ G8IO1	EVENT OUT
PC1											SEG19		COMP1_INP/ TIMx_IC2_4/ G8IO2	EVENT OUT
PC2											SEG20		COMP1_INP/ TIMx_IC3_4/ G8IO3	EVENT OUT
PC3											SEG21		COMP1_INP/ TIMx_IC4_4/ G8IO4	EVENT OUT
PC4											SEG22		COMP1_INP/ TIMx_IC1_5/ G9IO1	EVENT OUT

Table 10. Alternate function input/output (continued)

Port name	Digital alternate function number													
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	. .	AFIO10	AFIO11	. .	AFIO14	AFIO15
	Alternate function													
	SYSTEM	TIM2	TIM3/4/5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/3		USB	LCD		CPRI	SYSTEM
PC5											SEG23		COMP1_INP/ TIMx_IC2_5/ G9IO2	EVENT OUT
PC6			TIM3_CH1			I2S2_MCK					SEG24		TIMx_IC3_5/ G10IO1	EVENT OUT
PC7			TIM3_CH2				I2S3_MCK				SEG25		TIMx_IC4_5/ G10IO2	EVENT OUT
PC8			TIM3_CH3								SEG26		TIMx_IC1_6/ G10IO3	EVENT OUT
PC9			TIM3_CH4								SEG27		TIMx_IC2_6/ G10IO4	EVENT OUT
PC10							SPI3_SCK I2S3_CK	USART3_TX			COM4/ SEG28/ SEG40		TIMx_IC3_6	EVENT OUT
PC11							SPI3_MISO	USART3_RX			COM5/ SEG29 /SEG41		TIMx_IC4_6	EVENT OUT
PC12							SPI3_MOSI I2S3_SD	USART3_CK			COM6/ SEG30/ SEG42		TIMx_IC1_7	EVENT OUT
PC13-WKUP2	WKUP2/ TAMPER1/ TIMESTAMP/ ALARM_OUT/512Hz												TIMx_IC2_7	EVENT OUT
PC14 OSC32_IN	OSC32_IN												TIMx_IC3_7	EVENT OUT
PC15 OSC32_OUT	OSC32_OUT												TIMx_IC4_7	EVENT OUT
PD0				TIM9_CH1		SPI2_NSS I2S2_WS							TIMx_IC1_8	EVENT OUT
PD1						SPI2 SCK I2S2_CK							TIMx_IC2_8	EVENT OUT
PD2			TIM3_ETR								COM7/ SEG31/ SEG43		TIMx_IC3_8	EVENT OUT
PD3						SPI2_MISO		USART2_CTS					TIMx_IC4_8	EVENT OUT
PD4						SPI2_MOSI I2S2_SD		USART2_RTS					TIMx_IC1_9	EVENT OUT

Table 10. Alternate function input/output (continued)

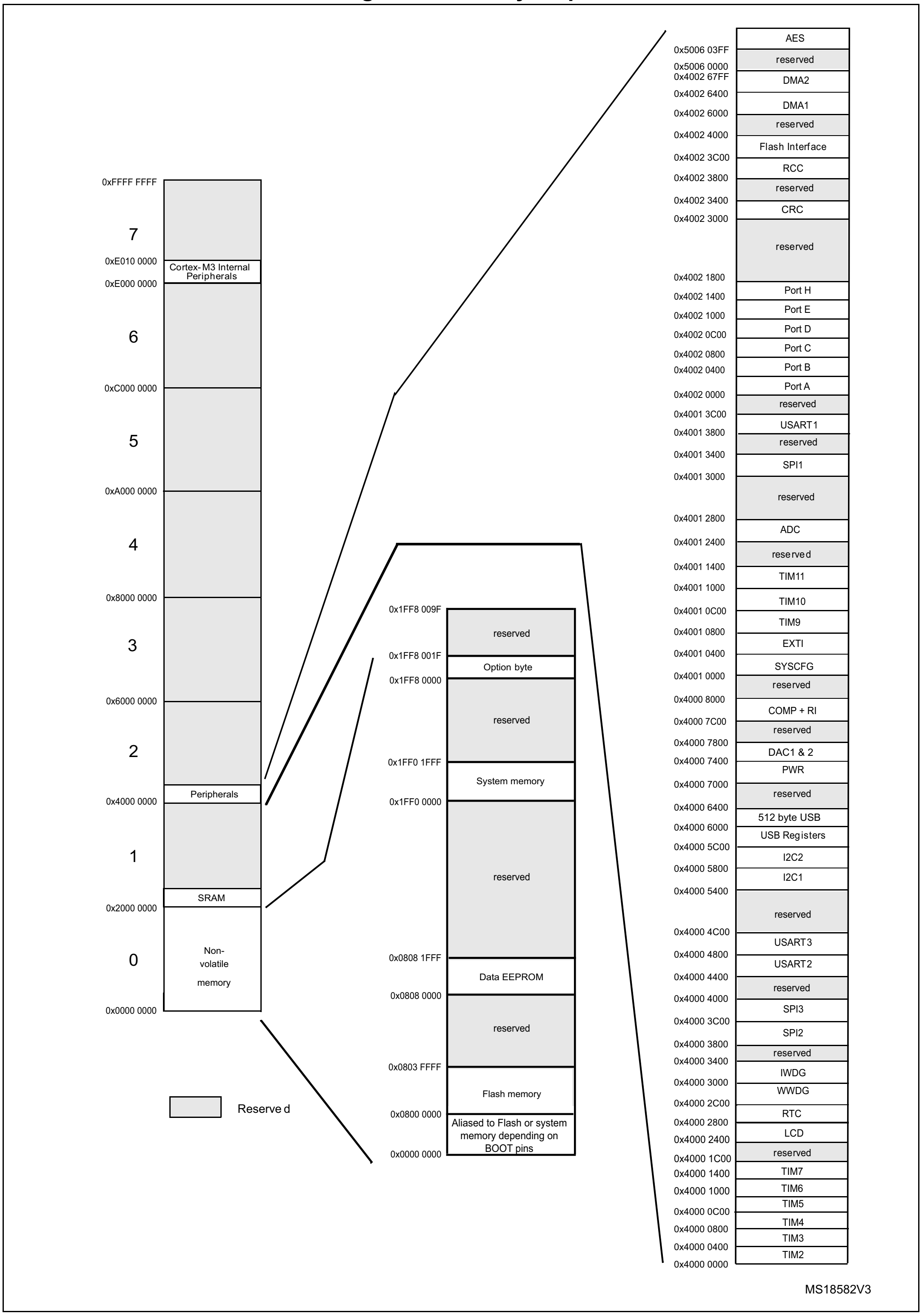
Port name	Digital alternate function number													
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	. .	AFIO10	AFIO11	. .	AFIO14	AFIO15
	Alternate function													
	SYSTEM	TIM2	TIM3/4/5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/3		USB	LCD		CPRI	SYSTEM
PD5								USART2_TX					TIMx_IC2_9	EVENT OUT
PD6								USART2_RX					TIMx_IC3_9	EVENT OUT
PD7				TIM9_CH2				USART2_CK					TIMx_IC4_9	EVENT OUT
PD8								USART3_TX			SEG28		TIMx_IC1_10	EVENT OUT
PD9								USART3_RX			SEG29		TIMx_IC2_10	EVENT OUT
PD10								USART3_CK			SEG30		TIMx_IC3_10	EVENT OUT
PD11								USART3_CTS			SEG31		TIMx_IC4_10	EVENT OUT
PD12			TIM4_CH1					USART3_RTS			SEG32		TIMx_IC1_11	EVENT OUT
PD13			TIM4_CH2								SEG33		TIMx_IC2_11	EVENT OUT
PD14			TIM4_CH3								SEG34		TIMx_IC3_11	EVENT OUT
PD15			TIM4_CH4								SEG35		TIMx_IC4_11	EVENT OUT
PE0			TIM4_ETR	TIM10_ CH1							SEG36		TIMx_IC1_12	EVENT OUT
PE1				TIM11_ CH1							SEG37		TIMx_IC2_12	EVENT OUT
PE2	TRACECK		TIM3_ETR								SEG 38		TIMx_IC3_12	EVENT OUT
PE3	TRACED0		TIM3_CH1								SEG 39		TIMx_IC4_12	EVENT OUT
PE4	TRACED1		TIM3_CH2										TIMx_IC1_13	EVENT OUT
PE5	TRACED2			TIM9_CH1									TIMx_IC2_13	EVENT OUT
PE6- WKUP3	WKUP3/ TAMPER3 / TRACED3			TIM9_CH2									TIMx_IC3_13	EVENT OUT
PE7													COMP1_INP/ TIMx_IC4_13	EVENT OUT
PE8													COMP1_INP/ TIMx_IC1_14	EVENT OUT
PE9		TIM2_CH1_ETR	TIM5_ETR										COMP1_INP/ TIMx_IC2_14	EVENT OUT

Table 10. Alternate function input/output (continued)

Port name	Digital alternate function number													
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	. .	AFIO10	AFIO11	. .	AFIO14	AFIO15
	Alternate function													
	SYSTEM	TIM2	TIM3/4/5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/3		USB	LCD		CPRI	SYSTEM
PE10		TIM2_CH2											COMP1_INP/ TIMx_IC3_14	EVENT OUT
PE11		TIM2_CH3											TIMx_IC4_14	EVENT OUT
PE12		TIM2_CH4				SPI1_NSS							TIMx_IC1_15	EVENT OUT
PE13						SPI1_SCK							TIMx_IC2_15	EVENT OUT
PE14						SPI1_MISO							TIMx_IC3_15	EVENT OUT
PE15						SPI1_MOSI							TIMx_IC4_15	EVENT OUT
PH0OSC_ IN	OSC_IN													
PH1OSC_ OUT	OSC_OUT													
PH2														

5 Memory mapping

Figure 5. Memory map



6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3Σ).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.6 V (for the 1.65 V ≤ V_{DD} ≤ 3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2Σ).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 6*.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 7*.

Figure 6. Pin loading conditions

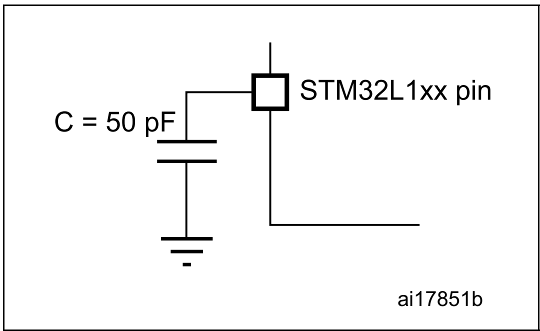
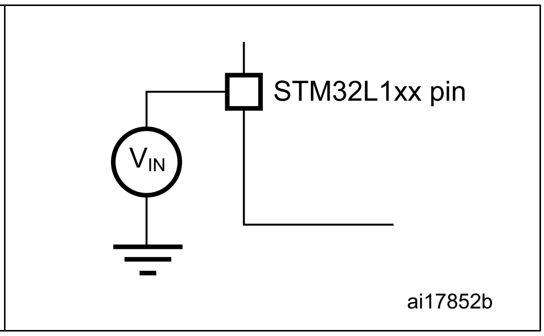
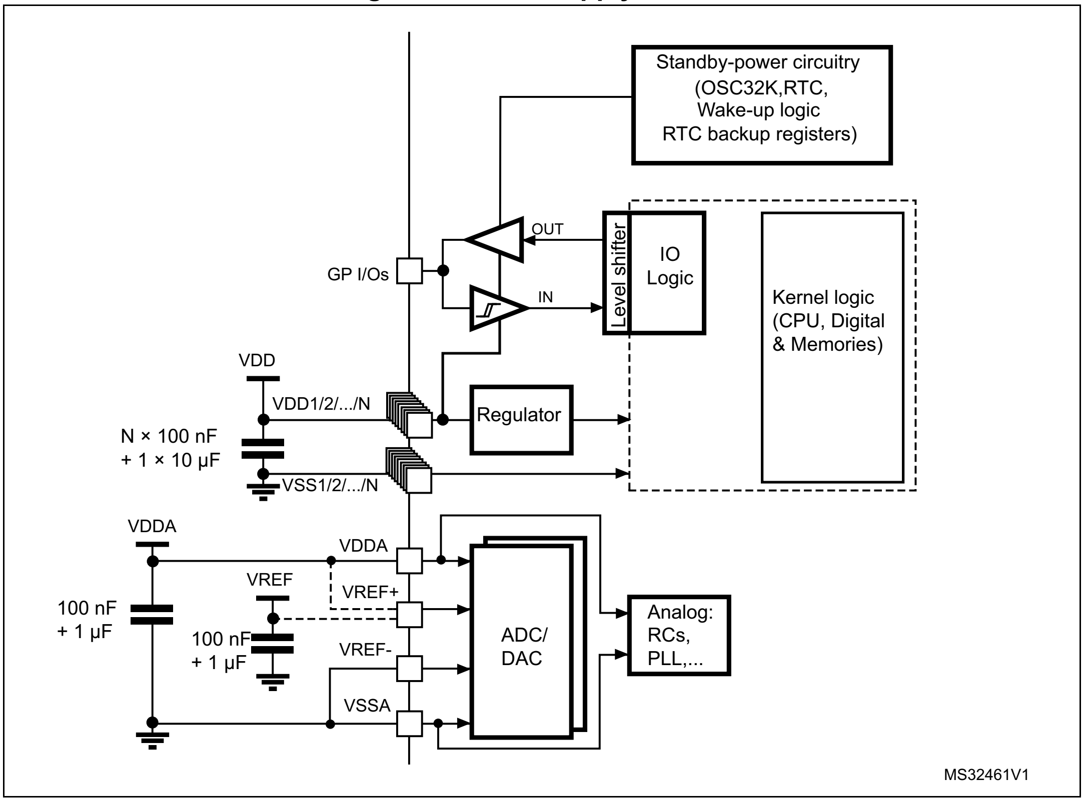


Figure 7. Pin input voltage



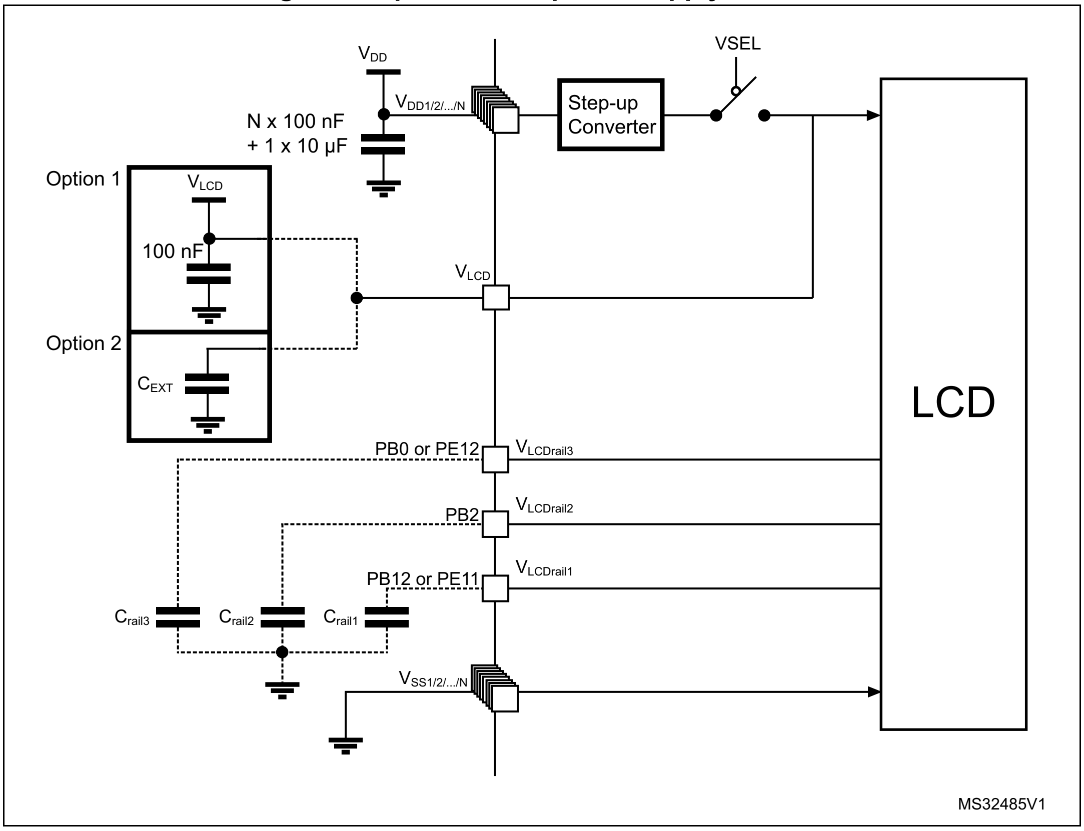
6.1.6 Power supply scheme

Figure 8. Power supply scheme



6.1.7 Optional LCD power supply scheme

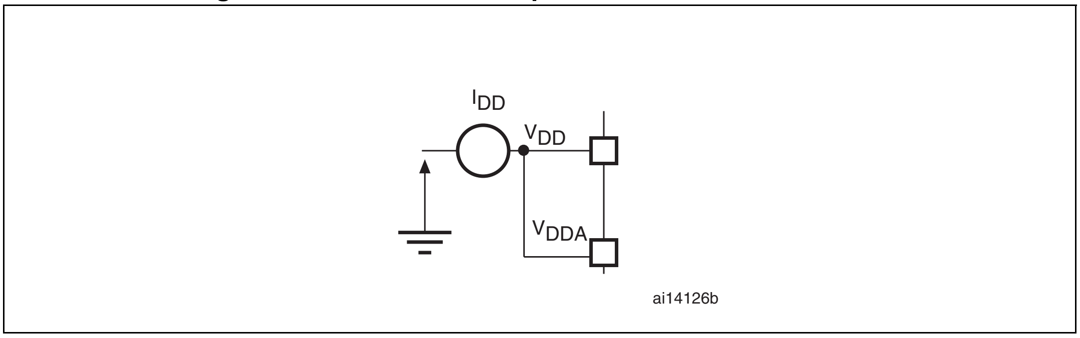
Figure 9. Optional LCD power supply scheme



1. Option 1: LCD power supply is provided by a dedicated VLCD supply source, VSEL switch is open.
2. Option 2: LCD power supply is provided by the internal step-up converter, VSEL switch is closed, an external capacitance is needed for correct behavior of this converter.

6.1.8 Current consumption measurement

Figure 10. Current consumption measurement scheme



6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 11: Voltage characteristics*, *Table 12: Current characteristics*, and *Table 13: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 11. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
$V_{DD}–V_{SS}$	External main supply voltage (including V_{DDA} and V_{DD})(1)	–0.3	4.0	V
V_{IN}(2)	Input voltage on five-volt tolerant pin	$V_{SS} - 0.3$	$V_{DD}+4.0$	V
	Input voltage on any other pin	$V_{SS} - 0.3$	4.0	V
$\lvert\Delta V_{DDx}\rvert$	Variations between different V_{DD} power pins		50	mV
$\lvert V_{SSX} - V_{SS}\rvert$	Variations between all different ground pins		50	mV
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see *Section 6.3.10*		

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum must always be respected. Refer to *Table 12* for maximum allowed injected current values.

Table 12. Current characteristics

Symbol	Ratings	Max.	Unit
I_{VDD}	Total current into V_{DD}/V_{DDA} power lines (source)(1)	80	mA
I_{VSS}	Total current out of V_{SS} ground lines (sink)(1)	80	mA
I_{IO}	Output current sunk by any I/O and control pin	25	mA
	Output current sourced by any I/O and control pin	- 25	mA
$I_{INJ(PIN)}$ (2)	Injected current on five-volt tolerant I/O(3)	+0 /-5	mA
	Injected current on any other pin (4)	± 5	mA
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins)(5)	± 25	mA

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. Negative injection disturbs the analog performance of the device. See note in *Section 6.3.17*.
3. Positive current injection is not possible on these I/Os. A negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 11* for maximum allowed input voltage values.
4. A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 11: Voltage characteristics* for the maximum allowed input voltage values.
5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 13. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	150	°C

6.3 Operating conditions

6.3.1 General operating conditions

Table 14. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{HCLK}	Internal AHB clock frequency		0	32	
f_{PCLK1}	Internal APB1 clock frequency		0	32	MHz
f_{PCLK2}	Internal APB2 clock frequency		0	32	
V_{DD}	Standard operating voltage	BOR detector disabled	1.65	3.6	V
		BOR detector enabled, at power on	1.8	3.6	
		BOR detector disabled, after power on	1.65	3.6	
V_{DDA}(1)	Analog operating voltage (ADC and DAC not used)	Must be the same voltage as V_{DD}(2)	1.65	3.6	V
	Analog operating voltage (ADC or DAC used)		1.8	3.6	
P_D	Power dissipation at T_A = 85 °C(3)	UFBGA100		464	mW
T_A	Temperature range	Maximum power dissipation	–40	85	°C
		Low power dissipation(4)	–40	105	
T_J	Junction temperature range	-40 °C ≤ T_A ≤ 105 °C	–40	105	°C

1. When the ADC is used, refer to *Table 55: ADC characteristics*.
2. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and operation.
3. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_J max (see *Table 66: Thermal characteristics on page 109*).
4. In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_J max (see *Table 66: Thermal characteristics on page 109*).

6.3.2 Embedded reset and power control block characteristics

The parameters given in the following table are derived from the tests performed under the ambient temperature condition summarized in *Table 14*.

Table 15. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{VDD} (1)	V_{DD} rise time rate	BOR detector enabled	0		∞	µs/V
		BOR detector disabled	0		1000	
	V_{DD} fall time rate	BOR detector enabled	20		∞	
		BOR detector disabled	0		1000	
$T_{RSTTEMPO}$ (1)	Reset temporization	V_{DD} rising, BOR enabled		2	3.3	ms
		V_{DD} rising, BOR disabled(2)	0.4	0.7	1.6	
$V_{POR/PDR}$	Power on/power down reset threshold	Falling edge	1	1.5	1.65	V
		Rising edge	1.3	1.5	1.65	
V_{BOR0}	Brown-out reset threshold 0	Falling edge	1.67	1.7	1.74	
		Rising edge	1.69	1.76	1.8	
V_{BOR1}	Brown-out reset threshold 1	Falling edge	1.87	1.93	1.97	
		Rising edge	1.96	2.03	2.07	
V_{BOR2}	Brown-out reset threshold 2	Falling edge	2.22	2.30	2.35	
		Rising edge	2.31	2.41	2.44	
V_{BOR3}	Brown-out reset threshold 3	Falling edge	2.45	2.55	2.6	
		Rising edge	2.54	2.66	2.7	
V_{BOR4}	Brown-out reset threshold 4	Falling edge	2.68	2.8	2.85	
		Rising edge	2.78	2.9	2.95	
V_{PVD0}	Programmable voltage detector threshold 0	Falling edge	1.8	1.85	1.88	
		Rising edge	1.88	1.94	1.99	
V_{PVD1}	PVD threshold 1	Falling edge	1.98	2.04	2.09	
		Rising edge	2.08	2.14	2.18	
V_{PVD2}	PVD threshold 2	Falling edge	2.20	2.24	2.28	
		Rising edge	2.28	2.34	2.38	
V_{PVD3}	PVD threshold 3	Falling edge	2.39	2.44	2.48	
		Rising edge	2.47	2.54	2.58	
V_{PVD4}	PVD threshold 4	Falling edge	2.57	2.64	2.69	
		Rising edge	2.68	2.74	2.79	
V_{PVD5}	PVD threshold 5	Falling edge	2.77	2.83	2.88	
		Rising edge	2.87	2.94	2.99	
V_{PVD6}	PVD threshold 6	Falling edge	2.97	3.05	3.09	
		Rising edge	3.08	3.15	3.20	

Table 15. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{hyst}	Hysteresis voltage	BOR0 threshold	-	40	-	mV
		All BOR and PVD thresholds excepting BOR0	-	100	-	

1. Guaranteed by characterisation, not tested in production.
2. Valid for device version without BOR at power up. Please see option "D" in Ordering information scheme for more details.

6.3.3 Embedded internal reference voltage

The parameters given in *Table 16* are based on characterization results, unless otherwise specified.

Table 16. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{REFINT\ out}$ (1)	Internal reference voltage	– 40 °C < T_J < +105 °C	1.202	1.224	1.242	V
I_{REFINT}	Internal reference current consumption		-	1.4	2.3	µA
$T_{VREFINT}$	Internal reference startup time		-	2	3	ms
V_{VREF_MEAS}	V_{DDA} and V_{REF+} voltage during V_{REFINT} factory measure		2.99	3	3.01	V
A_{VREF_MEAS}	Accuracy of factory-measured V_{REF} value(2)	Including uncertainties due to ADC and V_{DDA}/V_{REF+} values	-	-	±5	mV
T_{Coeff} (3)	Temperature coefficient	–40 °C < T_J < +105 °C	-	20	50	ppm/°C
		0 °C < T_J < +50 °C	-	-	20	
A_{Coeff} (3)	Long-term stability	1000 hours, T= 25 °C	-	-	1000	ppm
$V_{DDCoeff}$ (3)	Voltage coefficient	3.0 V < V_{DDA} < 3.6 V	-	-	2000	ppm/V
$T_{S\_vrefint}$ (3)(4)	ADC sampling time when reading the internal reference voltage		-	5	10	µs
T_{ADC_BUF} (3)	Startup time of reference voltage buffer for ADC		-	-	10	µs
I_{BUF_ADC} (3)	Consumption of reference voltage buffer for ADC		-	13.5	25	µA
I_{VREF_OUT} (3)	VREF_OUT output current(5)		-	-	1	µA
C_{VREF_OUT} (3)	VREF_OUT output load		-	-	50	pF
I_{LPBUF} (3)	Consumption of reference voltage buffer for VREF_OUT and COMP		-	730	1200	nA
V_{REFINT_DIV1} (3)	1/4 reference voltage		24	25	26	% V_{REFINT}
V_{REFINT_DIV2} (3)	1/2 reference voltage		49	50	51	
V_{REFINT_DIV3} (3)	3/4 reference voltage		74	75	76	

1. Tested in production.
2. The internal V_{REF} value is individually measured in production and stored in dedicated EEPROM bytes.
3. Guaranteed by design, not tested in production.
4. Shortest sampling time can be determined in the application by multiple iterations.
5. To guarantee less than 1% VREF_OUT deviation.

6.3.4 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code. The current consumption is measured as described in *Figure 10: Current consumption measurement scheme*.

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to Dhrystone 2.1 code.

Maximum current consumption

The MCU is placed under the following conditions:

- V_{DD} = 3.6 V
- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time is adjusted depending on f_{HCLK} frequency and voltage range
- Prefetch and 64-bit access are enabled in configurations with 1 wait state

The parameters given in *Table 17*, *Table 14* and *Table 15* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Table 17. Current consumption in Run mode, code with data processing running from Flash

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Run from Flash)	Supply current in Run mode, code executed from Flash	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = $f_{HCLK}/2$ above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	1 MHz	285	400	µA
				2 MHz	490	600	
				4 MHz	845	960	
			Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	4 MHz	0.9	1.1	mA
				8 MHz	1.8	2.1	
				16 MHz	3.5	3.9	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	8 MHz	2.3	2.8	
				16 MHz	4.3	4.9	
				32 MHz	8.2	9.4	
		HSI clock source (16 MHz)	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	16 MHz	3.6	4	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	32 MHz	8.4	9.6	
		MSI clock, 65 kHz	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	65 kHz	47	110	µA
		MSI clock, 524 kHz		524 kHz	135	190	
		MSI clock, 4.2 MHz		4.2 MHz	785	900	

1. Based on characterization, not tested in production, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 18. Current consumption in Run mode, code with data processing running from RAM

<table>
<tr><th>Symbol</th><th>Parameter</th><th colspan="2">Conditions</th><th>f_{HCLK}</th><th>Typ</th><th>Max[1]</th><th>Unit</th></tr>
<tr><td rowspan="14">I_{DD} (Run from RAM)</td><td rowspan="14">Supply current in Run mode, code executed from RAM, Flash switched off</td><td rowspan="9">f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = $f_{HCLK}/2$ above 16 MHz (PLL ON)[2]</td><td rowspan="3">Range 3, V_{CORE}=1.2 V VOS[1:0] = 11</td><td>1 MHz</td><td>160</td><td>240</td><td rowspan="3">µA</td></tr>
<tr><td>2 MHz</td><td>310</td><td>410</td></tr>
<tr><td>4 MHz</td><td>710</td><td>880[3]</td></tr>
<tr><td rowspan="3">Range 2, V_{CORE}=1.5 V VOS[1:0] = 10</td><td>4 MHz</td><td>0.79</td><td>1.4</td><td rowspan="8">mA</td></tr>
<tr><td>8 MHz</td><td>1.55</td><td>2.1</td></tr>
<tr><td>16 MHz</td><td>3.0</td><td>3.5</td></tr>
<tr><td rowspan="3">Range 1, V_{CORE}=1.8 V VOS[1:0] = 01</td><td>8 MHz</td><td>2.2</td><td>2.8</td></tr>
<tr><td>16 MHz</td><td>3.6</td><td>4.1</td></tr>
<tr><td>32 MHz</td><td>7.3</td><td>8.3</td></tr>
<tr><td rowspan="2">HSI clock source (16 MHz)</td><td>Range 2, V_{CORE}=1.5 V VOS[1:0] = 10</td><td>16 MHz</td><td>3.1</td><td>3.5</td></tr>
<tr><td>Range 1, V_{CORE}=1.8 V VOS[1:0] = 01</td><td>32 MHz</td><td>7.4</td><td>8.4</td></tr>
<tr><td>MSI clock, 65 kHz</td><td rowspan="3">Range 3, V_{CORE}=1.2 V VOS[1:0] = 11</td><td>65 kHz</td><td>36</td><td>85</td><td rowspan="3">µA</td></tr>
<tr><td>MSI clock, 524 kHz</td><td>524 kHz</td><td>110</td><td>160</td></tr>
<tr><td>MSI clock, 4.2 MHz</td><td>4.2 MHz</td><td>640</td><td>810</td></tr>
</table>

1. Based on characterization, not tested in production, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).
3. Tested in production.

Table 19. Current consumption in Sleep mode

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Sleep)	Supply current in Sleep mode, code executed from RAM, Flash switched OFF	$f_{HSE} = f_{HCLK}$ up to 16 MHz included, $f_{HSE} = f_{HCLK}/2$ above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	1 MHz	70	130	µA
				2 MHz	130	195	
				4 MHz	245	310	
			Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	4 MHz	250	310	
				8 MHz	365	440	
				16 MHz	735	830	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	8 MHz	430	550	
				16 MHz	855	990	
				32 MHz	1850	2100	
		HSI clock source (16 MHz)	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	16 MHz	790	890	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	32 MHz	1900	2200	
		MSI clock, 65 kHz	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	65 kHz	30	60	
		MSI clock, 524 kHz		524 kHz	43	99	
		MSI clock, 4.2 MHz		4.2 MHz	160	210	
	Supply current in Sleep mode, code executed from Flash	$f_{HSE} = f_{HCLK}$ up to 16 MHz included, $f_{HSE} = f_{HCLK}/2$ above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	1 MHz	70.5	130	µA
				2 MHz	130	190	
				4 MHz	255	320	
			Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	4 MHz	260	320	
				8 MHz	380	460	
				16 MHz	750	840	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	8 MHz	440	540	
				16 MHz	870	1000	
				32 MHz	1900	2100	
		HSI clock source (16 MHz)	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	16 MHz	820	910	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	32 MHz	1900	2200	

Table 19. Current consumption in Sleep mode (continued)

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Sleep)	Supply current in Sleep mode, code executed from Flash	MSI clock, 65 kHz	Range 3, V_{CORE}=1.2V VOS[1:0] = 11	65 kHz	38	90	µA
		MSI clock, 524 kHz		524 kHz	52	96	
		MSI clock, 4.2 MHz		4.2 MHz	170	220	

1. Based on characterization, not tested in production, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register)

Table 20. Current consumption in Low power run mode

Symbol	Parameter	Conditions			Typ	Max (1)	Unit
I_{DD} (LP Run)	Supply current in Low power run mode	All peripherals OFF, code executed from RAM, Flash switched OFF, V_{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f_{HCLK} = 32 kHz	T_A = -40 °C to 25 °C	8.6	12	µA
				T_A = 85 °C	19	25	
				T_A = 105 °C	35	47	
			MSI clock, 65 kHz f_{HCLK} = 65 kHz	T_A =-40 °C to 25 °C	14	16	
				T_A = 85 °C	24	29	
				T_A = 105 °C	40	51	
			MSI clock, 131 kHz f_{HCLK} = 131 kHz	T_A = -40 °C to 25 °C	26	29	
				T_A = 55 °C	28	31	
				T_A = 85 °C	36	42	
				T_A = 105 °C	52	64	
		All peripherals OFF, code executed from Flash, V_{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f_{HCLK} = 32 kHz	T_A = -40 °C to 25 °C	20	24	
				T_A = 85 °C	32	37	
				T_A = 105 °C	49	61	
			MSI clock, 65 kHz f_{HCLK} = 65 kHz	T_A = -40 °C to 25 °C	26	30	
				T_A = 85 °C	38	44	
				T_A = 105 °C	55	67	
			MSI clock, 131 kHz f_{HCLK} = 131 kHz	T_A = -40 °C to 25 °C	41	46	
				T_A = 55 °C	44	50	
				T_A = 85 °C	56	87	
				T_A = 105 °C	73	110	
I_{DD} max (LP Run)	Max allowed current in Low power run mode	V_{DD} from 1.65 V to 3.6 V			-	200	

1. Based on characterization, not tested in production, unless otherwise specified.

Table 21. Current consumption in Low power sleep mode

Symbol	Parameter	Conditions			Typ	Max (1)	Unit
I_{DD} (LP Sleep)	Supply current in Low power sleep mode	All peripherals OFF, V_{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f_{HCLK} = 32 kHz Flash OFF	T_A = -40 °C to 25 °C	4.4	-	μA
			MSI clock, 65 kHz f_{HCLK} = 32 kHz Flash ON	T_A = -40 °C to 25 °C	14	16	
				T_A = 85 °C	19	23	
				T_A = 105 °C	27	33	
			MSI clock, 65 kHz f_{HCLK} = 65 kHz, Flash ON	T_A = -40 °C to 25 °C	15	17	
				T_A = 85 °C	20	23	
				T_A = 105 °C	28	33	
			MSI clock, 131 kHz f_{HCLK} = 131 kHz, Flash ON	T_A = -40 °C to 25 °C	17	19	
				T_A = 55 °C	18	21	
				T_A = 85 °C	22	25	
				T_A = 105 °C	30	35	
		TIM9 and USART1 enabled, Flash ON, V_{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f_{HCLK} = 32 kHz	T_A = -40 °C to 25 °C	14	16	
				T_A = 85 °C	19	22	
				T_A = 105 °C	27	32	
			MSI clock, 65 kHz f_{HCLK} = 65 kHz	T_A = -40 °C to 25 °C	15	17	
				T_A = 85 °C	20	23	
				T_A = 105 °C	28	33	
			MSI clock, 131 kHz f_{HCLK} = 131 kHz	T_A = -40 °C to 25 °C	17	19	
				T_A = 55 °C	18	21	
				T_A = 85 °C	22	25	
				T_A = 105 °C	30	36	
I_{DD} max (LP Sleep)	Max allowed current in Low power Sleep mode	V_{DD} from 1.65 V to 3.6 V			-	200	

1. Based on characterization, not tested in production, unless otherwise specified.

Table 22. Typical and maximum current consumptions in Stop mode

Symbol	Parameter	Conditions			Typ	Max (1)	Unit
I_{DD} (Stop with RTC)	Supply current in Stop mode with RTC enabled	RTC clocked by LSI or LSE external clock (32.768kHz), regulator in LP mode,HSI and HSE OFF (no independent watchdog)	LCD OFF	T_A = -40°C to 25°C V_{DD} = 1.8 V	1.5		µA
				T_A = -40°C to 25°C	1.7	4	
				T_A = 55°C	2.4	6	
				T_A= 85°C	5.4	10	
				T_A = 105°C	11.0	23	
			LCD ON (static duty)(2)	T_A = -40°C to 25°C	3.8	6	
				T_A = 55°C	4.4	7	
				T_A= 85°C	7.4	12	
				T_A = 105°C	14.4	27	
			LCD ON (1/8 duty)(3)	T_A = -40°C to 25°C	7.8	10	
				T_A = 55°C	8.3	11	
				T_A= 85°C	11.4	16	
				T_A = 105°C	20.5	44	
		RTC clocked by LSE external quartz (32.768kHz), regulator in LP mode, HSI and HSE OFF (no independent watchdog(4)	LCD OFF	T_A = -40°C to 25°C	2.1	-	
				T_A = 55°C	2.8	-	
				T_A= 85°C	3.8	-	
				T_A = 105°C	11.1	-	
			LCD ON (static duty)(2)	T_A = -40°C to 25°C	4.2	-	
				T_A = 55°C	4.8	-	
				T_A= 85°C	7.9	-	
				T_A = 105°C	15.0	-	
			LCD ON (1/8 duty)(3)	T_A = -40°C to 25°C	8.2	-	
				T_A = 55°C	8.7	-	
				T_A= 85°C	11.9	-	
				T_A = 105°C	21.4	-	
			LCD OFF	T_A = -40°C to 25°C V_{DD} = 1.8V	1.6	-	
				T_A = -40°C to 25°C V_{DD} = 3.0V	1.9	-	
				T_A = -40°C to 25°C V_{DD} = 3.6V	2.1	-	

Table 22. Typical and maximum current consumptions in Stop mode (continued)

Symbol	Parameter	Conditions		Typ	Max (1)	Unit
I_{DD} (Stop)	Supply current in Stop mode (RTC disabled)	Regulator in LP mode, HSI and HSE OFF, independent watchdog and LSI enabled	T_A = -40°C to 25°C	1.6	2.2	µA
		Regulator in LP mode, LSI, HSI and HSE OFF (no independent watchdog)	T_A = -40°C to 25°C	0.65	1	
			T_A = 55°C	1.3	3	
			T_A= 85°C	4.4	9	
			T_A = 105°C	10.0	22(5)	
I_{DD} (WU from Stop)	Supply current during wakeup from Stop mode	MSI = 4.2 MHz	T_A = -40°C to 25°C	2	-	mA
		MSI = 1.05 MHz		1.45	-	
		MSI = 65 kHz(6)		1.45	-	

1. Based on characterization, not tested in production, unless otherwise specified.
2. LCD enabled with external VLCD, static duty, division ratio = 256, all pixels active, no LCD connected.
3. LCD enabled with external VLCD, 1/8 duty, 1/3 bias, division ratio = 64, all pixels active, no LCD connected.
4. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.
5. Tested in production.
6. When MSI = 64 kHz, the RMS current is measured over the first 15 µs following the wakeup event. For the remaining part of the wakeup period, the current corresponds the Run mode current.

Table 23. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions		Typ	Max (1)	Unit
I_{DD} (Standby with RTC)	Supply current in Standby mode with RTC enabled	RTC clocked by LSI (no independent watchdog)	T_A = -40 °C to 25 °C	1.3	1.9	µA
			T_A = 55 °C	1.44	2.2	
			T_A= 85 °C	1.90	4	
			T_A = 105 °C	3.05	8.3(2)	
		RTC clocked by LSE external quartz(no independent watchdog)(3)	T_A = -40 °C to 25 °C	1.7	-	
			T_A = 55 °C	1.84	-	
			T_A= 85 °C	2.33	-	
			T_A = 105 °C	3.59	-	
I_{DD} (Standby)	Supply current in Standby mode (RTC disabled)	Independent watchdog and LSI enabled	T_A = -40 °C to 25 °C	1	1.7	
		Independent watchdog and LSI OFF	T_A = -40 °C to 25 °C	0.35	0.6	
			T_A = 55 °C	0.47	0.9	
			T_A = 85 °C	1.2	2.75	
			T_A = 105 °C	2.9	7(2)	
I_{DD} (WU from Standby)	Supply current during wakeup time from Standby mode		T_A = -40 °C to 25 °C	1	-	mA

1. Based on characterization, not tested in production, unless otherwise specified
2. Tested in production.
3. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8pF loading capacitors.

Wakeup time from low-power mode

The wakeup times given in the following table are measured with the MSI RC oscillator. The clock source used to wake up the device depends on the current operating mode:

- Sleep mode: the clock source is the clock that was set before entering Sleep mode
- Stop mode: the clock source is the MSI oscillator in the range configured before entering Stop mode
- Standby mode: the clock source is the MSI oscillator running at 2.1 MHz

All timings are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in Table 14.

Table 24. Typical and maximum timings in Low power modes

Symbol	Parameter	Conditions	Typ	Max[1]	Unit
$t_{WUSLEEP}$	Wakeup from Sleep mode	f_{HCLK} = 32 MHz	0.4	-	µs
$t_{WUSLEEP\_LP}$	Wakeup from Low power sleep mode f_{HCLK} = 262 kHz	f_{HCLK} = 262 kHz Flash enabled	46	-	
		f_{HCLK} = 262 kHz Flash switched OFF	46	-	
t_{WUSTOP}	Wakeup from Stop mode, regulator in Run mode	f_{HCLK} = f_{MSI} = 4.2 MHz	8.2	-	
	Wakeup from Stop mode, regulator in low power mode	f_{HCLK} = f_{MSI} = 4.2 MHz Voltage range 1 and 2	7.7	8.9	
		f_{HCLK} = f_{MSI} = 4.2 MHz Voltage range 3	8.2	13.1	
		f_{HCLK} = f_{MSI} = 2.1 MHz	10.2	13.4	
		f_{HCLK} = f_{MSI} = 1.05 MHz	16	20	
		f_{HCLK} = f_{MSI} = 524 kHz	31	37	
		f_{HCLK} = f_{MSI} = 262 kHz	57	66	
		f_{HCLK} = f_{MSI} = 131 kHz	112	123	
		f_{HCLK} = MSI = 65 kHz	221	236	
$t_{WUSTDBY}$	Wakeup from Standby mode FWU bit = 1	f_{HCLK} = MSI = 2.1 MHz	58	104	
	Wakeup from Standby mode FWU bit = 0	f_{HCLK} = MSI = 2.1 MHz	2.6	3.25	ms

1. Based on characterization, not tested in production, unless otherwise specified

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following table. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
  - with all peripherals clocked off
  - with only one peripheral clocked on

Table 25. Peripheral current consumption(1)

Peripheral		Typical consumption, V_{DD} = 3.0 V, T_A = 25 °C				Unit
		Range 1, V_{CORE}= 1.8 V VOS[1:0] = 01	Range 2, V_{CORE}= 1.5 V VOS[1:0] = 10	Range 3, V_{CORE}= 1.2 V VOS[1:0] = 11	Low power sleep and run	
APB1	TIM2	13	11	9	11	µA/MHz (f_{HCLK})
	TIM3	12	10	9	11	
	TIM4	12	10	9	11	
	TIM5	16	13	11	14	
	TIM6	4	4	4	4	
	TIM7	4	4	4	4	
	LCD	4	3	3	4	
	WWDG	3	2.5	2.5	3	
	SPI2	8	7	9	7.5	
	SPI3	7	6	7	6	
	USART2	8	7	7	7	
	USART3	8	7	7	7	
	I2C1	8	7	6	7	
	I2C2	7	6	5	6	
	USB	15	7	7	7	
	PWR	3	3	3	3	
	DAC	6	5	4.5	5	
	COMP	4	3.5	3.5	4	

Table 25. Peripheral current consumption[1] (continued)

Peripheral		Typical consumption, V_{DD} = 3.0 V, T_A = 25 °C: Range 1, V_{CORE}= 1.8 V VOS[1:0] = 01	Range 2, V_{CORE}= 1.5 V VOS[1:0] = 10	Range 3, V_{CORE}= 1.2 V VOS[1:0] = 11	Low power sleep and run	Unit
APB2	SYSCFG & RI	3	2	2	3	µA/MHz (f_{HCLK})
	TIM9	8	7	6	7	
	TIM10	6	5	5	5	
	TIM11	6	5	5	5	
	ADC[2]	10	8	7	8	
	SPI1	4	4	4	4	
	USART1	8	7	6	7	
AHB	GPIOA	7	6	5	6	
	GPIOB	7	6	5	6	
	GPIOC	7	6	5	6	
	GPIOD	7	6	5	6	
	GPIOE	7	6	5	6	
	GPIOF	7	6	5	6	
	GPIOG	7	6	5	6	
	GPIOH	2	2	1	2	
	CRC	0.5	0.5	0.5	1	
	AES	5	4	3	4	
	FLASH	26	26	29	-[3]	
	DMA1	18	15	13	18	
	DMA2	16	14	12	16	
All enabled		279	221	219	215	
$I_{DD (RTC)}$		0.4				µA
$I_{DD (LCD)}$		3.1				
$I_{DD (ADC)}$[4]		1450				
$I_{DD (DAC)}$[5]		340				
$I_{DD (COMP1)}$		0.16				
$I_{DD (COMP2)}$	Slow mode	2				
	Fast mode	5				
$I_{DD (PVD / BOR)}$[6]		2.6				
$I_{DD (IWDG)}$		0.25				

1. Data based on differential I_{DD} measurement between all peripherals OFF an one peripheral with clock enabled, in the following conditions: f_{HCLK} = 32 MHz (range 1), f_{HCLK} = 16 MHz (range 2), f_{HCLK} = 4 MHz (range 3), f_{HCLK} = 64kHz (Low power run/sleep), f_{APB1} = f_{HCLK}, f_{APB2} = f_{HCLK}, default prescaler value for each peripheral. The CPU is in Sleep mode in both cases. No I/O pins toggling. Not tested in production.
2. HSI oscillator is OFF for this measure.
3. In low power sleep and run mode, the Flash memory must always be in power-down mode.
4. Data based on a differential I_{DD} measurement between ADC in reset configuration and continuous ADC conversion (HSI consumption not included).
5. Data based on a differential I_{DD} measurement between DAC in reset configuration and continuous DAC conversion of V_{DD}/2. DAC is in buffered mode, output is left floating.
6. Including supply current of internal reference voltage.

6.3.5 External clock source characteristics

High-speed external user clock generated from an external source

Table 26. High-speed external user clock characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency		1	8	32	MHz
V_{HSEH}	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSE)}$ $t_{w(HSE)}$	OSC_IN high or low time		12	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time		-	-	20	
$C_{in(HSE)}$	OSC_IN input capacitance		-	2.6	-	pF
$DuCy_{(HSE)}$	Duty cycle		45	-	55	%
I_L	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	µA

1. Guaranteed by design, not tested in production.

Low-speed external user clock generated from an external source

The characteristics given in the following table result from tests performed using a low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in Table 14.

Table 27. Low-speed external user clock characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User external clock source frequency		1	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{LSEL}	OSC32_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	V
$t_{w(LSE)}$ $t_{w(LSE)}$	OSC32_IN high or low time		465	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time		-	-	10	ns
$C_{IN(LSE)}$	OSC32_IN input capacitance		-	0.6	-	pF
$DuCy_{(LSE)}$	Duty cycle		45	-	55	%
I_L	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	µA

1. Guaranteed by design, not tested in production

Figure 11. Low-speed external clock source AC timing diagram

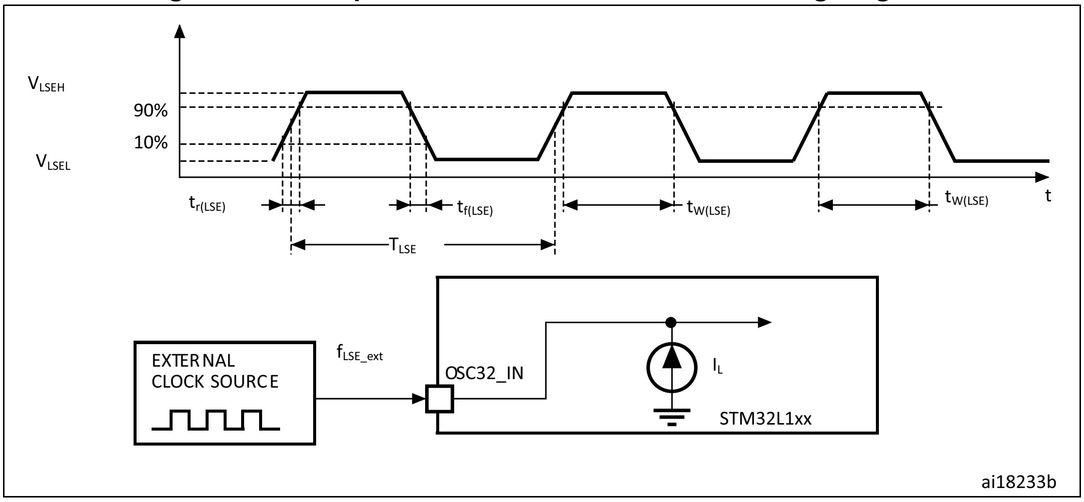
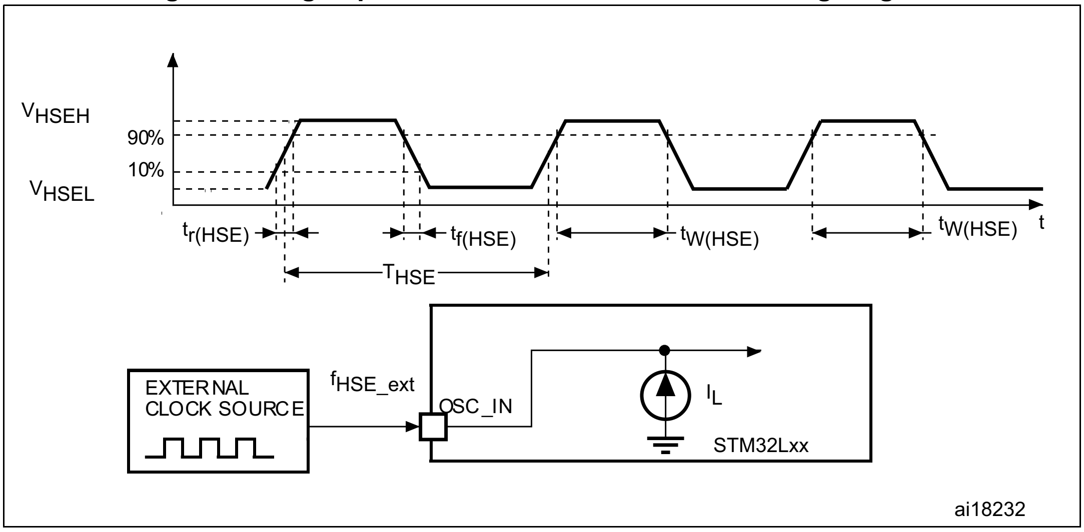


Figure 12. High-speed external clock source AC timing diagram



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 1 to 24 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 28*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

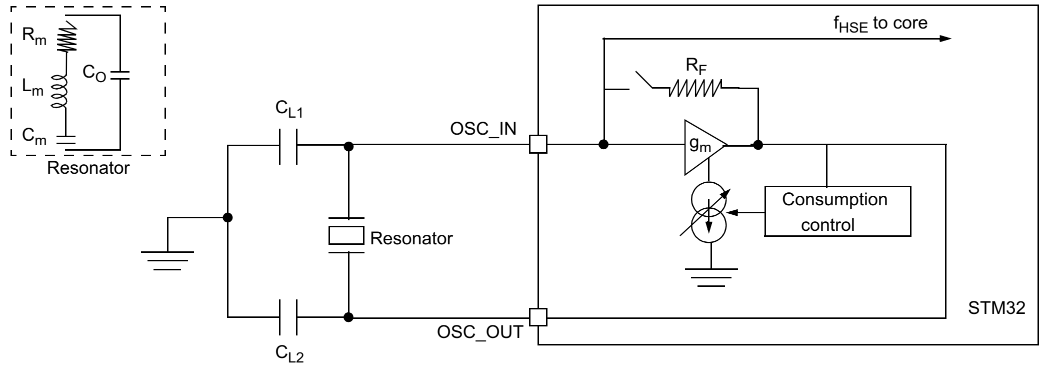
Table 28. HSE 1-24 MHz oscillator characteristics(1)(2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency		1		24	MHz
R_F	Feedback resistor		-	200	-	kΩ
C	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S)(3)	R_S = 30 Ω	-	20	-	pF
I_{HSE}	HSE driving current	V_{DD}= 3.3 V, V_{IN} = V_{SS} with 30 pF load	-	-	3	mA
$I_{DD(HSE)}$	HSE oscillator power consumption	C = 20 pF f_{OSC} = 16 MHz	-	-	2.5 (startup) 0.7 (stabilized)	mA
		C = 10 pF f_{OSC} = 16 MHz	-	-	2.5 (startup) 0.46 (stabilized)	
g_m	Oscillator transconductance	Startup	3.5	-	-	mA /V
$t_{SU(HSE)}$(4)	Startup time	V_{DD} is stabilized	-	1	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Based on characterization results, not tested in production.
3. The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 13*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}. Refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website www.st.com.

Figure 13. HSE oscillator circuit diagram



1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 29*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 29. LSE oscillator characteristics (f_{LSE} = 32.768 kHz)(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE}	Low speed external oscillator frequency		-	32.768	-	kHz
R_F	Feedback resistor		-	1.2	-	MΩ
C(2)	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S)(3)	R_S = 30 kΩ	-	8	-	pF
I_{LSE}	LSE driving current	V_{DD} = 3.3 V, V_{IN} = V_{SS}	-	-	1.1	µA
$I_{DD\ (LSE)}$	LSE oscillator current consumption	V_{DD} = 1.8 V	-	450	-	nA
		V_{DD} = 3.0 V	-	600	-	
		V_{DD} = 3.6V	-	750	-	
g_m	Oscillator transconductance		3		-	µA/V
$t_{SU(LSE)}$(4)	Startup time	V_{DD} is stabilized	-	1	-	s

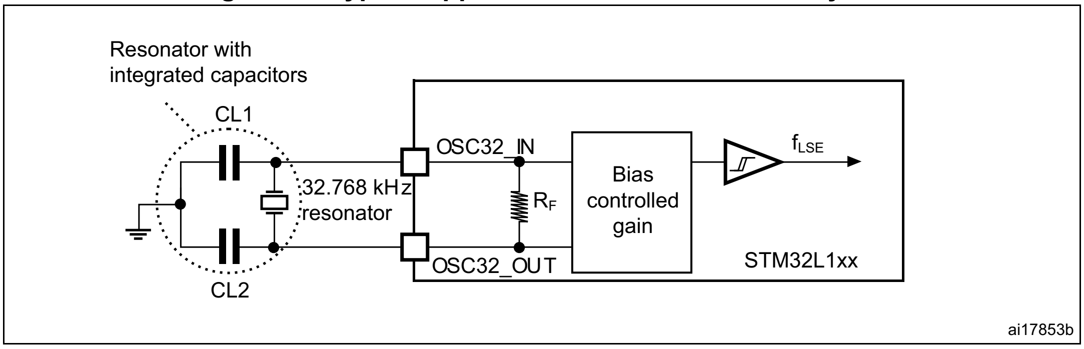
1. Based on characterization, not tested in production.
2. Refer to the note and caution paragraphs below the table, and to the application note AN2867 “Oscillator design guide for ST microcontrollers”.
3. The oscillator selection can be optimized in terms of supply current using an high quality resonator with small R_S value for example MSIV-TIN32.768kHz. Refer to crystal manufacturer for more details.

4. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Note: For C_{L1} and C_{L2}, it is recommended to use high-quality ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator (see Figure 14). C_{L1} and $C_{L2,}$ are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}.
Load capacitance C_L has the following formula: $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{stray}$ where C_{stray} is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.

Caution: To avoid exceeding the maximum value of C_{L1} and C_{L2} (15 pF) it is strongly recommended to use a resonator with a load capacitance $C_L \leq 7$ pF. Never use a resonator with a load capacitance of 12.5 pF.
Example: if you choose a resonator with a load capacitance of C_L = 6 pF and C_{stray} = 2 pF, then $C_{L1} = C_{L2}$ = 8 pF.

Figure 14. Typical application with a 32.768 kHz crystal



6.3.6 Internal clock source characteristics

The parameters given in Table 30 are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in Table 14.

High-speed internal (HSI) RC oscillator

Table 30. HSI oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	V_{DD} = 3.0 V	-	16	-	MHz
TRIM(1)(2)	HSI user-trimmed resolution	Trimming code is not a multiple of 16	-	± 0.4	0.7	%
		Trimming code is a multiple of 16	-	-	± 1.5	%
ACC_{HSI}(2)	Accuracy of the factory-calibrated HSI oscillator	V_{DDA} = 3.0 V, T_A = 25 °C	-1(3)	-	1(3)	%
		V_{DDA} = 3.0 V, T_A = 0 to 55 °C	-1.5	-	1.5	%
		V_{DDA} = 3.0 V, T_A = -10 to 70 °C	-2	-	2	%
		V_{DDA} = 3.0 V, T_A = -10 to 85 °C	-2.5	-	2	%
		V_{DDA} = 3.0 V, T_A = -10 to 105 °C	-4	-	2	%
		V_{DDA} = 1.65 V to 3.6 V T_A = -40 to 105 °C	-4	-	3	%
$t_{SU(HSI)}$(2)	HSI oscillator startup time		-	3.7	6	µs
$I_{DD(HSI)}$(2)	HSI oscillator power consumption		-	100	140	µA

1. The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).
2. Based on characterization, not tested in production.
3. Tested in production.

Low-speed internal (LSI) RC oscillator

Table 31. LSI oscillator characteristics

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI}(1)	LSI frequency	26	38	56	kHz
D_{LSI}(2)	LSI oscillator frequency drift 0°C ≤ T_A ≤ 85°C	-10	-	4	%
$t_{su(LSI)}$(3)	LSI oscillator startup time	-	-	200	µs
$I_{DD(LSI)}$(3)	LSI oscillator power consumption	-	400	510	nA

1. Tested in production.
2. This is a deviation for an individual part, once the initial frequency has been measured.
3. Guaranteed by design, not tested in production.

Multi-speed internal (MSI) RC oscillator

Table 32. MSI oscillator characteristics

Symbol	Parameter	Condition	Typ	Max	Unit
f_{MSI}	Frequency after factory calibration, done at V_{DD}= 3.3 V and T_A = 25 °C	MSI range 0	65.5	-	kHz
		MSI range 1	131	-	
		MSI range 2	262	-	
		MSI range 3	524	-	
		MSI range 4	1.05	-	MHz
		MSI range 5	2.1	-	
		MSI range 6	4.2	-	
ACC_{MSI}	Frequency error after factory calibration		±0.5	-	%
$D_{TEMP(MSI)}$(1)	MSI oscillator frequency drift 0 °C ≤ T_A ≤ 85 °C		±3	-	%
$D_{VOLT(MSI)}$(1)	MSI oscillator frequency drift 1.65 V ≤ V_{DD} ≤ 3.6 V, T_A = 25 °C		-	2.5	%/V
$I_{DD(MSI)}$(2)	MSI oscillator power consumption	MSI range 0	0.75	-	µA
		MSI range 1	1	-	
		MSI range 2	1.5	-	
		MSI range 3	2.5	-	
		MSI range 4	4.5	-	
		MSI range 5	8	-	
		MSI range 6	15	-	

Table 32. MSI oscillator characteristics (continued)

Symbol	Parameter	Condition	Typ	Max	Unit
$t_{SU(MSI)}$	MSI oscillator startup time	MSI range 0	30	-	μs
		MSI range 1	20	-	
		MSI range 2	15	-	
		MSI range 3	10	-	
		MSI range 4	6	-	
		MSI range 5	5	-	
		MSI range 6, Voltage range 1 and 2	3.5	-	
		MSI range 6, Voltage range 3	5	-	
$t_{STAB(MSI)}$(2)	MSI oscillator stabilization time	MSI range 0	-	40	
		MSI range 1	-	20	
		MSI range 2	-	10	
		MSI range 3	-	4	
		MSI range 4	-	2.5	
		MSI range 5	-	2	
		MSI range 6, Voltage range 1 and 2	-	2	
		MSI range 3, Voltage range 3	-	3	
$f_{OVER(MSI)}$	MSI oscillator frequency overshoot	Any range to range 5	-	4	MHz
		Any range to range 6	-	6	

1. This is a deviation for an individual part, once the initial frequency has been measured.
2. Based on characterization, not tested in production.

6.3.7 PLL characteristics

The parameters given in *Table 33* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Table 33. PLL characteristics

Symbol	Parameter	Value			Unit
		Min	Typ	Max(1)	
f_{PLL_IN}	PLL input clock(2)	2	-	24	MHz
	PLL input clock duty cycle	45	-	55	%
f_{PLL_OUT}	PLL output clock	2	-	32	MHz
t_{LOCK}	Worst case PLL lock time PLL input = 2 MHz PLL VCO = 96 MHz	-	100	130	µs
Jitter	Cycle-to-cycle jitter	-		± 600	ps
I_{DDA}(PLL)	Current consumption on V_{DDA}	-	220	450	µA
I_{DD}(PLL)	Current consumption on V_{DD}	-	120	150	

1. Based on characterization, not tested in production.
2. Take care of using the appropriate multiplier factors so as to have PLL input clock values compatible with the range defined by f_{PLL_OUT}.

6.3.8 Memory characteristics

The characteristics are given at T_A = -40 to 105 °C unless otherwise specified.

RAM memory

Table 34. RAM and hardware registers

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
VRM	Data retention mode(1)	STOP mode (or RESET)	1.65	-	-	V

1. Minimum supply voltage without losing data stored in RAM (in Stop mode or under Reset) or in hardware registers (only in Stop mode).

Flash memory and data EEPROM

Table 35. Flash memory and data EEPROM characteristics

Symbol	Parameter	Conditions	Min	Typ	Max(1)	Unit
V_{DD}	Operating voltage Read / Write / Erase		1.65	-	3.6	V
t_{prog}	Programming time for word or half-page	Erasing	-	3.28	3.94	ms
		Programming	-	3.28	3.94	
I_{DD}	Average current during the whole programming / erase operation	$T_A = 25$ °C, $V_{DD} = 3.6$ V	-	600	900	µA
	Maximum current (peak) during the whole programming / erase operation		-	1.5	2.5	mA

1. Guaranteed by design, not tested in production.

Table 36. Flash memory and data EEPROM endurance and retention

Symbol	Parameter	Conditions	Value			Unit
			Min(1)	Typ	Max	
N_{CYC}(2)	Cycling (erase / write) Program memory	T_A = -40°C to 105 °C	10	-	-	kcycles
	Cycling (erase / write) EEPROM data memory		300	-	-	
t_{RET}(2)	Data retention (program memory) after 10 kcycles at T_A = 85 °C	T_{RET} = +85 °C	30	-	-	years
	Data retention (EEPROM data memory) after 300 kcycles at T_A = 85 °C		30	-	-	
	Data retention (program memory) after 10 kcycles at T_A = 105 °C	T_{RET} = +105 °C	10	-	-	
	Data retention (EEPROM data memory) after 300 kcycles at T_A = 105 °C		10	-	-	

1. Based on characterization not tested in production.
2. Characterization is done according to JEDEC JESD22-A117.

6.3.9 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 37*. They are based on the EMS levels and classes defined in application note AN1709.

Table 37. EMS characteristics

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, LQFP100, T_A = +25 °C, f_{HCLK} = 32 MHz conforms to IEC 61000-4-2	2B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, LQFP100, T_A = +25 °C, f_{HCLK} = 32 MHz conforms to IEC 61000-4-4	4A

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 38. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. frequency range			Unit
				4 MHz voltage range 3	16 MHz voltage range 2	32 MHz voltage range 1	
S_{EMI}	Peak level	V_{DD} = 3.3 V, T_A = 25 °C, LQFP100 package compliant with IEC 61967-2	0.1 to 30 MHz	3	-6	-5	dBµV
			30 to 130 MHz	18	4	-7	
			130 MHz to 1GHz	15	5	-7	
			SAE EMI Level	2.5	2	1	-

6.3.10 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 39. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C, conforming to JESD22-A114	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C, conforming to JESD22-C101	II	500	

1. Based on characterization results, not tested in production.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 40. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = +105 °C conforming to JESD78A	II level A

6.3.11 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error, out of spec current injection on adjacent pins or other functional failure (for example reset, oscillator frequency deviation, LCD levels, etc.).

The test results are given in the following table.

Table 41. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on true open-drain pins	-5	+0	mA
	Injected current on all 5 V tolerant (FT) pins	-5	+0	
	Injected current on any other pin	-5	+5	

6.3.12 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 42* are derived from tests performed under the conditions summarized in *Table 14*. All I/Os are CMOS and TTL compliant.

Table 42. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage	TTL ports 2.7 V ≤ V_{DD} ≤ 3.6 V	V_{SS} - 0.3	-	0.8	V
V_{IH}	Standard I/O input high level voltage		2(1)	-	V_{DD}+0.3	
	FT(2) I/O input high level voltage			-	5.5V	
V_{IL}	Input low level voltage	CMOS ports 1.65 V ≤ V_{DD} ≤ 3.6 V	–0.3	-	0.3V_{DD}(3)	
V_{IH}	Standard I/O Input high level voltage	CMOS ports 1.65 V ≤ V_{DD} ≤ 3.6 V	0.7 V_{DD}(3)(4)	-	V_{DD}+0.3	
	FT(5) I/O input high level voltage	CMOS ports 1.65 V ≤ V_{DD} ≤ 2.0 V		-	5.25	
		CMOS ports 2.0 V ≤ V_{DD} ≤ 3.6 V		-	5.5	
V_{hys}	Standard I/O Schmitt trigger voltage hysteresis(6)		10% V_{DD}(7)	-	-	
I_{lkg}	Input leakage current (8)(3)	V_{SS} ≤ V_{IN} ≤ V_{DD} I/Os with LCD	-	-	±50	nA
		V_{SS} ≤ V_{IN} ≤ V_{DD} I/Os with analog switches	-	-	±50	
		V_{SS} ≤ V_{IN} ≤ V_{DD} I/Os with analog switches and LCD	-	-	±50	
		V_{SS} ≤ V_{IN} ≤ V_{DD} I/Os with USB	-	-	TBD	
		V_{SS} ≤ V_{IN} ≤ V_{DD} Standard I/Os	-	-	±50	
R_{PU}	Weak pull-up equivalent resistor(9)(3)	V_{IN} = V_{SS}	30	45	60	kΩ
R_{PD}	Weak pull-down equivalent resistor(9)(3)	V_{IN} = V_{DD}	30	45	60	kΩ
C_{IO}	I/O pin capacitance		-	5	-	pF

1. Guaranteed by design.
2. FT = 5V tolerant. To sustain a voltage higher than VDD +0.5 the internal pull-up/pull-down resistors must be disabled.
3. Tested in production
4. 0.7V_{DD} for 5 V-tolerant receiver
5. FT = Five-volt tolerant.
6. Hysteresis voltage between Schmitt trigger switching levels. Based on characterization, not tested in production.
7. With a minimum of 200 mV. Based on characterization, not tested in production.

8. The max. value may be exceeded if negative current is injected on adjacent pins.
9. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This MOS/NMOS contribution to the series resistance is minimum (~10% order).

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ±8 mA, and sink or source up to ±20 mA with the non-standard V_{OL}/V_{OH} specifications given in Table 43.

in the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in Section 6.2:

- The sum of the currents sourced by all the I/Os on $V_{DD,}$ plus the maximum Run consumption of the MCU sourced on $V_{DD,}$ cannot exceed the absolute maximum rating I_{VDD} (see Table 12).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating I_{VSS} (see Table 12).

Output voltage levels

Unless otherwise specified, the parameters given in Table 43 are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in Table 14. All I/Os are CMOS and TTL compliant.

Table 43. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL} (1)(2)	Output low level voltage for an I/O pin when 8 pins are sunk at same time	I_{IO} = +8 mA 2.7 V < V_{DD} < 3.6 V	-	0.4	V
V_{OH} (3)(2)	Output high level voltage for an I/O pin when 8 pins are sourced at same time		2.4	-	
V_{OL} (1)(4)	Output low level voltage for an I/O pin when 8 pins are sunk at same time	I_{IO} =+ 4 mA 1.65 V < V_{DD} < 2.7 V	-	0.45	
V_{OH} (3)(4)	Output high level voltage for an I/O pin when 8 pins are sourced at same time		V_{DD}-0.45	-	
V_{OL} (1)(4)	Output low level voltage for an I/O pin when 4 pins are sunk at same time	I_{IO} = +20 mA 2.7 V < V_{DD} < 3.6 V	-	1.3	
V_{OH} (3)(4)	Output high level voltage for an I/O pin when 4 pins are sourced at same time		V_{DD}-1.3	-	

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in Table 12 and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.
2. Tested in production.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in Table 12 and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD}.
4. Based on characterization data, not tested in production.

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 15* and *Table 44*, respectively.

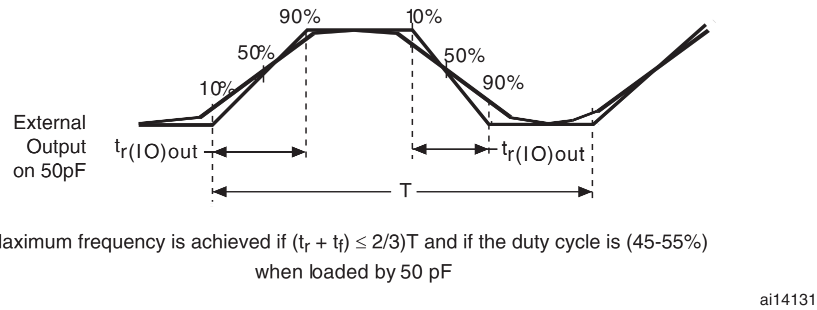
Unless otherwise specified, the parameters given in *Table 44* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Table 44. I/O AC characteristics(1)

OSPEEDRx [1:0] bit value(1)	Symbol	Parameter	Conditions	Min	Max(2)	Unit
00	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	400	kHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	400	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	625	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	625	
01	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	2	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	1	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	125	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	250	
10	$F_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	10	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	2	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	25	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	125	
11	$F_{max(IO)out}$	Maximum frequency(3)	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	50	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	8	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	5	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	30	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller		8	-	

1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the STM32L151xx, STM32L152xx and STM32L162xx reference manual for a description of GPIO Port configuration register.
2. Guaranteed by design. Not tested in production.
3. The maximum frequency is defined in *Figure 15*.

Figure 15. I/O AC characteristics definition



6.3.13 NRST pin characteristics

The NRST pin input driver uses CMOS technology.

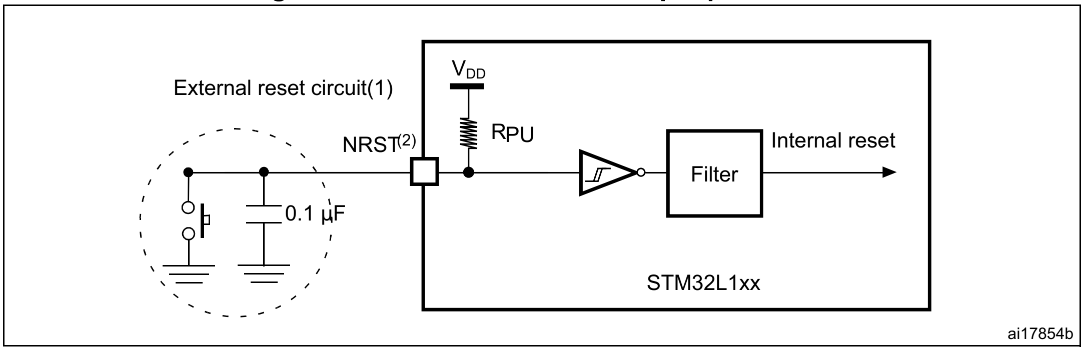
Unless otherwise specified, the parameters given in *Table 45* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Table 45. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}$(1)	NRST input low level voltage		V_{SS}	-	0.8	V
$V_{IH(NRST)}$(1)	NRST input high level voltage		1.4	-	V_{DD}	
$V_{OL(NRST)}$(1)	NRST output low level voltage	I_{OL} = 2 mA 2.7 V < V_{DD} < 3.6 V	-	-	0.4	
		I_{OL} = 1.5 mA 1.65 V < V_{DD} < 2.7 V	-	-		
$V_{hys(NRST)}$(1)	NRST Schmitt trigger voltage hysteresis		10%V_{DD}(2)	-	-	mV
R_{PU}	Weak pull-up equivalent resistor(3)	$V_{IN} = V_{SS}$	30	45	60	kΩ
$V_{F(NRST)}$(1)	NRST input filtered pulse		-	-	50	ns
$V_{NF(NRST)}$(1)	NRST input not filtered pulse		350	-	-	ns

1. Guaranteed by design, not tested in production.
2. 200 mV minimum value
3. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is around 10%.

Figure 16. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 45*. Otherwise the reset will not be taken into account by the device.

6.3.14 TIM timer characteristics

The parameters given in the following table are guaranteed by design.

Refer to *Section 6.3.11: I/O current injection characteristics* for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 46. TIMx(1) characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time		1	-	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 32 MHz	31.25	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4		0	$f_{TIMxCLK}/2$	MHz
		$f_{TIMxCLK}$ = 32 MHz	0	16	MHz
Res_{TIM}	Timer resolution			16	bit
$t_{COUNTER}$	16-bit counter clock period when internal clock is selected (timer's prescaler disabled)		1	65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 32 MHz	0.0312	2048	µs
t_{MAX_COUNT}	Maximum possible count		-	65536 × 65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 32 MHz	-	134.2	s

1. TIMx is used as a general term to refer to the TIM2, TIM3 and TIM4 timers.

6.3.15 Communications interfaces

I^2C interface characteristics

The STM32L162xC product line I^2C interface meets the requirements of the standard I^2C communication protocol with the following restrictions: SDA and SCL are not “true” open-drain I/O pins. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.

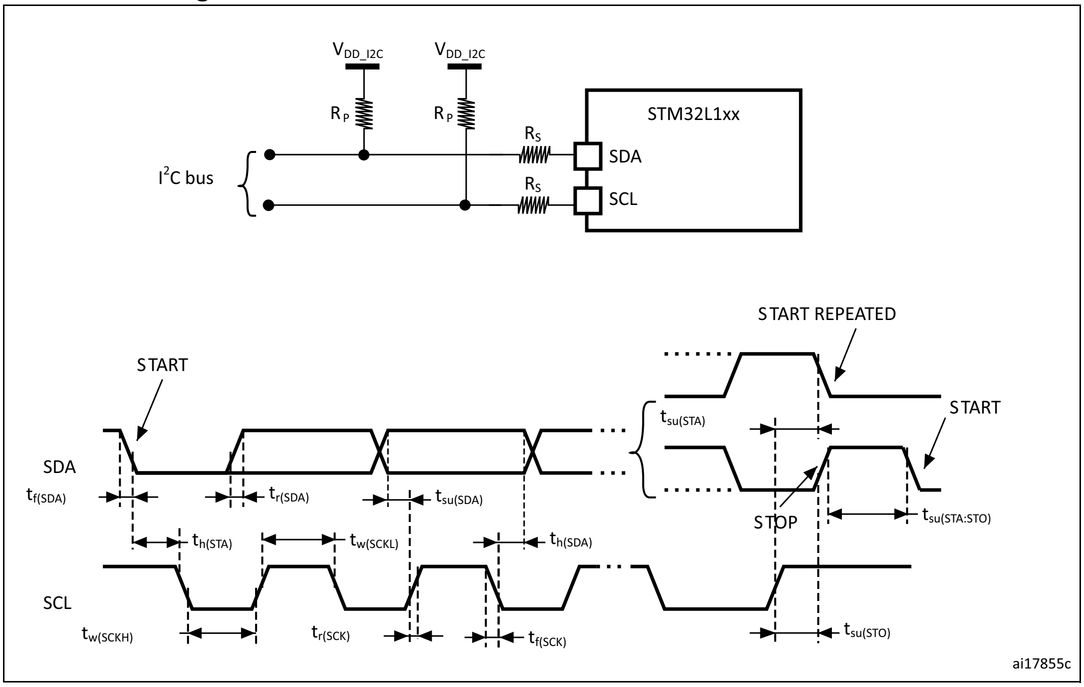
The I^2C characteristics are described in *Table 47*. Refer also to *Section 6.3.11: I/O current injection characteristics* for more details on the input/output alternate function characteristics (SDA and SCL).

Table 47. I^2C characteristics

Symbol	Parameter	Standard mode I^2C(1)		Fast mode I^2C(1)(2)		Unit
		Min	Max	Min	Max	
$t_{w(SCLL)}$	SCL clock low time	4.7	-	1.3	-	µs
$t_{w(SCLH)}$	SCL clock high time	4.0	-	0.6	-	µs
$t_{su(SDA)}$	SDA setup time	250	-	100	-	ns
$t_{h(SDA)}$	SDA data hold time	0	-	0	900(3)	ns
$t_{r(SDA)}$ $t_{r(SCL)}$	SDA and SCL rise time	-	1000	$20 + 0.1C_b$	300	ns
$t_{f(SDA)}$ $t_{f(SCL)}$	SDA and SCL fall time	-	300	-	300	ns
$t_{h(STA)}$	Start condition hold time	4.0	-	0.6	-	µs
$t_{su(STA)}$	Repeated Start condition setup time	4.7	-	0.6	-	µs
$t_{su(STO)}$	Stop condition setup time	4.0	-	0.6	-	µs
$t_{w(STO:STA)}$	Stop to Start condition time (bus free)	4.7	-	1.3	-	µs
C_b	Capacitive load for each bus line	-	400	-	400	pF

1. Guaranteed by design, not tested in production.
2. f_{PCLK1} must be at least 2 MHz to achieve standard mode I²C frequencies. It must be at least 4 MHz to achieve fast mode I²C frequencies. It must be a multiple of 10 MHz to reach the 400 kHz maximum I²C fast mode clock.
3. The maximum Data hold time has only to be met if the interface does not stretch the low period of SCL signal.

Figure 17. I^2C bus AC waveforms and measurement circuit



1. R_S = series protection resistor.
2. R_P = external pull-up resistor.
3. V_{DD_I2C} is the I2C bus power supply.
4. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Table 48. SCL frequency (f_{PCLK1}= 32 MHz, V_{DD} = V_{DD_I2C} = 3.3 V)(1)(2)

f_{SCL} (kHz)	I2C_CCR value
	R_P = 4.7 kΩ
400	0x801B
300	0x8024
200	0x8035
100	0x00A0
50	0x0140
20	0x0320

1. R_P = External pull-up resistance, f_{SCL} = I^2C speed.
2. For speeds around 200 kHz, the tolerance on the achieved speed is of ±5%. For other speed ranges, the tolerance on the achieved speed is ±2%. These variations depend on the accuracy of the external components used to design the application.

SPI characteristics

Unless otherwise specified, the parameters given in the following table are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 14*.

Refer to *Section 6.3.11: I/O current injection characteristics* for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 49. SPI characteristics(1)

Symbol	Parameter	Conditions	Min	Max(2)	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	16	MHz
		Slave mode	-	16	
		Slave transmitter	-	12(3)	
$t_{r(SCK)}$(2) $t_{f(SCK)}$(2)	SPI clock rise and fall time	Capacitive load: C = 30 pF	-	6	ns
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	30	70	%
$t_{su(NSS)}$	NSS setup time	Slave mode	$4t_{HCLK}$	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode	$2t_{HCLK}$	-	
$t_{w(SCKH)}$(2) $t_{w(SCKL)}$(2)	SCK high and low time	Master mode	$t_{SCK}/2-5$	$t_{SCK}/2+3$	
$t_{su(MI)}$(2)	Data input setup time	Master mode	5	-	
$t_{su(SI)}$(2)		Slave mode	6	-	
$t_{h(MI)}$(2)	Data input hold time	Master mode	5	-	
$t_{h(SI)}$(2)		Slave mode	5	-	
$t_{a(SO)}$(4)	Data output access time	Slave mode	0	$3t_{HCLK}$	
$t_{v(SO)}$(2)	Data output valid time	Slave mode	-	33	
$t_{v(MO)}$(2)	Data output valid time	Master mode	-	6.5	
$t_{h(SO)}$(2)	Data output hold time	Slave mode	17	-	
$t_{h(MO)}$(2)		Master mode	0.5	-	

1. The characteristics above are given for voltage range 1.
2. Based on characterization, not tested in production.
3. The maximum SPI clock frequency in slave transmitter mode is given for an SPI slave input clock duty cycle (DuCy(SCK)) ranging between 40 to 60%.
4. Min time is for the minimum time to drive the output and max time is for the maximum time to validate the data.

Figure 18. SPI timing diagram - slave mode and CPHA = 0

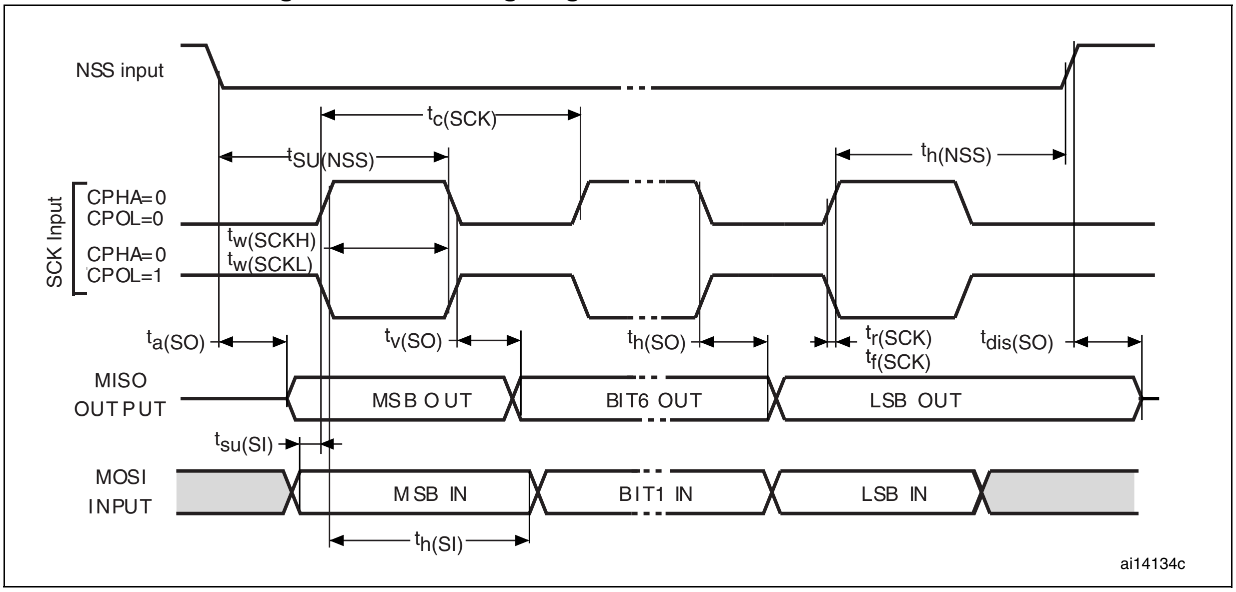
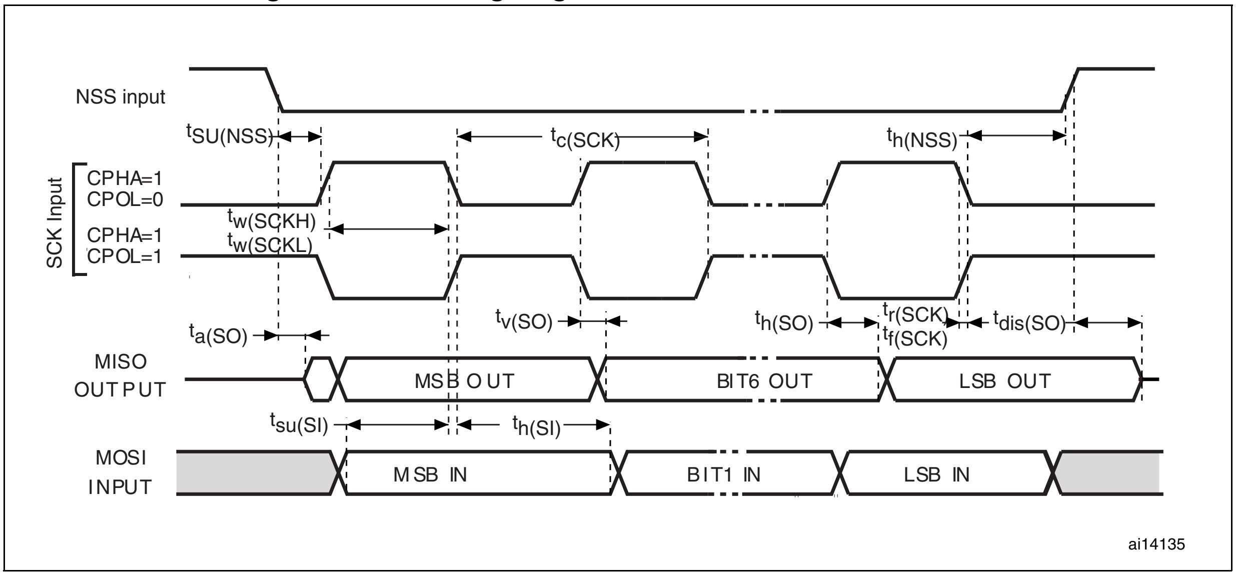
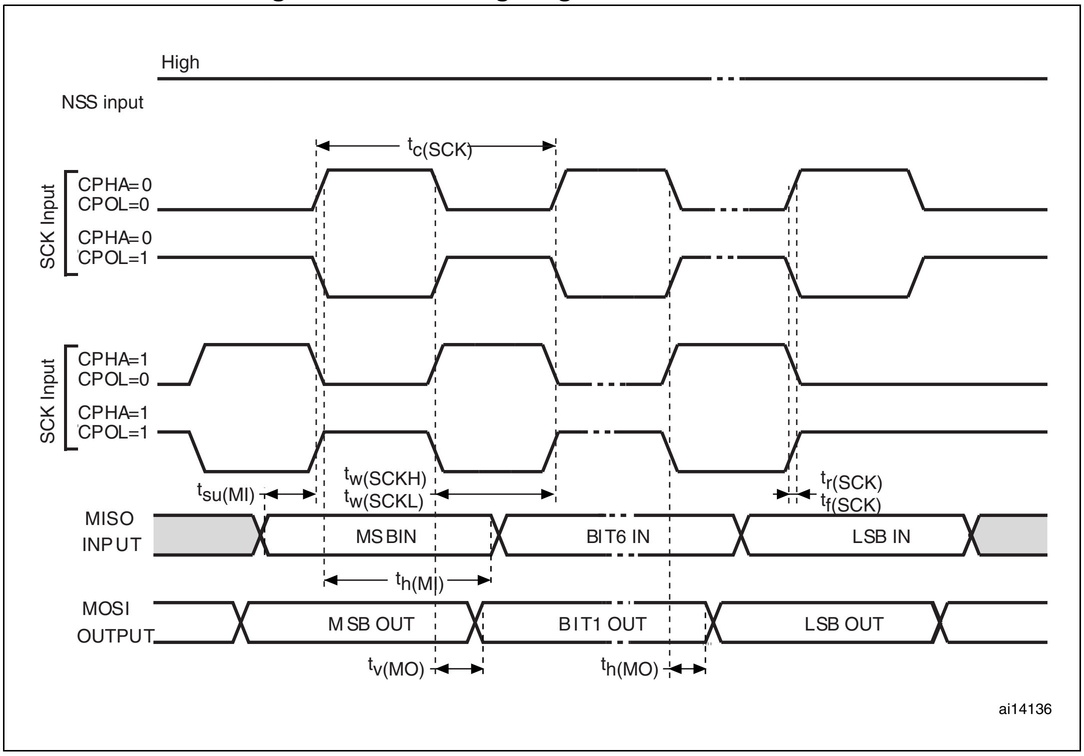


Figure 19. SPI timing diagram - slave mode and CPHA = 1[(1)]



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Figure 20. SPI timing diagram - master mode(1)



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

6.3.16 I2S characteristics

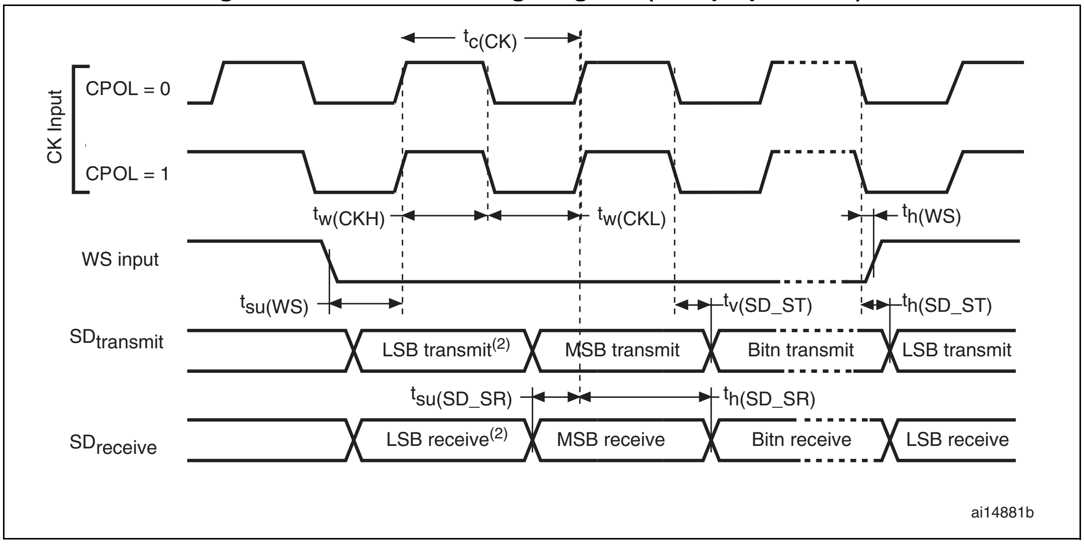
Table 50. I2S characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCK}	I2S Main Clock Output		256 x 8K	256xFs [1]	MHz
f_{CK}	I2S clock frequency	Master data: 32 bits	-	64xFs	MHz
		Slave data: 32 bits	-	64xFs	
D_{CK}	I2S clock frequency duty cycle	Slave receiver, 48KHz	30	70	%
$t_{r(CK)}$	I2S clock rise time	Capacitive load CL=30pF	-	8	ns
$t_{f(CK)}$	I2S clock fall time			8	
$t_{v(WS)}$	WS valid time	Master mode	4	24	
$t_{h(WS)}$	WS hold time	Master mode	0	-	
$t_{su(WS)}$	WS setup time	Slave mode	15	-	
$t_{h(WS)}$	WS hold time	Slave mode	0	-	
$t_{su(SD\_MR)}$	Data input setup time	Master receiver	8	-	
$t_{su(SD\_SR)}$	Data input setup time	Slave receiver	9	-	
$t_{h(SD\_MR)}$	Data input hold time	Master receiver	5	-	
$t_{h(SD\_SR)}$		Slave receiver	4	-	
$t_{v(SD\_ST)}$	Data output valid time	Slave transmitter (after enable edge)	-	64	
$t_{h(SD\_ST)}$	Data output hold time	Slave transmitter (after enable edge)	22	-	
$t_{v(SD\_MT)}$	Data output valid time	Master transmitter (after enable edge)	-	12	
$t_{h(SD\_MT)}$	Data output hold time	Master transmitter (after enable edge)	8	-	

1. The maximum for 256xFs is 8 MHz

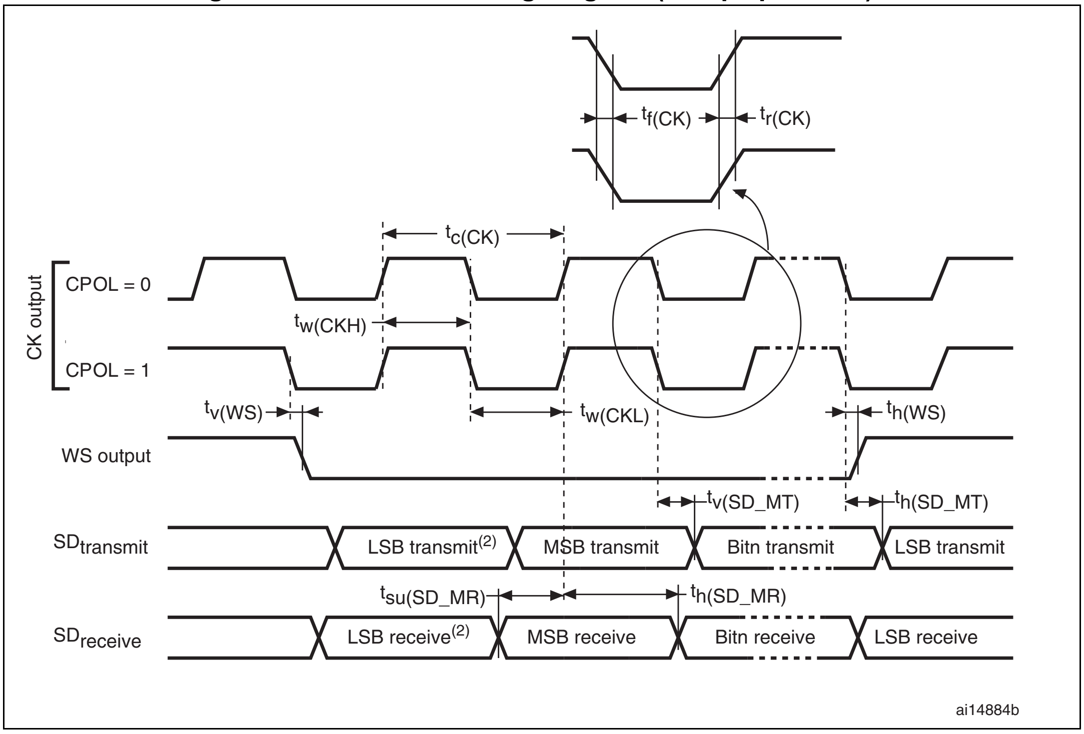
*Note: Refer to the I2S section of the product reference manual for more details about the sampling frequency (Fs), f_{MCK}, f_{CK} and D_{CK} values. These values reflect only the digital peripheral behavior, source clock precision might slightly change them. DCK depends mainly on the ODD bit value, digital contribution leads to a min of (I2SDIV/(2*I2SDIV+ODD) and a max of (I2SDIV+ODD)/(2*I2SDIV+ODD). Fs max is supported for each mode/condition.*

Figure 21. I²S slave timing diagram (Philips protocol)(1)



1. Measurement points are done at CMOS levels: $0.3 \times V_{DD}$ and $0.7 \times V_{DD}$.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 22. I²S master timing diagram (Philips protocol)(1)



1. Based on characterization, not tested in production.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

USB characteristics

The USB interface is USB-IF certified (full speed).

Table 51. USB startup time

Symbol	Parameter	Max	Unit
$t_{STARTUP}$(1)	USB transceiver startup time	1	µs

1. Guaranteed by design, not tested in production.

Table 52. USB DC electrical characteristics

Symbol	Parameter	Conditions	Min.(1)	Max.(1)	Unit
Input levels					
V_{DD}	USB operating voltage		3.0	3.6	V
V_{DI}(2)	Differential input sensitivity	I(USB_DP, USB_DM)	0.2	-	V
V_{CM}(2)	Differential common mode range	Includes V_{DI} range	0.8	2.5	V
V_{SE}(2)	Single ended receiver threshold		1.3	2.0	V
Output levels					
V_{OL}(3)	Static output level low	R_L of 1.5 kΩ to 3.6 V(4)	-	0.3	V
V_{OH}(3)	Static output level high	R_L of 15 kΩ to V_{SS}(4)	2.8	3.6	V

1. All the voltages are measured from the local ground potential.
2. Guaranteed by characterization, not tested in production.
3. Tested in production.
4. R_L is the load connected on the USB drivers.

Figure 23. USB timings: definition of data signal rise and fall time

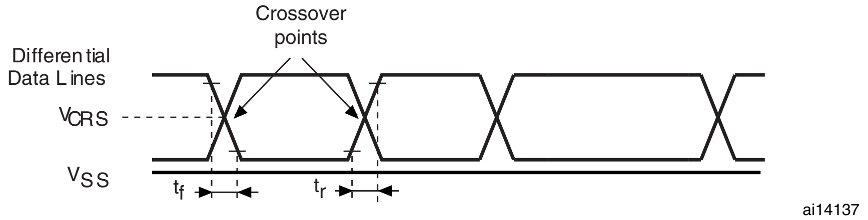


Table 53. USB: full speed electrical characteristics

Driver characteristics(1)					
Symbol	**Parameter**	**Conditions**	**Min**	**Max**	**Unit**
t_r	Rise time(2)	C_L = 50 pF	4	20	ns
t_f	Fall Time(2)	C_L = 50 pF	4	20	ns
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage		1.3	2.0	V

1. Guaranteed by design, not tested in production.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

6.3.17 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 55* are guaranteed by design.

Table 54. ADC clock frequency

Symbol	Parameter	Conditions			Min	Max	Unit
f_{ADC}	ADC clock frequency	Voltage range 1 & 2	$2.4\ V \le V_{DDA} \le 3.6\ V$	$V_{REF+} = V_{DDA}$	0.480	16	MHz
				$V_{REF+} < V_{DDA}$ $V_{REF+} > 2.4\ V$		8	
				$V_{REF+} < V_{DDA}$ $V_{REF+} \le 2.4\ V$		4	
			$1.8\ V \le V_{DDA} \le 2.4\ V$	$V_{REF+} = V_{DDA}$		8	
				$V_{REF+} < V_{DDA}$		4	
		Voltage range 3				4	

Table 55. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Power supply		1.8	-	3.6	V
V_{REF+}	Positive reference voltage	$2.4\ V \le V_{DDA} \le 3.6\ V$ V_{REF+} must be below or equal to V_{DDA}	1.8(1)	-	V_{DDA}	
V_{REF-}	Negative reference voltage		-	V_{SSA}	-	
I_{VDDA}	Current on the V_{DDA} input pin		-	1000	1450	µA
I_{VREF}(2)	Current on the V_{REF} input pin	Peak	-	400	700	
		Average	-		450	
V_{AIN}	Conversion voltage range(3)		0(4)	-	V_{REF+}	V
f_S	12-bit sampling rate	Direct channels	0.03	-	1	Msps
		Multiplexed channels	0.03	-	0.76	
	10-bit sampling rate	Direct channels	0.03	-	1.07	Msps
		Multiplexed channels	0.03	-	0.8	
	8-bit sampling rate	Direct channels	0.03	-	1.23	Msps
		Multiplexed channels	0.03	-	0.89	
	6-bit sampling rate	Direct channels	0.03	-	1.54	Msps
		Multiplexed channels	0.03	-	1	

Table 55. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_S	Sampling time	Direct channels 2.4 V ≤ V_{DDA} ≤ 3.6 V	0.25	-	-	µs
		Multiplexed channels 2.4 V ≤ V_{DDA} ≤ 3.6 V	0.56	-	-	
		Direct channels 1.8 V ≤ V_{DDA} ≤ 2.4 V	0.56	-	-	
		Multiplexed channels 1.8 V ≤ V_{DDA} ≤ 2.4 V	1	-	-	
			4	-	384	$1/f_{ADC}$
t_{CONV}	Total conversion time (including sampling time)	f_{ADC} = 16 MHz	1	-	24.75	µs
			4 to 384 (sampling phase) +12 (successive approximation)			$1/f_{ADC}$
C_{ADC}	Internal sample and hold capacitor	Direct channels	-	16	-	pF
		Multiplexed channels	-		-	
f_{TRIG}	External trigger frequency Regular sequencer	12-bit conversions	-	-	Tconv+1	$1/f_{ADC}$
		6/8/10-bit conversions	-	-	Tconv	$1/f_{ADC}$
f_{TRIG}	External trigger frequency Injected sequencer	12-bit conversions	-	-	Tconv+2	$1/f_{ADC}$
		6/8/10-bit conversions	-	-	Tconv+1	$1/f_{ADC}$
R_{AIN}	External input impedance		-	-	50	κΩ
t_{lat}	Injection trigger conversion latency	f_{ADC} = 16 MHz	219	-	281	ns
			3.5	-	4.5	$1/f_{ADC}$
t_{latr}	Regular trigger conversion latency	f_{ADC} = 16 MHz	156	-	219	ns
			2.5	-	3.5	$1/f_{ADC}$
t_{STAB}	Power-up time		-	-	3.5	µs

1. The Vref+ input can be grounded if neither the ADC nor the DAC are used (this allows to shut down an external voltage reference).
2. The current consumption through VREF is composed of two parameters:

   - one constant (max 300 µA)

   - one variable (max 400 µA), only during sampling time + 2 first conversion pulses

   So, peak consumption is 300+400 = 700 µA and average consumption is 300 + [(4 sampling + 2) /16] x 400 = 450 µA at 1Msps
3. V_{REF+} can be internally connected to V_{DDA} and V_{REF-} can be internally connected to V_{SSA}, depending on the package. Refer to *Section 4: Pin descriptions* for further details.
4. V_{SSA} or V_{REF-} must be tied to ground.

Table 56. ADC accuracy(1)(2)

Symbol	Parameter	Test conditions	Min(3)	Typ	Max(3)	Unit
ET	Total unadjusted error	$2.4\ V \leq V_{DDA} \leq 3.6\ V$ $2.4\ V \leq V_{REF+} \leq 3.6\ V$ $f_{ADC} = 8\ MHz$, $R_{AIN} = 50\ \Omega$ $T_A = -40$ to 105 °C	-	2	4	LSB
EO	Offset error		-	1	2	
EG	Gain error		-	1.5	3.5	
ED	Differential linearity error		-	1	2	
EL	Integral linearity error		-	1.7	3	
ENOB	Effective number of bits	$2.4\ V \leq V_{DDA} \leq 3.6\ V$ $V_{DDA} = V_{REF+}$ $f_{ADC} = 16\ MHz$, $R_{AIN} = 50\ \Omega$ $T_A = -40$ to 105 °C $1\ kHz \leq F_{input} \leq 100\ kHz$	9.2	10	-	bits
SINAD	Signal-to-noise and distortion ratio		57.5	62	-	dB
SNR	Signal-to-noise ratio		57.5	62	-	
THD	Total harmonic distortion		-74	-75	-	
ET	Total unadjusted error	$2.4\ V \leq V_{DDA} \leq 3.6\ V$ $1.8\ V \leq V_{REF+} \leq 2.4\ V$ $f_{ADC} = 4\ MHz$, $R_{AIN} = 50\ \Omega$ $T_A = -40$ to 105 °C	-	4	6.5	LSB
EO	Offset error		-	2	4	
EG	Gain error		-	4	6	
ED	Differential linearity error		-	1	2	
EL	Integral linearity error		-	1.5	3	
ET	Total unadjusted error	$1.8\ V \leq V_{DDA} \leq 2.4\ V$ $1.8\ V \leq V_{REF+} \leq 2.4\ V$ $f_{ADC} = 4\ MHz$, $R_{AIN} = 50\ \Omega$ $T_A = -40$ to 105 °C	-	2	3	LSB
EO	Offset error		-	1	1.5	
EG	Gain error		-	1.5	2	
ED	Differential linearity error		-	1	2	
EL	Integral linearity error		-	1	1.5	

1. ADC DC accuracy values are measured after internal calibration.
2. ADC accuracy vs. negative injection current: Injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.
Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 6.3.11* does not affect the ADC accuracy.
3. Based on characterization, not tested in production.

Figure 24. ADC accuracy characteristics

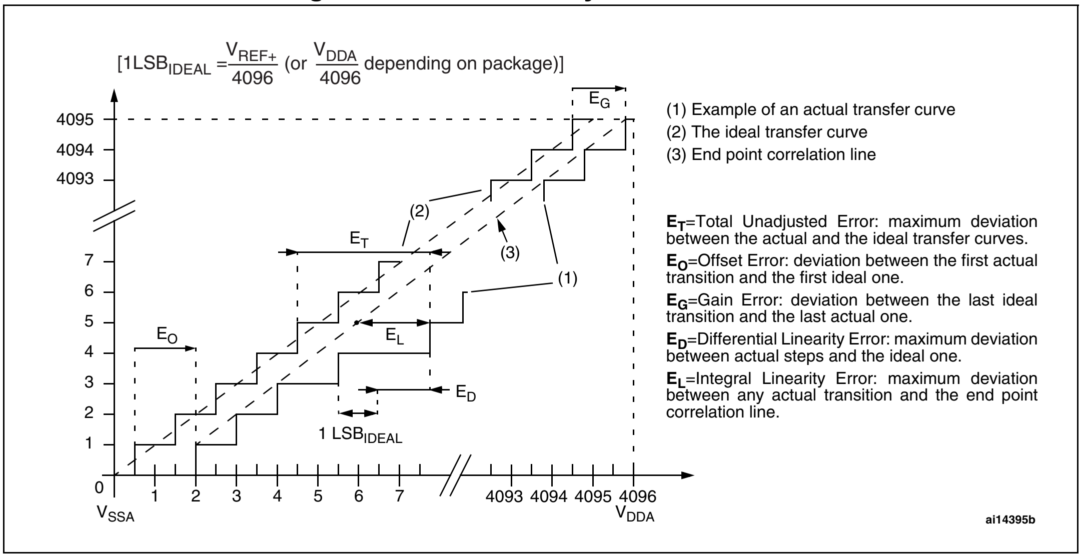
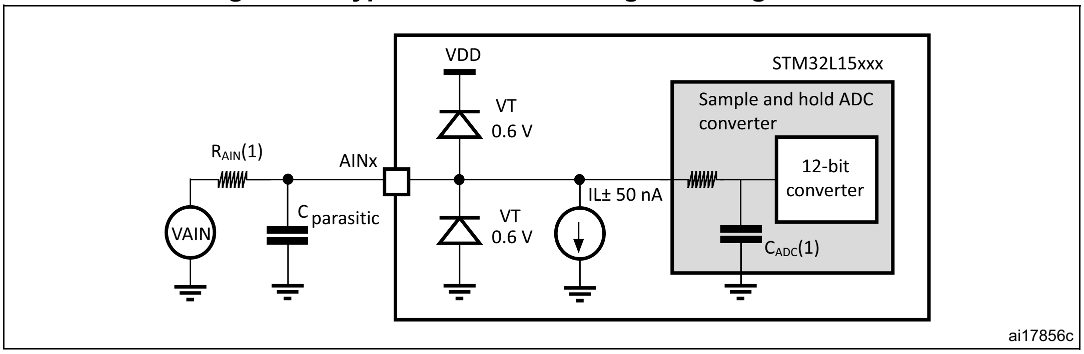


Figure 25. Typical connection diagram using the ADC



1. Refer to *Table 57: RAIN max for fADC = 16 MHz* for the value of R_{AIN} and *Table 55: ADC characteristics* for the value of C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

Figure 26. Maximum dynamic current consumption on V_{REF+} supply pin during ADC conversion

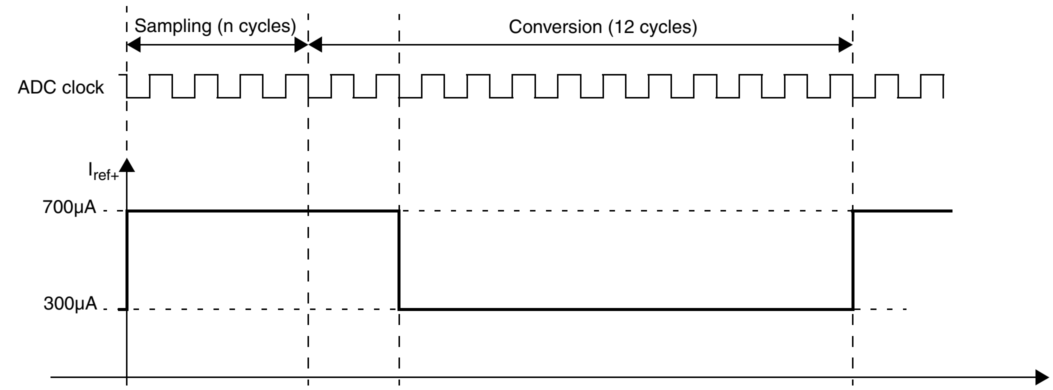


Table 57. R_{AIN} max for f_{ADC} = 16 MHz(1)

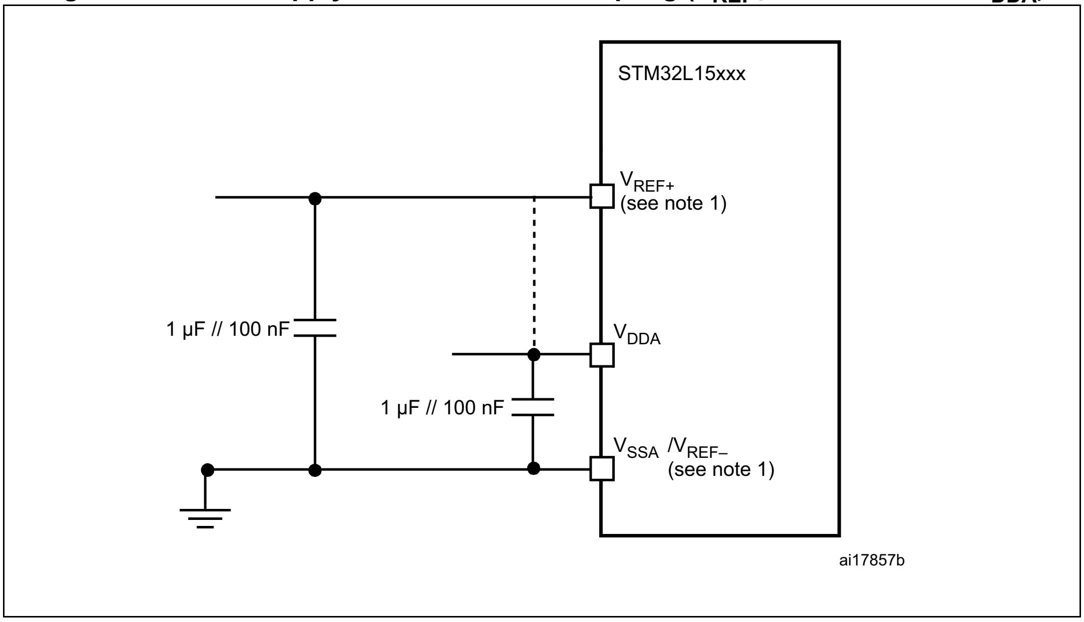
Ts (cycles)	Ts (µs)	R_{AIN} max (kΩ)			
		Multiplexed channels		Direct channels	
		2.4 V < V_{DDA} < 3.6 V	1.8 V < V_{DDA} < 2.4 V	2.4 V < V_{DDA} < 3.3 V	1.8 V < V_{DDA} < 2.4 V
4	0.25	Not allowed	Not allowed	0.7	Not allowed
9	0.5625	0.8	Not allowed	2.0	1.0
16	1	2.0	0.8	4.0	3.0
24	1.5	3.0	1.8	6.0	4.5
48	3	6.8	4.0	15.0	10.0
96	6	15.0	10.0	30.0	20.0
192	12	32.0	25.0	50.0	40.0
384	24	50.0	50.0	50.0	50.0

1. Guaranteed by design, not tested in production.

General PCB design guidelines

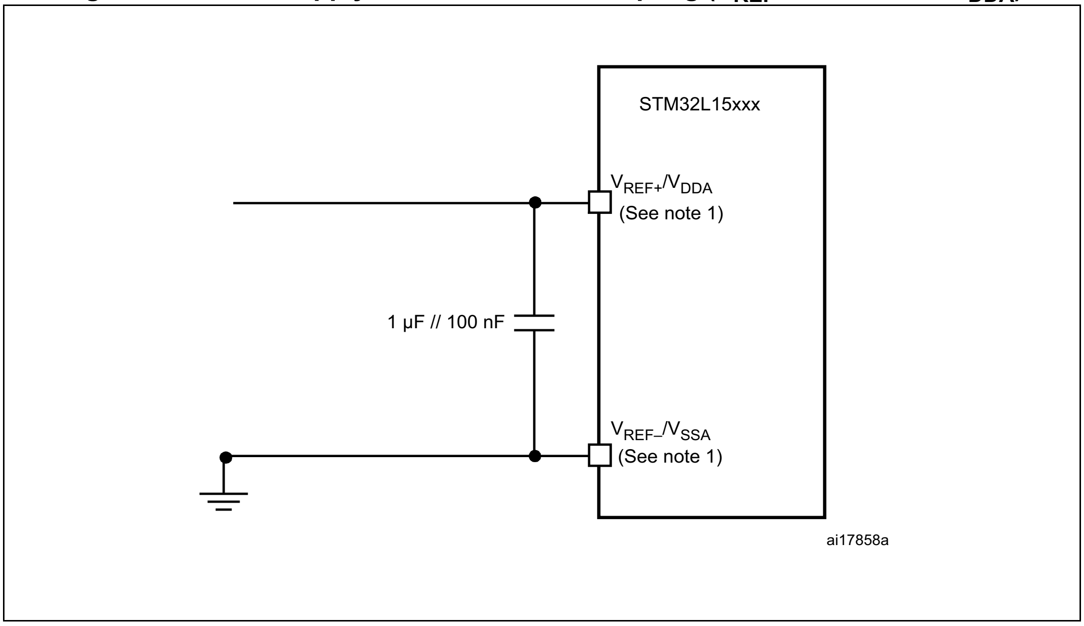
Power supply decoupling should be performed as shown in *Figure 27* or *Figure 28*, depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed as close as possible to the chip.

Figure 27. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are available only on 100-pin packages.

Figure 28. Power supply and reference decoupling (V_{REF+} connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are available only on 100-pin packages.

6.3.18 DAC electrical specifications

Data guaranteed by design, not tested in production, unless otherwise specified.

Table 58. DAC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage		1.8	-	3.6	V
V_{REF+}	Reference supply voltage	V_{REF+} must always be below V_{DDA}	1.8	-	3.6	V
V_{REF-}	Lower reference voltage		V_{SSA}			V
$I_{DDVREF+}$(1)	Current consumption on V_{REF+} supply V_{REF+} = 3.3 V	No load, middle code (0x800)	-	130	220	µA
		No load, worst code (0x000)	-	220	350	µA
I_{DDA}(1)	Current consumption on V_{DDA} supply V_{DDA} = 3.3 V	No load, middle code (0x800)	-	210	320	µA
		No load, worst code (0xF1C)	-	320	520	µA
R_L(2)	Resistive load	DAC output buffer ON	5	-	-	kΩ
C_L(2)	Capacitive load	DAC output buffer ON	-	-	50	pF
R_O	Output impedance	DAC output buffer OFF	6	8	10	kΩ
V_{DAC_OUT}	Voltage on DAC_OUT output	DAC output buffer ON	0.2	-	$V_{DDA} - 0.2$	V
		DAC output buffer OFF	0.5	-	$V_{REF+} - 1LSB$	mV
DNL(1)	Differential non linearity(3)	$C_L \leq$ 50 pF, $R_L \geq$ 5 kΩ DAC output buffer ON	-	1.5	3	LSB
		No R_{LOAD}, $C_L \leq$ 50 pF DAC output buffer OFF	-	1.5	3	LSB
INL(1)	Integral non linearity(4)	$C_L \leq$ 50 pF, $R_L \geq$ 5 kΩ DAC output buffer ON	-	2	4	LSB
		No R_{LOAD}, $C_L \leq$ 50 pF DAC output buffer OFF	-	2	4	LSB
Offset(1)	Offset error at code 0x800 (5)	$C_L \leq$ 50 pF, $R_L \geq$ 5 kΩ DAC output buffer ON	-	±10	±25	LSB
		No R_{LOAD}, $C_L \leq$ 50 pF DAC output buffer OFF	-	±5	±8	LSB
Offset1(1)	Offset error at code 0x001(6)	No R_{LOAD}, $C_L \leq$ 50 pF DAC output buffer OFF	-	±1.5	±5	LSB

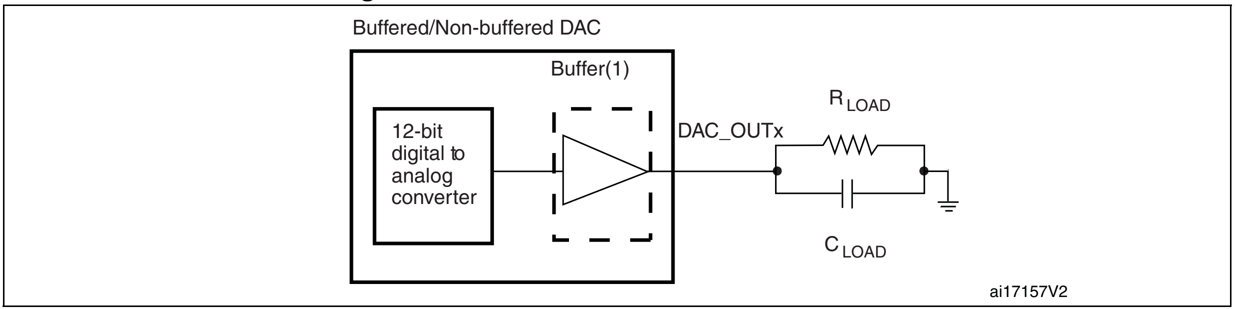
Table 58. DAC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
dOffset/dT[1]	Offset error temperature coefficient (code 0x800)	V_{DDA} = 3.3V V_{REF+} = 3.0V T_A = 0 to 50 °C DAC output buffer OFF	-20	-10	0	µV/°C
		V_{DDA} = 3.3V V_{REF+} = 3.0V T_A = 0 to 50 °C DAC output buffer ON	0	20	50	
Gain[1]	Gain error[7]	$C_L \leq$ 50 pF, $R_L \geq$ 5 kΩ DAC output buffer ON	-	+0.1 / -0.2%	+0.2 / -0.5%	%
		No R_{LOAD}, $C_L \leq$ 50 pF DAC output buffer OFF	-	+0 / -0.2%	+0 / -0.4%	
dGain/dT[1]	Gain error temperature coefficient	V_{DDA} = 3.3V V_{REF+} = 3.0V T_A = 0 to 50 °C DAC output buffer OFF	-10	-2	0	µV/°C
		V_{DDA} = 3.3V V_{REF+} = 3.0V T_A = 0 to 50 °C DAC output buffer ON	-40	-8	0	
TUE[1]	Total unadjusted error	$C_L \leq$ 50 pF, $R_L \geq$ 5 kΩ DAC output buffer ON	-	12	30	LSB
		No R_{LOAD}, $C_L \leq$ 50 pF DAC output buffer OFF	-	8	12	
$t_{SETTLING}$	Settling time (full scale: for a 12-bit code transition between the lowest and the highest input codes till DAC_OUT reaches final value ±1LSB	$C_L \leq$ 50 pF, $R_L \geq$ 5 kΩ	-	7	12	µs
Update rate	Max frequency for a correct DAC_OUT change (95% of final value) with 1 LSB variation in the input code	$C_L \leq$ 50 pF, $R_L \geq$ 5 kΩ	-		1	Msps
t_{WAKEUP}	Wakeup time from off state (setting the ENx bit in the DAC Control register)[8]	$C_L \leq$ 50 pF, $R_L \geq$ 5 kΩ	-	9	15	µs
PSRR+	V_{DDA} supply rejection ratio (static DC measurement)	$C_L \leq$ 50 pF, $R_L \geq$ 5 kΩ	-	-60	-35	dB

1. Data based on characterization results.
2. Connected between DAC_OUT and V_{SSA}.
3. Difference between two consecutive codes - 1 LSB.

4. Difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 4095.
5. Difference between the value measured at Code (0x800) and the ideal value = $V_{REF+}/2$.
6. Difference between the value measured at Code (0x001) and the ideal value.
7. Difference between ideal slope of the transfer function and measured slope computed from code 0x000 and 0xFFF when buffer is OFF, and from code giving 0.2 V and (V_{DDA} – 0.2) V when buffer is ON.
8. In buffered mode, the output can overshoot above the final value for low input code (starting from min value).

Figure 29. 12-bit buffered /non-buffered DAC



1. The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

6.3.19 Operational amplifier characteristics

Table 59. Operational amplifier characteristics

Symbol	Parameter		Condition(1)	Min(2)	Typ	Max(2)	Unit
CMIR	Common mode input range			0	-	V_{DD}	
VI_{OFFSET}	Input offset voltage	Maximum calibration range		-	-	±15	mV
		After offset calibration		-	-	±1.5	
ΔVI_{OFFSET}	Input offset voltage drift	Normal mode		-	-	±40	µV/°C
		Low power mode		-	-	±80	
I_{IB}	Input current bias	Dedicated input	75 °C	-	-	1	nA
		General purpose input		-	-	10	
I_{LOAD}	Drive current	Normal mode		-	-	500	µA
		Low power mode		-	-	100	
I_{DD}	Consumption	Normal mode	No load, quiescent mode	-	100	220	µA
		Low power mode		-	30	60	
CMRR	Common mode rejection ration	Normal mode		-	-85	-	dB
		Low power mode		-	-90	-	
PSRR	Power supply rejection ratio	Normal mode	DC	-	-85	-	dB
		Low power mode		-	-90	-	

Table 59. Operational amplifier characteristics (continued)

Symbol	Parameter		Condition[(1)]	Min[(2)]	Typ	Max[(2)]	Unit
GBW	Bandwidth	Normal mode	V_{DD}>2.4 V	400	1000	3000	kHZ
		Low power mode		150	300	800	
		Normal mode	V_{DD}<2.4 V	200	500	2200	
		Low power mode		70	150	800	
SR	Slew rate	Normal mode	V_{DD}>2.4 V (between 0.1 V and V_{DD}-0.1 V)	-	700	-	V/ms
		Low power mode	V_{DD}>2.4 V	-	100	-	
		Normal mode	V_{DD}<2.4 V	-	300	-	
		Low power mode		-	50	-	
AO	Open loop gain	Normal mode		55	100	-	dB
		Low power mode		65	110	-	
R_{LOAD}	Resistive load	Normal mode	V_{DD}<2.4 V	4	-	-	kΩ
		Low power mode		20	-	-	
C_{LOAD}	Capacitive load			-	-	50	pF
VOH_{SAT}	High saturation voltage	Normal mode	I_{LOAD} = max or R_{LOAD} = min	V_{DD}-100	-	-	mV
		Low power mode		V_{DD}-50	-	-	
VOL_{SAT}	Low saturation voltage	Normal mode		-	-	100	
		low power mode		-	-	50	
φm	Phase margin			-	60	-	°
GM	Gain margin			-	-12	-	dB
$t_{OFFTRIM}$	Offset trim time: during calibration, minimum time needed between two steps to have 1 mV accuracy			-	1	-	ms
t_{WAKEUP}	Wakeup time	Normal mode	C_{LOAD} ≤ 50 pf, R_{LOAD} ≥ 4 kΩ	-	10	-	µs
		Low power mode	C_{LOAD} ≤ 50 pf, R_{LOAD} ≥ 20 kΩ	-	30	-	

1. Operating conditions are limited to junction temperature (0 °C to 105 °C) when V_{DD} is below 2 V. Otherwise, the operating temperature range is 105 °C to -40 °C.
2. Data based on characterization results, not tested in production.

6.3.20 Temperature sensor characteristics

Table 60. Temperature sensor characteristics

Symbol	Parameter	Min	Typ	Max	Unit
T_L(1)	V_{SENSE} linearity with temperature	-	±1	±2	°C
Avg_Slope(1)	Average slope	1.48	1.61	1.75	mV/°C
V_{110}	Voltage at 110°C ±5°C(2)	612	626.8	641.5	mV
$I_{DDA(TEMP)}$(3)	Current consumption	-	3.4	6	µA
t_{START}(3)	Startup time	-	-	10	µs
T_{S_temp}(4)(3)	ADC sampling time when reading the temperature	10	-	-	µs

1. Guaranteed by characterization, not tested in production.
2. Measured at V_{DD} = 3 V ±10 mV. V110 ADC conversion result is stored in the TSENSE_CAL2 byte.
3. Guaranteed by design, not tested in production.
4. Shortest sampling time can be determined in the application by multiple iterations.

6.3.21 Comparator

Table 61. Comparator 1 characteristics

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
V_{DDA}	Analog supply voltage		1.65		3.6	V
R_{400K}	R_{400K} value		-	400	-	kΩ
R_{10K}	R_{10K} value		-	10	-	kΩ
V_{IN}	Comparator 1 input voltage range		0.6	-	V_{DDA}	V
t_{START}	Comparator startup time		-	7	10	µs
td	Propagation delay(2)		-	3	10	µs
Voffset	Comparator offset		-	±3	±10	mV
$d_{Voffset}/dt$	Comparator offset variation in worst voltage stress conditions	V_{DDA} = 3.6 V V_{IN+} = 0 V V_{IN-} = V_{REFINT} T_A = 25 °C	0	1.5	10	mV/1000 h
I_{COMP1}	Current consumption(3)		-	160	260	nA

1. Based on characterization, not tested in production.
2. The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.
3. Comparator consumption only. Internal reference voltage not included.

Table 62. Comparator 2 characteristics

Symbol	Parameter	Conditions	Min	Typ	Max[1]	Unit
V_{DDA}	Analog supply voltage		1.65	-	3.6	V
V_{IN}	Comparator 2 input voltage range		0	-	V_{DDA}	V
t_{START}	Comparator startup time	Fast mode	-	15	20	µs
		Slow mode	-	20	25	
$t_{d\ slow}$	Propagation delay[2] in slow mode	1.65 V ≤ V_{DDA} ≤ 2.7 V	-	1.8	3.5	
		2.7 V ≤ V_{DDA} ≤ 3.6 V	-	2.5	6	
$t_{d\ fast}$	Propagation delay[2] in fast mode	1.65 V ≤ V_{DDA} ≤ 2.7 V	-	0.8	2	
		2.7 V ≤ V_{DDA} ≤ 3.6 V	-	1.2	4	
V_{offset}	Comparator offset error		-	±4	±20	mV
dThreshold/dt	Threshold voltage temperature coefficient	V_{DDA} = 3.3V T_A = 0 to 50 °C V- = V_{REFINT}, 3/4 V_{REFINT}, 1/2 V_{REFINT}, 1/4 V_{REFINT}.	-	15	30	ppm/°C
I_{COMP2}	Current consumption[3]	Fast mode	-	3.5	5	µA
		Slow mode	-	0.5	2	

1. Based on characterization, not tested in production.
2. The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.
3. Comparator consumption only. Internal reference voltage (necessary for comparator operation) is not included.

6.3.22 LCD controller

The STM32L162xC embeds a built-in step-up converter to provide a constant LCD reference voltage independently from the V_{DD} voltage. An external capacitor C_{ext} must be connected to the V_{LCD} pin to decouple this converter.

Table 63. LCD controller characteristics

Symbol	Parameter	Min	Typ	Max	Unit
V_{LCD}	LCD external voltage	-	-	3.6	V
V_{LCD0}	LCD internal reference voltage 0	-	2.6	-	
V_{LCD1}	LCD internal reference voltage 1	-	2.73	-	
V_{LCD2}	LCD internal reference voltage 2	-	2.86	-	
V_{LCD3}	LCD internal reference voltage 3	-	2.98	-	
V_{LCD4}	LCD internal reference voltage 4	-	3.12	-	
V_{LCD5}	LCD internal reference voltage 5	-	3.26	-	
V_{LCD6}	LCD internal reference voltage 6	-	3.4	-	
V_{LCD7}	LCD internal reference voltage 7	-	3.55	-	
C_{ext}	V_{LCD} external capacitance	0.1		2	µF
I_{LCD}(1)	Supply current at V_{DD} = 2.2 V	-	3.3	-	µA
	Supply current at V_{DD} = 3.0 V	-	3.1	-	
R_{Htot}(2)	Low drive resistive network overall value	5.28	6.6	7.92	MΩ
R_L(2)	High drive resistive network total value	192	240	288	kΩ
V_{44}	Segment/Common highest level voltage	-	-	V_{LCD}	V
V_{34}	Segment/Common 3/4 level voltage	-	3/4 V_{LCD}	-	V
V_{23}	Segment/Common 2/3 level voltage	-	2/3 V_{LCD}	-	
V_{12}	Segment/Common 1/2 level voltage	-	1/2 V_{LCD}	-	
V_{13}	Segment/Common 1/3 level voltage	-	1/3 V_{LCD}	-	
V_{14}	Segment/Common 1/4 level voltage	-	1/4 V_{LCD}	-	
V_0	Segment/Common lowest level voltage	0	-	-	
ΔVxx(3)	Segment/Common level voltage error T_A = -40 to 85 °C	-	-	± 50	mV

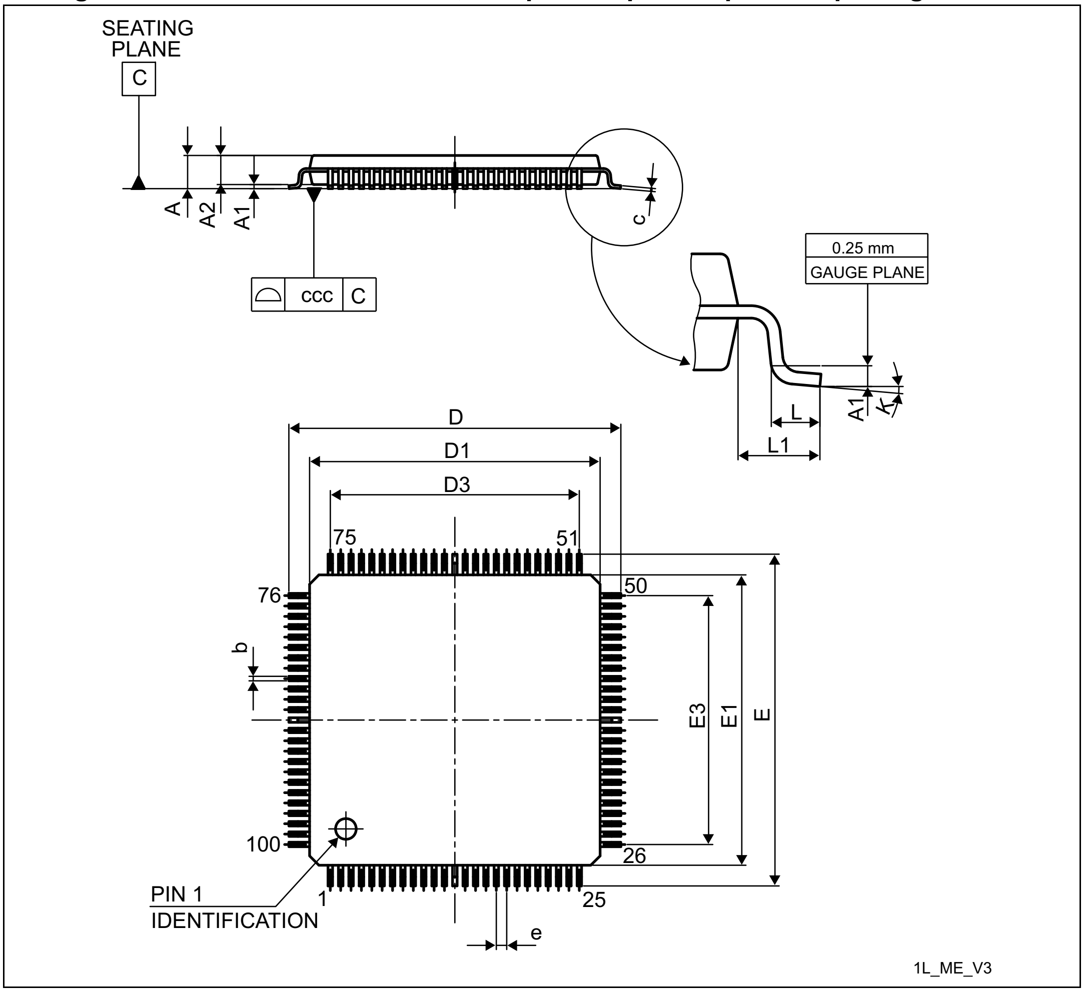
1. LCD enabled with 3 V internal step-up active, 1/8 duty, 1/4 bias, division ratio= 64, all pixels active, no LCD connected.
2. Guaranteed by design, not tested in production.
3. Based on characterization, not tested in production.

7 Package characteristics

7.1 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

Figure 30. LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package outline



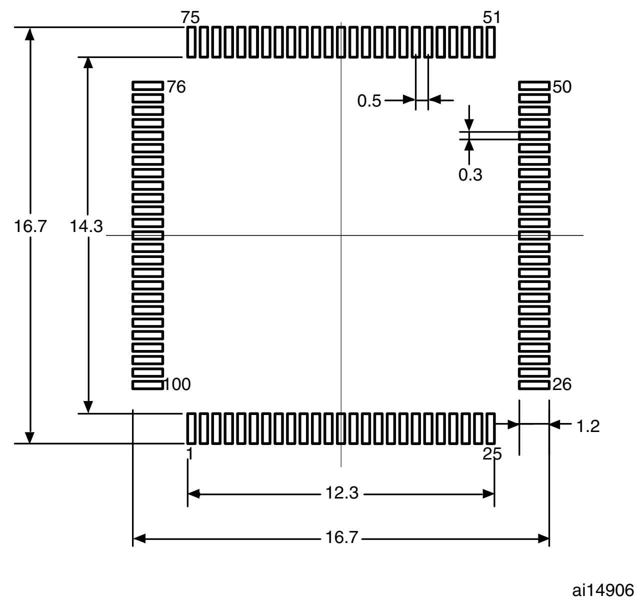
1. Drawing is not to scale.

Table 64. LQPF100, 14 x 14 mm, 100-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
A			1.600			0.0630
A1	0.050		0.150	0.0020		0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090		0.200	0.0035		0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3		12.000			0.4724	
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3		12.000			0.4724	
e		0.500			0.0197	
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1		1.000			0.0394	
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc			0.080			0.0031

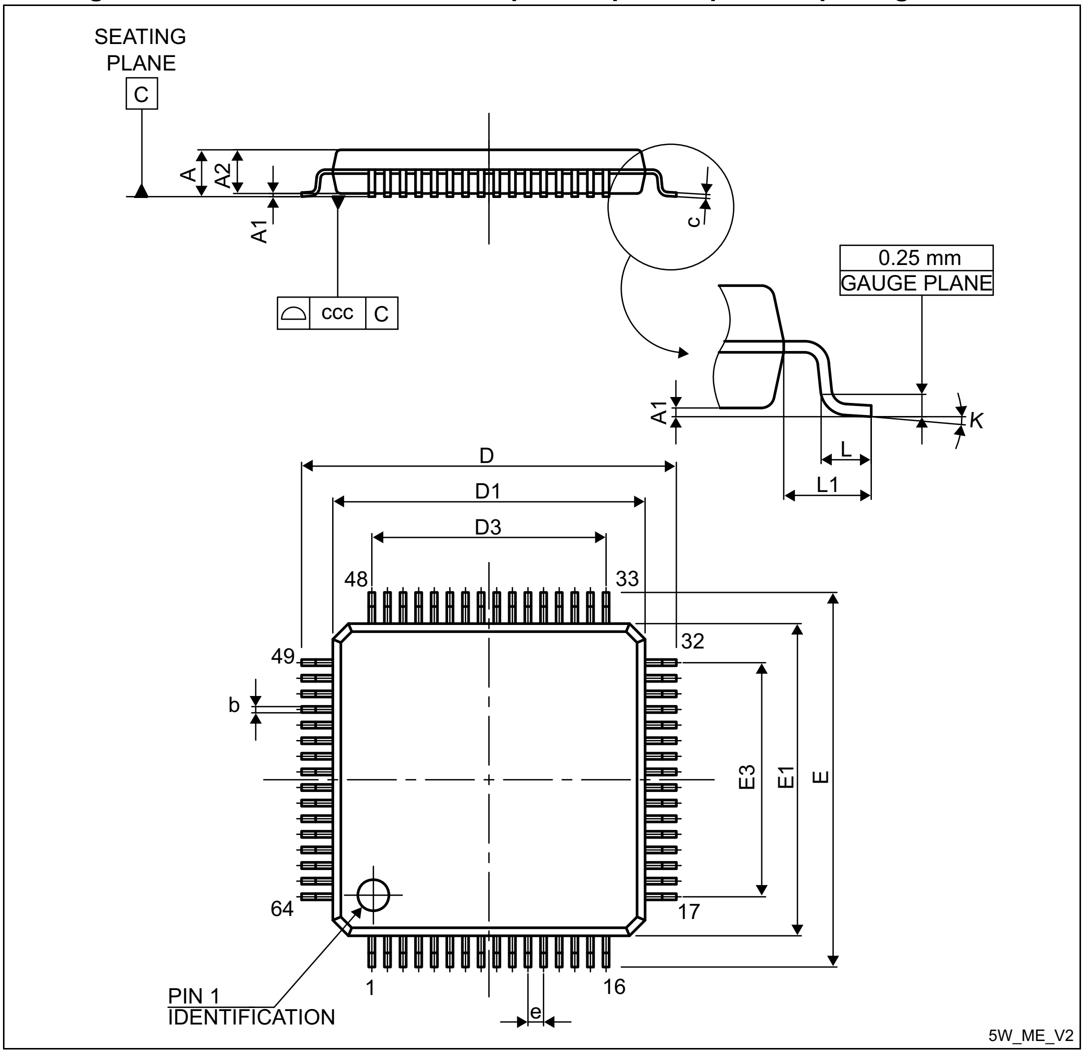
1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 31. LQFP100 recommended footprint



1. Dimensions are in millimeters.

Figure 32. LQFP64, 10 x 10 mm, 64-pin low-profile quad flat package outline



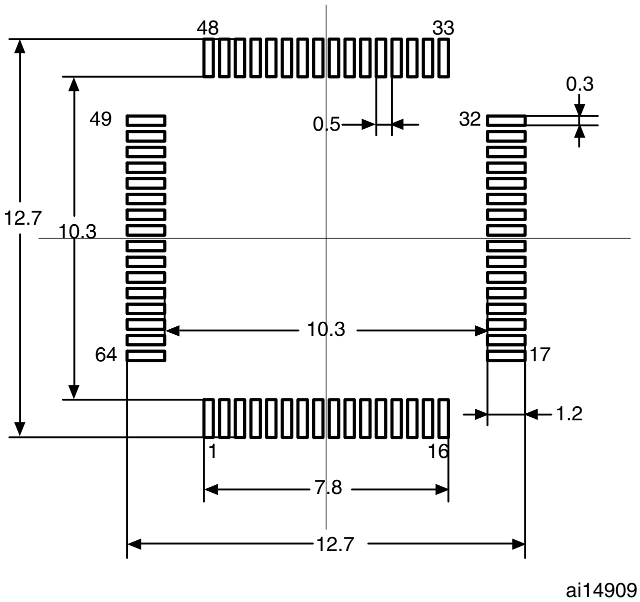
1. Drawing is not to scale.

Table 65. LQFP64, 10 x 10 mm 64-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
A			1.600			0.0630
A1	0.050		0.150	0.0020		0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090		0.200	0.0035		0.0079
D	11.800	12.000	12.200	0.4646	0.4724	0.4803
D1	9.800	10.000	10.200	0.3858	0.3937	0.4016
D3		7.500			0.2953	
E	11.800	12.000	12.200	0.4646	0.4724	0.4803
E1	9.800	10.000	10.200	0.3858	0.3937	0.4016
E3		7.500			0.2953	
e		0.500			0.0197	
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1		1.000			0.0394	
ccc			0.080			0.0031
K	0.0	3.5	7.0	0.0	3.5	7.0

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 33. LQFP64 recommended footprint



1. Dimensions are in millimeters.

7.2 Thermal characteristics

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

T_J max = T_A max + (P_D max × Θ_{JA})

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

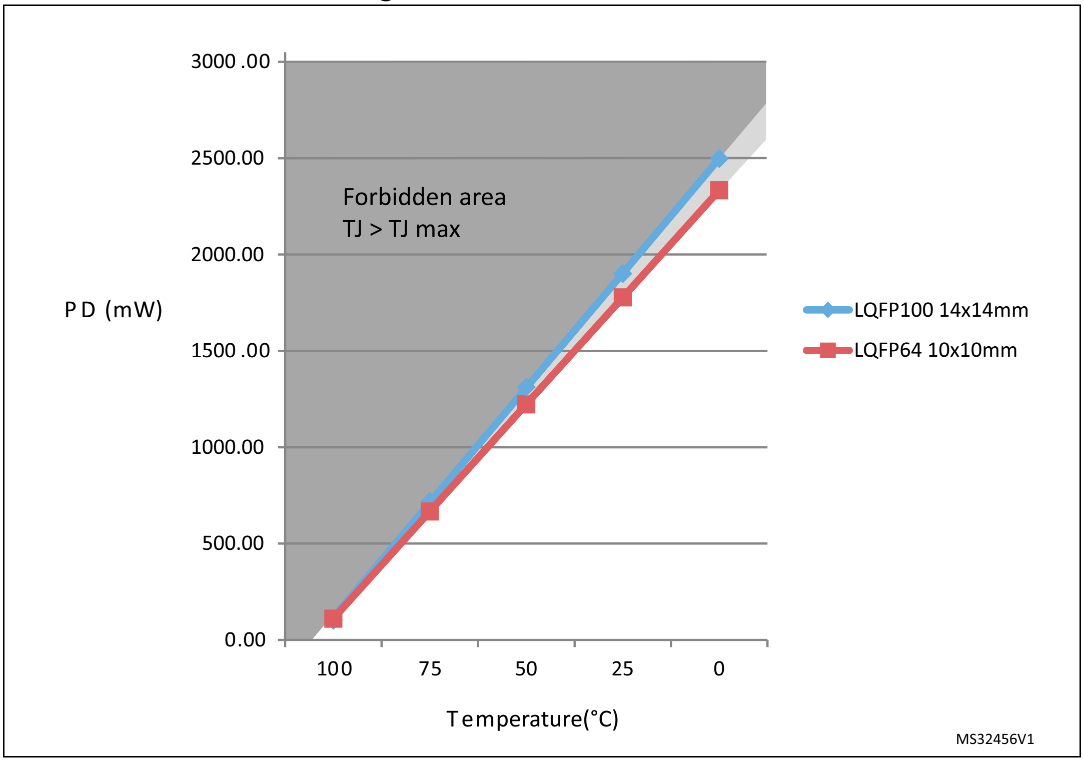
$P_{I/O}$ max = Σ (V_{OL} × I_{OL}) + Σ((V_{DD} – V_{OH}) × I_{OH}),

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 66. Thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	**Thermal resistance junction-ambient** LQFP100 - 14 x 14 mm / 0.5 mm pitch	43	°C/W
	Thermal resistance junction-ambient LQFP64 - 10 x 10 mm / 0.5 mm pitch	46	

Figure 34. Thermal resistance



7.2.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

8 Ordering information scheme

Table 67. STM32L162xC ordering information scheme

Example: STM32 L 162 V C T 6 D xxx

Device family

STM32 = ARM-based 32-bit microcontroller

Product type

L = Low power

Device subfamily

162: Devices with LCD

Pin count

R = 64 pins

V = 100 pins

Flash memory size

C = 256 Kbytes of Flash memory

Package

T = LQFP

Temperature range

6 = Industrial temperature range, –40 to 85 °C

Options

No character = V_{DD} range: 1.8 to 3.6 V and BOR enabled

D = V_{DD} range: 1.65 to 3.6 V and BOR disabled

Packing

TR = tape and reel

No character = tray or tube

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

9 Revision history

Table 68. Document revision history

Date	Revision	Changes
04-Apr-2012	1	Initial release.
12-Oct-2012	2	Added *Table 4: Functionalities depending on the working mode (from Run/active down to standby)* and *Table 3: CPU frequency range depending on dynamic voltage scaling*. Updated *Section 3.10: ADC (analog-to-digital converter)* to add *Section 3.10.1: Temperature sensor* and *Section 3.10.2: Internal voltage reference (VREFINT)*. Updated *Figure 3: STM32L162VC LQFP100 pinout*. Changed FSMC_LBAR into FSMC_NADV, I2C1_SMBAI into I2C1_SMBA in *Table 9: STM32L162xC pin definitions*. Modified PB10/11/12 for AFIO4 alternate function, and replaced LBAR by NADV for AFIO12 in *Table 10: Alternate function input/output*. Removed caution note below *Figure 8: Power supply scheme*. Added *Note 2* in *Table 15: Embedded reset and power control block characteristics*. Updated *Table 22: Typical and maximum current consumptions in Stop mode* and added *Note 6*. Updated *Table 23: Typical and maximum current consumptions in Standby mode*. Updated t_{WUSTOP} in *Table :* . Updated *Table 25: Peripheral current consumption*. Updated *Table 35: Flash memory and data EEPROM characteristics*. Updated *Table 49: SPI characteristics*, added *Note 1* and *Note 3*, and applied *Note 2* to $t_{r(SCK)}$, $t_{f(SCK)}$, $t_{w(SCKH)}$, $t_{w(SCKL)}$, $t_{su(MI)}$, $t_{su(SI)}$, $t_{h(MI)}$, and $t_{h(SI)}$. Added *Table 50: I2S characteristics*, *Figure 21: I2S slave timing diagram (Philips protocol)(1)* and *Figure 22: I2S master timing diagram (Philips protocol)(1)*. Updated *Table 60: Temperature sensor characteristics*. Added *Figure 34: Thermal resistance on page 109*.

Table 68. Document revision history (continued)

Date	Revision	Changes
06-Feb-2013	3	Removed AHB1/AHB2 and corrected typo on APB1/APB2 in *Figure 1: Ultra-low-power STM32L162xC block diagram* Updated "OP amp" line in *Table 4: Functionalities depending on the working mode (from Run/active down to standby)* Added IWDG and WWDG rows in *Table 4: Functionalities depending on the working mode (from Run/active down to standby)* Updated address range in *Table 7: Internal voltage reference measured values* The comment "HSE = 16 MHz(2) (PLL ON for fHCLK above 16 MHz)" replaced by "fHSE = fHCLK up to 16 MHz included, fHSE = fHCLK/2 above 16 MHz (PLL ON)(2)" in table *Table 19: Current consumption in Sleep mode* Updated Stop mode current to 1.5 µA in *Ultra-low-power platform* Replaced BGA132 by UFBGA132 in *Figure 4: STM32L162QC UFBGA132 ballout.* Updated entire *Section 7: Package characteristics* Updated *Figure 25: Typical connection diagram using the ADC* and definition of symbol "R_{AIN}" in *Table 55: ADC characteristics* Removed first sentence in *Section : I2C interface characteristics*
19-Jul-2013	4	Removed STM32L162QC and STM32L162ZC part numbers including all associated features. Updated dThreshold/dt conditions in *Table 62: Comparator 2 characteristics*. Updated *Figure 8: Power supply scheme*. Updated *Figure 34: Thermal resistance*. Updated PH0-OSC_IN and PH1-OSC_OUT type in *Figure 9: STM32L162xC pin definitions*. Added *Section 6.1.7: Optional LCD power supply scheme*. Updated I_{DD} (WU from Standby) unit in *Table 23: Typical and maximum current consumptions in Standby mode*. Updated *Figure 6: Pin loading conditions*. Updated *Figure 7: Pin input voltage*. Updated *Figure 14: Typical application with a 32.768 kHz crystal*. Updated *Figure 16: Recommended NRST pin protection*. Updated *Figure 17: I2C bus AC waveforms and measurement circuit*.
04-Sep-2013	5	Added *Table 5: VLCD rail decoupling* Added VRAIL functions in *Table 9: STM32L162xC pin definitions* Updated *Figure 9: Optional LCD power supply scheme* Updated consumption data in *Section 6.3.4: Supply current characteristics* Fixed columns inversion in *Table 65: LQFP64, 10 x 10 mm 64-pin low-profile quad flat package mechanical data*